AO 120 (Rev. 08/10)

DECISION/JUDGEMENT

TO: Mail Stop 8 TO: Director of the U.S. Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450			REPORT ON THE FILING OR DETERMINATION OF AN ACTION REGARDING A PATENT OR TRADEMARK		
filed in the U.S. Distr		rn Distr	§ 1116 you are hereby advised that a court action has been ict of Texas, Waco Division on the following es 35 U.S.C. § 292.):		
DOCKET NO. 6:22-cv-00105	DATE FILED 1/27/2022	U.S. DI	STRICT COURT Western District of Texas, Waco Division		
PLAINTIFF GREENTHREAD, LLC			DEFENDANT INTEL CORPORATION, DELL INC., AND DELL TECHNOLOGIES INC.,		
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK		HOLDER OF PATENT OR TRADEMARK		
1 8,421,195	4/16/2013	GRE	EENTHREAD, LLC		
2 9,190,502	11/17/2015	GREENTHREAD, LLC			
3 10,510,842	12/17/2019	GREENTHREAD, LLC			
4 10,734,481	8/4/2020	GREENTHREAD, LLC			
5 11,121,222	9/14/2021	GRE	EENTHREAD, LLC		

In the above---entitled case, the following patent(s)/ trademark(s) have been included:

DATE INCLUDED	INCLUDED BY	dment 🔲 Answer 🔲 Cross Bill 🔲 Other Pleading
PATENT OR TRADEMARK NO.	DATE OF PATENT OR TRADEMARK	HOLDER OF PATENT OR TRADEMARK
1 11,316,014	4/26/2022	GREENTHREAD, LLC
2		
3		
4		
5		

In the above---entitled case, the following decision has been rendered or judgement issued:

CLERK (BY) DEPUTY CLERK DATE

Copy 1—Upon initiation of action, mail this copy to Director Copy 3—Upon termination of action, mail this copy to Director Copy 2—Upon filing document adding patent(s), mail this copy to Director Copy 4—Case file copy

UNITED STATES PATENT AND TRADEMARK OFFICE



APPLICATION NO.	ISSUE DATE	PATENT NO.	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	04/26/2022	11316014	GRTD60-35314	2197

25883 7590 04/06/2022 MUNCK WILSON MANDALA L.L.P P.O. Drawer 800889 DALLAS, TX 75380

ISSUE NOTIFICATION

The projected patent number and issue date are specified above.

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(application filed on or after May 29, 2000)

The Patent Term Adjustment is 0 day(s). Any patent to issue from the above-identified application will include an indication of the adjustment on the front page.

If a Continued Prosecution Application (CPA) was filed in the above-identified application, the filing date that determines Patent Term Adjustment is the filing date of the most recent CPA.

Applicant will be able to obtain more detailed information by accessing the Patent Application Information Retrieval (PAIR) WEB site (http://pair.uspto.gov).

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Application Assistance Unit (AAU) of the Office of Patents Stakeholder Experience (OPSE), Stakeholder Support Division (SSD) at (571)-272-4200.

INVENTOR(s) (Please see PAIR WEB site http://pair.uspto.gov for additional inventors):

G.R. MOHAN RAO, ALLEN, TX;

APPLICANT(s) (Please see PAIR WEB site http://pair.uspto.gov for additional applicants):

GREENTHREAD, LLC, Dallas, TX;

The United States represents the largest, most dynamic marketplace in the world and is an unparalleled location for business investment, innovation, and commercialization of new technologies. The USA offers tremendous resources and advantages for those who invest and manufacture goods here. Through SelectUSA, our nation works to encourage and facilitate business investment. To learn more about why the USA is the best country in the world to develop technology, manufacture products, and grow your business, visit <u>SelectUSA.gov</u>. IR103 (Rev. 10/09)

further correspondence inc	cluding the Patent, advar	nce orders and notification	n of maintenance fees will b lence address; and/or (b) in	be mailed to the curr idicating a separate	s 1 through 5 should be comp ent correspondence address "FEE ADDRESS" for main	as indicated unless corrected tenance fee notifications.
CURRENT CORRESPONDED	NCE ADDRESS (Note: Use Blo	ock 1 for any change of address)	Fee(pape	Note: A certificate of mailing can only be used for domestic mailings of the Fee(s) Transmittal. This certificate cannot be used for any other accompanying papers. Each additional paper, such as an assignment or formal drawing, must have its own certificate of mailing or transmission.		
	7590 03/23/			Cert	tificate of Mailing or Trans	
	MUNCK WILSON MANDALA L.L.P P.O. Drawer 800889			es Postal Service w	s Fee(s) Transmittal is being ith sufficient postage for fir	st class mail in an envelope
	DALLAS, TX 75380				top ISSUE FEE address ab eb or by facsimile to (571) 2	
21122110, 11170	DALLAS, 1X 75500					(Typed or printed name)
						(Signature)
						(Date)
APPLICATION NO.	FILING DATE		FIRST NAMED INVENTOR		ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021		G.R. MOHAN RAO		GRTD60-35314	2197
TITLE OF INVENTION:	SEMICONDUCTOR D	EVICES WITH GRADE	ED DOPANT REGIONS			
APPLN. TYPE	ENTITY STATUS	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE	E FEE TOTAL FEE(S) DUE	DATE DUE
nonprovisional	UNDISCOUNTED	\$1200	\$0.00	\$0.00	\$1200	06/23/2022
EXAMI	NER	ART UNIT	CLASS-SUBCLASS			
ARORA,	AJAY	2892	257-025000	1		
1. Change of corresponder	nce address or indication	of "Fee Address" (37	2. For printing on the p	atent front page. lis	t	
CFR 1.363).		× ×	(1) The names of up to or agents OR, alternativ	3 registered patent		M. Howison
Change of correspond	ndence address (or Char A/122 or PTO/SB/122) a	nge of Correspondence	(2) The name of a singl	le firm (having as a	member a	
			registered attorney or agent) and the names of up to 2 registered patent attorneys or agents. If no name is listed, no name will be printed.			
AIA/47 or PTO/SB/47; Customer Number is 1	cation (or "Fee Address" Rev 03-02 or more reco	ent) attached. Use of a				
3. ASSIGNEE NAME AN		TO BE PRINTED ON T	FHE PATENT (print or typ	pe)		
PLEASE NOTE: Unles	ss an assignee is identifie	ed below, no assignee dat	a will appear on the patent. $P_{3} \otimes P_{4}$	If an assignee is id	entified below, the documen substitute for filing an assign	t must have been previously
(A) NAME OF ASSIG		157 CFK 5.11 and 57 CF	(B) RESIDENCE: (CITY			innent.
GREENTHREA			DALLAS, TEXAS			
	•				ation or other private group	
		lication Fee (if required)	Advance Order - #		ation or other private group	entity 🖵 Government
4b. Method of Payment: (1				or copies		
Electronic Payment			Non-electronic payment by	credit card (Attach	form PTO-2038)	
🛛 The Director is here	by authorized to charge	the required fee(s), any	deficiency, or credit any ov	erpayment to Depo	sit Account No. <u>50-0208</u>	_
5. Change in Entity Statu	us (from status indicated	d above)	NOTE About out 11	10 - 11 CD C		0/0D/15 A
Applicant certifying	g micro entity status. See	e 37 CFR 1.29	fee payment in the micro	entity amount will a	Entity Status (see forms PTG not be accepted at the risk of	application abandonment.
Applicant asserting				s of entitlement to n		0
Applicant changing	to regular undiscounted	l fee status.	<u>NOTE:</u> Checking this box entity status, as applicable		a notification of loss of enti	itlement to small or micro
NOTE: This form must be				ature requirements a	und certifications.	
Authorized Signature _	/William G. Howis	son, Reg. #66850/		Date March	n 23, 2022	
Typed or printed name	Typed or printed name William G. Howison Registration No. 66,850					

PTOL-85 Part B (08-18) Approved for use through 01/31/2020

Page 2 of 3 OMB 0651-0033 003

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

By fax, send to: (571)-273-2885

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), by mail or fax, or via EFS-Web.

By mail, send to: Mail Stop ISSUE FEE Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Electronic Patent Application Fee Transmittal					
Application Number:	17:	371839			
Filing Date:	09.	-Jul-2021			
Title of Invention:	SEI	MICONDUCTOR DE\	/ICES WITH GRA	ded dopant reg	ions
First Named Inventor/Applicant Name:	G.R. MOHAN RAO				
Filer:	William G. Howison/Anna Nguyen				
Attorney Docket Number:	GR	TD60-35314			
Filed as Large Entity					
Filing Fees for Utility under 35 USC 111(a)					
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Basic Filing:					
Pages:					
Claims:					
Miscellaneous-Filing:					
Petition:					
Patent-Appeals-and-Interference:					
Post-Allowance-and-Post-Issuance:					

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)	
PUBL. FEE- EARLY, VOLUNTARY, OR NORMAL	1504	1	0	0	
UTILITY APPL ISSUE FEE	1501	1	1200	1200	
Extension-of-Time:					
Miscellaneous:					
	Tot	al in USD	(\$)	1200	

Electronic A	Electronic Acknowledgement Receipt					
EFS ID:	45300225					
Application Number:	17371839					
International Application Number:						
Confirmation Number:	2197					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	G.R. MOHAN RAO					
Customer Number:	25883					
Filer:	William G. Howison					
Filer Authorized By:						
Attorney Docket Number:	GRTD60-35314					
Receipt Date:	23-MAR-2022					
Filing Date:	09-JUL-2021					
Time Stamp:	15:40:43					
Application Type:	Utility under 35 USC 111(a)					

Payment information:

Submitted with Payment	yes				
Payment Type	CARD				
Payment was successfully received in RAM	\$1200				
RAM confirmation Number	E20223MF45452092				
Deposit Account	500208				
Authorized User	William Howison				
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:					
37 CFR 1.16 (National application filing, search, an	d examination fees)				

37 CFR 1.17 (Patent application and reexamination processing fees)

37 CFR 1.19 (Document supply fees)

37 CFR 1.21 (Miscellaneous fees and charges)

File Listing:

Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.
			1231571		
1	Issue Fee Payment (PTO-85B)	GRT35314IssueFeeTransmittal. pdf	c23ddc1d6949e077a00bd27b1dc82df75f1 50ea8	no	1
Warnings:					
nformation:					
			40395		
2	Fee Worksheet (SB06)	fee-info.pdf	591f9a252b7a02f743b3047422b0137efc39 3983	no	2
Warnings:					
Information:					
		Total Files Size (in bytes)	12	71966	
characterized Post Card, as	edgement Receipt evidences receip I by the applicant, and including pa described in MPEP 503. <u>ions Under 35 U.S.C. 111</u>				
	cation is being filed and the applica	ation includes the necessary c	omponents for a filin	a date (see	37 CFR



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

NOTICE OF ALLOWANCE AND FEE(S) DUE

25883 7590 03/23/2022 MUNCK WILSON MANDALA L.L.P P.O. Drawer 800889 DALLAS, TX 75380 EXAMINER ARORA, AJAY ART UNIT PAPER NUMBER 2892

DATE MAILED: 03/23/2022

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197

TITLE OF INVENTION: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

APPLN. TYPE	ENTITY STATUS	ISSUE FEE DUE	PUBLICATION FEE DUE	PREV. PAID ISSUE FEE	TOTAL FEE(S) DUE	DATE DUE
nonprovisional	UNDISCOUNTED	\$1200	\$0.00	\$0.00	\$1200	06/23/2022

THE APPLICATION IDENTIFIED ABOVE HAS BEEN EXAMINED AND IS ALLOWED FOR ISSUANCE AS A PATENT. <u>PROSECUTION ON THE MERITS IS CLOSED</u>. THIS NOTICE OF ALLOWANCE IS NOT A GRANT OF PATENT RIGHTS. THIS APPLICATION IS SUBJECT TO WITHDRAWAL FROM ISSUE AT THE INITIATIVE OF THE OFFICE OR UPON PETITION BY THE APPLICANT. SEE 37 CFR 1.313 AND MPEP 1308.

THE ISSUE FEE AND PUBLICATION FEE (IF REQUIRED) MUST BE PAID WITHIN <u>THREE MONTHS</u> FROM THE MAILING DATE OF THIS NOTICE OR THIS APPLICATION SHALL BE REGARDED AS ABANDONED. <u>THIS STATUTORY PERIOD</u> <u>CANNOT BE EXTENDED</u>. SEE 35 U.S.C. 151. THE ISSUE FEE DUE INDICATED ABOVE DOES NOT REFLECT A CREDIT FOR ANY PREVIOUSLY PAID ISSUE FEE IN THIS APPLICATION. IF AN ISSUE FEE HAS PREVIOUSLY BEEN PAID IN THIS APPLICATION (AS SHOWN ABOVE), THE RETURN OF PART B OF THIS FORM WILL BE CONSIDERED A REQUEST TO REAPPLY THE PREVIOUSLY PAID ISSUE FEE TOWARD THE ISSUE FEE NOW DUE.

HOW TO REPLY TO THIS NOTICE:

I. Review the ENTITY STATUS shown above. If the ENTITY STATUS is shown as SMALL or MICRO, verify whether entitlement to that entity status still applies.

If the ENTITY STATUS is the same as shown above, pay the TOTAL FEE(S) DUE shown above.

If the ENTITY STATUS is changed from that shown above, on PART B - FEE(S) TRANSMITTAL, complete section number 5 titled "Change in Entity Status (from status indicated above)".

For purposes of this notice, small entity fees are 1/2 the amount of undiscounted fees, and micro entity fees are 1/2 the amount of small entity fees.

II. PART B - FEE(S) TRANSMITTAL, or its equivalent, must be completed and returned to the United States Patent and Trademark Office (USPTO) with your ISSUE FEE and PUBLICATION FEE (if required). If you are charging the fee(s) to your deposit account, section "4b" of Part B - Fee(s) Transmittal should be completed. If an equivalent of Part B is filed, a request to reapply a previously paid issue fee must be clearly made, and delays in processing may occur due to the difficulty in recognizing the paper as an equivalent of Part B.

III. All communications regarding this application must give the application number. Please direct all communications prior to issuance to Mail Stop ISSUE FEE unless advised to the contrary.

IMPORTANT REMINDER: Maintenance fees are due in utility patents issuing on applications filed on or after Dec. 12, 1980. It is patentee's responsibility to ensure timely payment of maintenance fees when due. More information is available at www.uspto.gov/PatentMaintenanceFees.

INSTRUCTIONS: This form should be used for transmitting the ISSUE FEE and PUBLICATION FEE (if required). Blocks 1 through 5 should be completed where appropriate. All further correspondence including the Patent, advance orders and notification of maintenance fees will be mailed to the current correspondence address as indicated unless corrected below or directed otherwise in Block 1, by (a) specifying a new correspondence address; and/or (b) indicating a separate "FEE ADDRESS" for maintenance fee notifications. Note: A certificate of mailing can only be used for domestic mailings of the Fee(s) Transmittal. This certificate cannot be used for any other accompanying CURRENT CORRESPONDENCE ADDRESS (Note: Use Block 1 for any change of address) papers. Each additional paper, such as an assignment or formal drawing, must have its own certificate of mailing or transmission. Certificate of Mailing or Transmission 25883 7590 03/23/2022 I hereby certify that this Fee(s) Transmittal is being deposited with the United MUNCK WILSON MANDALA L.L.P States Postal Service with sufficient postage for first class mail in an envelope P.O. Drawer 800889 addressed to the Mail Stop ISSUE FEE address above, or being transmitted to the USPTO via EFS-Web or by facsimile to (571) 273-2885, on the date below. **DALLAS, TX 75380** (Typed or printed name (Signature (Date APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO. 17/371.839 07/09/2021 G.R. MOHAN RAO GRTD60-35314 2197 TITLE OF INVENTION: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS APPLN. TYPE ENTITY STATUS **ISSUE FEE DUE** PUBLICATION FEE DUE PREV. PAID ISSUE FEE TOTAL FEE(S) DUE DATE DUE UNDISCOUNTED \$1200 \$0.00 \$0.00 \$1200 06/23/2022 nonprovisional EXAMINER ART UNIT CLASS-SUBCLASS ARORA, AJAY 2892 257-025000 1. Change of correspondence address or indication of "Fee Address" (37 2. For printing on the patent front page, list CFR 1.363). (1) The names of up to 3 registered patent attorneys or agents OR, alternatively, Change of correspondence address (or Change of Correspondence (2) The name of a single firm (having as a member a Address form PTO/AIA/122 or PTO/SB/122) attached. registered attorney or agent) and the names of up to 2 registered patent attorneys or agents. If no name is "Fee Address" indication (or "Fee Address" Indication form PTO/ listed, no name will be printed. AIA/47 or PTO/SB/47; Rev 03-02 or more recent) attached. Use of a Customer Number is required. 3. ASSIGNEE NAME AND RESIDENCE DATA TO BE PRINTED ON THE PATENT (print or type) PLEASE NOTE: Unless an assignee is identified below, no assignee data will appear on the patent. If an assignee is identified below, the document must have been previously recorded, or filed for recordation, as set forth in 37 CFR 3.11 and 37 CFR 3.81(a). Completion of this form is NOT a substitute for filing an assignment. (A) NAME OF ASSIGNEE (B) RESIDENCE: (CITY and STATE OR COUNTRY) Please check the appropriate assignee category or categories (will not be printed on the patent) : 🗖 Individual 📮 Corporation or other private group entity 📮 Government Issue Fee Publication Fee (if required) Advance Order - # of Copies 4a. Fees submitted: 4b. Method of Payment: (Please first reapply any previously paid fee shown above) Electronic Payment via EFS-Web Enclosed check Non-electronic payment by credit card (Attach form PTO-2038) The Director is hereby authorized to charge the required fee(s), any deficiency, or credit any overpayment to Deposit Account No. 5. Change in Entity Status (from status indicated above) NOTE: Absent a valid certification of Micro Entity Status (see forms PTO/SB/15A and 15B), issue Applicant certifying micro entity status. See 37 CFR 1.29 fee payment in the micro entity amount will not be accepted at the risk of application abandonment. NOTE: If the application was previously under micro entity status, checking this box will be taken Applicant asserting small entity status. See 37 CFR 1.27 to be a notification of loss of entitlement to micro entity status. NOTE: Checking this box will be taken to be a notification of loss of entitlement to small or micro Applicant changing to regular undiscounted fee status. entity status, as applicable. NOTE: This form must be signed in accordance with 37 CFR 1.31 and 1.33. See 37 CFR 1.4 for signature requirements and certifications. Authorized Signature Date Typed or printed name Registration No.

PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), by mail or fax, or via EFS-Web.

By mail, send to: Mail Stop ISSUE FEE Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 By fax, send to: (571)-273-2885

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

UNITED STATES PATENT AND TRADEMARK OFFICE UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Mission 22313-1450 www.uspto.gov					
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197	
25883 75	03/23/2022		EXAM	IINER	
MUNCK WILSO	ON MANDALA L.L.	Р	ARORA	, AJAY	
P.O. Drawer 80088 DALLAS, TX 753			ART UNIT	PAPER NUMBER	
DALLAS, IA 155	00		2892		
			DATE MAILED: 03/23/202	2	

Determination of Patent Term Adjustment under 35 U.S.C. 154 (b)

(Applications filed on or after May 29, 2000)

The Office has discontinued providing a Patent Term Adjustment (PTA) calculation with the Notice of Allowance.

Section 1(h)(2) of the AIA Technical Corrections Act amended 35 U.S.C. 154(b)(3)(B)(i) to eliminate the requirement that the Office provide a patent term adjustment determination with the notice of allowance. See Revisions to Patent Term Adjustment, 78 Fed. Reg. 19416, 19417 (Apr. 1, 2013). Therefore, the Office is no longer providing an initial patent term adjustment determination with the notice of allowance. The Office will continue to provide a patent term adjustment determination Letter that is mailed to applicant approximately three weeks prior to the issue date of the patent, and will include the patent term adjustment on the patent. Any request for reconsideration of the patent term adjustment determination (or reinstatement of patent term adjustment) should follow the process outlined in 37 CFR 1.705.

Any questions regarding the Patent Term Extension or Adjustment determination should be directed to the Office of Patent Legal Administration at (571)-272-7702. Questions relating to issue and publication fee payments should be directed to the Customer Service Center of the Office of Patent Publication at 1-(888)-786-0101 or (571)-272-4200.

OMB Clearance and PRA Burden Statement for PTOL-85 Part B

The Paperwork Reduction Act (PRA) of 1995 requires Federal agencies to obtain Office of Management and Budget approval before requesting most types of information from the public. When OMB approves an agency request to collect information from the public, OMB (i) provides a valid OMB Control Number and expiration date for the agency to display on the instrument that will be used to collect the information and (ii) requires the agency to inform the public about the OMB Control Number's legal significance in accordance with 5 CFR 1320.5(b).

The information collected by PTOL-85 Part B is required by 37 CFR 1.311. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 30 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450. Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b) (2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- 1. The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether disclosure of these records is required by the Freedom of Information Act.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspection or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

	Application No.	Applicant(s)			
Notice of Allowability	17/371,839	RAO, G.R. MOHAN			
	Examiner	Art Unit	AIA (FITF) Status		
	AJAY ARORA	2892	No		

All claims being allowable, PROSECUTION ON THE ME herewith (or previously mailed), a Notice of Allowance (P	RITS IS (OR REMA TOL-85) or other ap TENT RIGHTS. This	propriate communication will be mailed in due course. THIS s application is subject to withdrawal from issue at the initiative
1. This communication is responsive to $3/4/2022$.		
A declaration(s)/affidavit(s) under 37 CFR 1.13	30(b) was/were filed	on
2. An election was made by the applicant in response restriction requirement and election have been inc		
	operty office for the c	ou may be eligible to benefit from the Patent Prosecution corresponding application. For more information, please see inquiry to PPHfeedback@uspto.gov.
4. Acknowledgment is made of a claim for foreign pri	ority under 35 U.S.C	. § 119(a)-(d) or (f).
Certified copies:		
a) 🗌 All b) 🛄 Some* c) 🗌 None of t	he:	
 Certified copies of the priority docum Certified copies of the priority docum 		
3. Copies of the certified copies of the	priority documents ha	ave been received in this national stage application from the
International Bureau (PCT Rule 17.2	?(a)).	
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILIN noted below. Failure to timely comply will result in AB. THIS THREE-MONTH PERIOD IS NOT EXTENDAB	ANDONMENT of this	nmunication to file a reply complying with the requirements application.
5. CORRECTED DRAWINGS (as "replacement shee	ets") must be submitt	ed.
including changes required by the attached E Paper No./Mail Date		
Identifying indicia such as the application number (see sheet. Replacement sheet(s) should be labeled as such		ld be written on the drawings in the front (not the back) of each ling to 37 CFR 1.121(d).
6. DEPOSIT OF and/or INFORMATION about the de attached Examiner's comment regarding REQUIR		
Attachment(s)		
1. Notice of References Cited (PTO-892)		5. 🗌 Examiner's Amendment/Comment
2. Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date		6. 🗹 Examiner's Statement of Reasons for Allowance
3. Examiner's Comment Regarding Requirement for I	Deposit	7. 🗌 Other
of Biological Material 4. Interview Summary (PTO-413),		
Paper No./Mail Date		
/AJAY ARORA/		
Primary Examiner, Art Unit 2892		
U.S. Patent and Trademark Office PTOL-37 (Rev. 08-13)	Notice of Allowabil	ity Part of Paper No./Mail Date 20220308
	AUGUCE OF AUGWADII	ny

DETAILED ACTION

Notice of Pre-AIA or AIA Status

1. The present application is being examined under the pre-AIA first to invent provisions.

Reasons for Allowance

2. Claims 1-30 are allowed. The following is an examiner's statement of reasons for allowance:

Claims 1-20 are allowed because the prior art of record does not teach or suggest, singularly or in combination, at least the limitations of the base claim 1 that requires "at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface towards the area of the substrate where there are no active regions" (see last 5 lines).

The closest reference is Hong (US 2007/0045682), hereinafter Hong. More specifically, regarding claim 17, Hong (refer to Figures 4A-4D and 5A-5C) teaches An electronic system, the system comprising:

a substrate (312 – see para 29) of a first doping type (i.e. parts 312 and 21 of the substrate have n-type doping, see para 29) of a first doping type and a first doping level having a surface;

Application/Control Number: 17/371,839 Art Unit: 2892

a first region (311, which includes wells such as 21, 22, 5, 2) disposed adjacent the first surface,

a second active region (such as source/drain region 2, see para 40; or 2 or 5 or 22 of pixel cell formed in an adjacent region separated by shallow trench isolation 37 – see para 30) separate from the first region disposed adjacent to the first active region and within which transistors (406, 407) may be formed;

at least a portion of at least one of the first and second regions having at least one graded dopant concentration (350 – see para 24, last 3 sentences; also see Figure 5C and para 29) to aid carrier movement (para 26).

However, the first region is not an "active" region and the structure does not show that the graded dopant region is to "aid carrier movement from the surface to the area of the substrate where there are no active regions". Further, it is not obvious to modify Hong as changing first region and second region as above would change the intended function of the device.

Similarly, claims 21-30 are allowed because the prior art of record does not teach or suggest, singularly or in combination, at least the limitations of base claim 21 that requires "at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface to the area of the substrate where there are no active regions" (see last 5 lines). Again, the closest reference is Hong.

014

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY ARORA whose telephone number is (571)272-8347. The examiner can normally be reached 9 AM - 5 PM.

Examiner interviews are available via telephone, in-person, and video conferencing using a USPTO supplied web-based collaboration tool. To schedule an interview, applicant is encouraged to use the USPTO Automated Interview Request (AIR) at http://www.uspto.gov/interviewpractice.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on 5712721708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of published or unpublished applications may be obtained from Patent Center. Unpublished application information in Patent Center is available to registered users. To file and manage patent submissions in Patent Center, visit: https://patentcenter.uspto.gov. Visit https://www.uspto.gov/patents/apply/patentcenter for more information about Patent Center and https://www.uspto.gov/patents/docx for information about filing in DOCX format. For additional questions, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service

Representative, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY ARORA/ Primary Examiner, Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Issue Classification	17/371,839	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY ARORA	2892

CPC	CPC									
Symbol			Туре	Version						
H01L	/ 29	/ 1095	F	2013-01-01						
H01L	/ 27	/ 11524	I	2013-01-01						
H01L	/ 27	/ 14643	I	2013-01-01						
H01L	/ 27	/ 11521	I	2013-01-01						
H01L	/ 29	/ 7395	I	2013-01-01						
H01L	/ 29	/ 36	I	2013-01-01						
H01L	/ 27	0214	А	2013-01-01						
H01L	/ 27	/ 10844	А	2013-01-01						

CPC Combination Sets									
Symbol	Туре	Set	Ranking	Version					

NONE	Total Claims Allowed:					
(Assistant Examiner)	(Date)	30				
/AJAY ARORA/ Primary Examiner, Art Unit 2892	08 March 2022	O.G. Print Claim(s)	O.G. Print Figure			
(Primary Examiner)	(Date)	1	5b			
U.S. Patent and Trademark Office		Part of Paper No.: 202203				

Application/Control No.	Applicant(s)/Patent Under Reexamination
17/371,839	RAO, G.R. MOHAN
Examiner	Art Unit
AJAY ARORA	2892

INTERNATIONAL CLASSIFICATION							
CLAIMED							
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NON-CLAIMED							
		1					

US ORIGINAL CLASSIFICATION										
CLASS			SUBCLASS							
257				25						
CROSS REFERENC	ES(S)									
CLASS		SUBCLASS (ONE SUBCLASS PER BLOCK)								

NONE	Total Claim	s Allowed:				
(Assistant Examiner)	(Date)	30				
/AJAY ARORA/ Primary Examiner, Art Unit 2892	08 March 2022	O.G. Print Claim(s)	O.G. Print Figure			
(Primary Examiner)	(Date)	1 5b				
U.S. Patent and Trademark Office Part of Paper No.: 20220						

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Issue Classification	17/371,839	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY ARORA	2892

	Claims renumbered in the same order as presented by applicant CPA IT.D. R.1.47														
CLAIN	CLAIMS														
Final	Original	Final	Original	Final	Original	Final	Original	Final	Original	Final	Original	Final	Original	Final	Original
	1		10		19		28								
	2		11		20		29								
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	7		16		25										
	8		17		26										
	9		18		27										

NONE		Total Claim	s Allowed:
(Assistant Examiner)	(Date)	30)
/AJAY ARORA/ Primary Examiner, Art Unit 2892	08 March 2022	O.G. Print Claim(s)	O.G. Print Figure
(Primary Examiner)	(Date)	1	5b
U.S. Patent and Trademark Office		Pa	art of Paper No.: 20220308



Application/Control No.	Applicant(s)/Patent Under Reexamination
17/371,839	RAO, G.R. MOHAN
Examiner	Art Unit
AJAY ARORA	2892

CPC - Searched*				
Symbol	Date	Examiner		
H01L 29/1095	10/23/2021	АКА		

CPC Combination Sets - Searched*					
Symbol Date Examiner					

US Classification - Searched*					
Class	Subclass Date Examine				
257	25	10/23/2021	AKA		

* See search history printout included with this form or the SEARCH NOTES box below to determine the scope of the search.

Search Notes					
Search Notes	Date	Examiner			
Inventor search	10/23/2021	AKA			
Assignee search	10/23/2021	AKA			
References for all parent applications (10/934,915; 11/622,496; 15/ 590,282; 16/717950 and 16/947294) considered	10/23/2021	АКА			
.clm. interference search	10/23/2021	AKA			
EAST search history report	10/23/2021	AKA			
Revised EAST search history report	02/23/2022	AKA			
Revised EAST search history report	03/08/2022	aka			

/AJAY ARORA/ Primary Examiner, Art Unit 2892



Application/Control No.	Applicant(s)/Patent Under Reexamination
17/371,839	RAO, G.R. MOHAN
Examiner	Art Unit
AJAY ARORA	2892

Interference Search						
US Class/CPC Symbol	US Subclass/CPC Group	Date	Examiner			
H01L	29/1095	10/23/2021	АКА			
257	25	10/23/2021	AKA			

/AJAY ARORA/ Primary Examiner, Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Index of Claims	17/371,839	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY ARORA	2892

•	Rejected		Cancelled	N	Non-Elected	Α	Appeal
=	Allowed	+	Restricted	Ι	Interference	0	Objected

					CLAIMS					
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Final	Original	10/23/2021	02/23/2022	03/08/2022						
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	2	✓	1	=						
	3	1	1	=						
	4	✓	 ✓ 	=						
	5	~	 ✓ 	=						
	6	✓	 ✓ 	=						
	7	1	~	=						
	8	~	1	=						
	9	1	1	=						
	10	~	1	=						
	11	~	1	=						
	12	1	1	=						
	13	~	~	=						
	14	1	1	=						
	15	√	1	=						
	16	1	1	=						
	17	1	1	=						
	18	1	1	=						
	19	1	1	=						
	20	√	1	=						
	21	1	1	=						
	22	1	1	=						
	23	1	1	=						
	24	1	✓	=						
	25	1		=						
	26	1	✓	=						L
	27	1	✓	=						L
	28	1	<i>✓</i>	=						L
	29	1	✓	=						
	30	1	√	=						

OK TO ENTER: /A.A/

GRTD60-35314

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	G. R. Mohan Rao
Serial No.:	17/371,839
Confirmation No.:	2197
Filed:	July 9, 2021
Group:	2892
Examiner:	Ajay Arora
For:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT
	REGIONS

Mail Stop AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

AMENDMENT AND RESPONSE TO OFFICE ACTION

This communication is responsive to the Examiner's Office Action dated February 28, 2022. Reconsideration is respectfully requested.

<u>Amendments to the Claims</u> are reflected in the listing of claims beginning on page 2 of this paper. <u>Remarks/Arguments</u> begin on page 7 of this paper.

PE2E SEARCH - Search History (Prior Art)

Ref#	Hits	Search Query	DBs	Default Operator	Plurals	British Equivalents	Time Stamp
L1	0	17/371,839	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 10:17 AM
L2	31	((("GREENTHREAD") near3 ("LLC"))).AS,AANM.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 10:18 AM
L3	29	((("RAO") near3 ("G.R") near3 ("MOHAN"))).INV.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 10:19 AM
L4	30065	H01L29/1095.cpc.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 10:19 AM
L5	669	(257/25).CCLS.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 10:19 AM
L6	56	("20010028097" "20020 195656" "20030183856 " "20070045682" "2008 0142899" "2014003499 7" "20170243876" "416 0985" "4684971" "4688 063" "4907058" "49948 87" "5835402" "602523 7" "6384431" "6465862").PN.		OR	ON	ON	2021/10/23 10:20 AM
L7	29	("5448087" "5888857" " 20030030488" "672062 2" "20030026126" "597 3575" "5262345" "2004 0027753").PN.	USOCR; FPRS; EPO; JPO; DERWENT;	OR	OFF	OFF	2021/10/23 10:20 AM
L8	12	(US-20040027753-\$ or US-20030030488-\$ or US-20140034997-\$ or US-20060049464-\$ or US-20030026126-\$ or US-20070181927-\$ or US-20070045682- \$).did. or (US-5973575- \$ or US-5262345-\$ or US-5448087-\$ or US- 6720622-\$ or US- 5888857-\$).did.	(US-PGPUB; USPAT)	OR	ON	ON	2021/10/23 10:21 AM
L9	47	("20020056883" "20020 084430" "20020102783 " "20030042511" "4160	USOCR; FPRS; EPO;	OR	OFF	OFF	2021/10/23 10:22 AM

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10:23 AM 46"(668343")"666631 USOCR: FPRS: EPO; (19747883")"567699" 10.23 AM 10:23 AM 81"(337634")"2000068000" (1974117)"(19754093")" S213988")556612"]"R 10.23 AM 10.23 AM 11:1 255 (2010783")"20020 (US-PGPUB; USPAT; 0201783")"20020 OR OFF 0FF 2021/10/23 12:1 255 (2020102783")"20030 (US-PGPUB; USPAT; 07:0217711925"]" OR OFF 0FF 2021/10/23 10:15 02:15217" 190; DERWENT; 10:57:522"]" IPO; DERWENT; 10:57:522"]" IPO; DERWENT; 10:58 AM IPO; DERWENT; 10:58 AM IPO; DERWENT; 10:58 AM IPO; DERWENT; 10:58 AM 10:23 44:175040861"]"20020036885"]"5 448067"[6737722"]"674 IPO; DERWENT; 10:57:0527"]"65 IPO; DERWENT; 10:57:057879"]"692 IPO; DERWENT; 10:57:05789"]"692 10:23 44:17634682"]"20040 0207757138"]"692 IPO; DERWENT; 10:57:0769613"]"20020 IPO; DERWENT; 10:57:07697613"]"2002 IPO; DERWENT; 10:57:07697613"]"2007 10:45:17"50262"]"20150003141"PG 2 2200013419"1" IPO; DERWENT; 10:57:0769769989"]"50 IPO; IPO; IPO; IPO; IPO; IPO; IPO; IPO;			52" "4481522" "683129 2" "20020093281" "502 9277" "20060113592" " 20020134419").PN.					
L12 271 ("2002102783"]"20030030488 USOCR: FPRS: EPC; "["6211028"]"6310366"]" 6753202"]"7115925"]"5 104124"]"6676037120 020056883"]"20020093 281"]"20150200314"]"4 347654"]"5496746"]"67 52066"]"67713813"]"2003 0042511"]"5029277"]"5 888557"]"6670544"]"67 065507"[6713813"]"2004 0027753"]"4100985"]"5 4480857"]"6670544"]"67 065507"[6713813"]"2004 0027753"]"4100985"]"5 8825"]"5637898"]"67206 22"]"574140985"]"5 8825"]"5637898"]"67206 22"]"6744117"[200700 445682"]"20020134419"] "20060113592"]"2010 001661"]"4481522"]"55 62345"]"6756616"]"693 3215"]"723044"]"201 0040622"]"20120074588 5"]"5130262"]"5797999"]"5 973575"]"6767999"]"5 973575"]"676909"]"5 973575"]"676909"]"5 973575"]"676909"]"5 973575"]"676909"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769099"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6769090"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"5 973575"]"6779000"]"6 973575"]"7 973575"]"6 9		118	46" "6683343" "669631 4" "6452086" "6472715" "6747883" "5797999" " 6670544" "2004006328 8" "4347654" "4866000" "6744117" "6754093" " 5213988" "5569612" "R E37441" "4001864" "67 56616" "5130262" "532 9144" "6706550" "6753 202" "5480816" "67138 13" "6737722" "557586	USOCR; FPRS; EPO; JPO; DERWENT;	IOR	OFF	OFF	
134419" "20070045682 USOCR; FPRS; EPO; 10:59 AM			("20020102783" "20030 026126" "20030030488 " "6211028" "6310366" " 6753202" "7115925" "8 164124" "6878603" "20 020056883" "20020093 281" "20150200314" "4 347654" "5496746" "64 52086" "6737722" "674 7883" "6780713" "2003 0042511" "5029277" "5 888857" "6670544" "67 06550" "6713813" "692 1943" "7504692" "2004 0027753" "4160985" "5 448087" "6472715" "66 83343" "6831292" "730 7327" "5569612" "5575 862" "5637898" "67206 22" "6744117" "200700 45682" "20020134419" "20060113592" "20130 001661" "4481522" "52 62345" "6756616" "693 3215" "7233044" "2001 0040622" "2002007458 5" "5130262" "5213988" "5329144" "6465862" " 6696314" "RE37441" "2 0020084430" "4001864 " "4866000" "5480816" " 5517052" "5797999" "5 973575" "6754093" "70 64385" "20120048462") .PN.	USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)				10:58 AM
	L12	271	("20020102783" "20020 134419" "20070045682	USOCR; FPRS; EPO;	OR	OFF	OFF	

	1	1		1	1	1	1
		"20040027753" "20120	IBM_TDB)				
		048462" "4160985" "43					
		47654" "5213988" "557					
		5862" "8164124" "2013					
		0001661" "5329144" "5					
		496746" "5569612" "56					
		37898" "5973575" "621					
		1028" "6683343" "6696					
		314" "6713813" "67540					
		93" "7064385" "200300					
		30488" "20070045682"					
		· · ·					
		4481522" "6753202" "2					
		0020056883" "2002008					
		4430" "20020093281" "					
		20030026126" "200300					
		42511" "4001864" "513					
		0262" "5262345" "5448					
		087" "6472715" "66705					
		44" "6720622" "678071					
		3" "6921946" "1051084					
		2" "20010040622" "200					
		20074585" "6465862" "					
		6747883" "7233044" "7					
		307327" "20030030488					
		" "20040063288" "2006					
		0113592" "2015020031					
		4" "4866000" "5029277"					
		"5480816" "5517052" "					
		5797999" "6452086" "6					
		706550" "6737722" "68					
		31292" "6878603" "711					
		5925" "9190502" "9647					
		070" "5888857" "67441					
		5" "7504692" "8421195"					
).PN.					
L13	316	("20020102783" "20020	(US-PGPUB; USPAT;	OR	OFF	OFF	2021/10/23
		134419" "20070045682					11:00 AM
		" "6310366" "RE37441"					
		"4907058" "200400277					
		53" "20080142899" "20	·····_· /				
		120048462" "4160985"					
		"4347654" "5213988" "5					
		575862" "8164124" "20					
		010028097" "4994887"					
		"6025237" "201300016					
		61" "5329144" "549674					
		6" "5569612" "5637898"					
		"5973575" "6211028" "					
		6683343" "6696314" "6					
		713813" "6754093" "70					
		64385" "20140034997"					
		"10734481" "4481522" "					
		6753202" "2002019565					
		6" "20030183856" "200					
		20056883" "200200844					
		30" "20020093281" "20					
		030026126" "20030042					
				1		1	

	-	-					
		511" "4001864" "51302 62" "5262345" "544808 7" "6472715" "6670544" "6720622" "6780713" "					
		6921946" "2017024387 6" "5835402" "2007004 5682" "10510842" "200					
		10040622" "200200745 85" "20030183856" "46 84971" "6465862" "674					
		7883" "7233044" "7307 327" "4688063" "20030 030488" "20040063288 " "20060113592" "2015					
		0200314" "4866000" "5 029277" "5480816" "55 17052" "5797999" "645 2086" "6706550" "6737					
		722" "6831292" "68786 03" "7115925" "919050 2" "9647070" "2008014 2899" "6384431" "5888 857" "6744117" "67566					
		16" "6933215" "750469 2" "8421195").PN.					
L14	319	L7 L9 L10 L11 L12 L13	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 11:01 AM
L15	10	L3 and drift	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 11:02 AM
L16	14	L2 and drift	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 11:02 AM
L17	574	(source drain source/drain) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 11:03 AM
L18	25930	H01L27/11521.cpc.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:03 AM
L19	14669	H01L27/11524.cpc.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:04 AM
L20	29711	H01L27/14643.cpc.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:04 AM
L21	11836	H01L29/36.cpc.	(US-PGPUB; USPAT;	OR	ON	ON	2021/10/23

			USOCR; FPRS; EPO; JPO; DERWENT;				11:04 AM
L22	13097	H01L29/7395.cpc.	IBM_TDB) (US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:04 AM
L23	18	L4 and L18 and L21	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:08 AM
L24	18	L4 and L18 and L20	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:10 AM
L25	18	L4 and L19 and L20	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:10 AM
L26	66	L4 and L19 and L21	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	ON	ON	2021/10/23 11:10 AM
L27	2	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive))).clm.	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 11:11 AM
L28	32	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive)))	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 11:13 AM
L30	574	(source drain source/drain) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 03:37 PM
L31	574	L30	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2021/10/23 03:37 PM
L32	1	("9647070").PN.	(US-PGPUB; USPAT)	OR	OFF	OFF	2021/10/23 04:21 PM
L33	1	("6384431").PN.	(US-PGPUB; USPAT)	OR	OFF	OFF	2021/10/23 04:21 PM
L34	3	16/947,294	(US-PGPUB; USPAT; USOCR; FIT (AU, AP,	OR	ON	ON	2022/02/23 11:02 PM

			AT, BE, BG, BR, BY, CA, CH, CN, CS, CU, CZ, DD, DE, DK, EA, EE, EP, ES, FI, FR, GB, HR, HU, ID, IE, IL, IS, IT, JP, KR, LT, LU, LV, MA, OA, RU, SU, WO, MC, MD, MY, NL, NO, NZ, PH, PL, PT, RO, RS, SE, SG, SI, SK, TH, TN, TR, TW, UA, VN); FPRS; EPO; JPO; DERWENT; IBM_TDB)				
L35	544	(source drain source\$1drain) AND drift AND ((gradient graded) near2 concentration near2 dop\$3) AND well	(US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB)	OR	OFF	OFF	2022/02/23 11:22 PM
L36	1	"11121222"	(USPAT)	OR	ON	ON	2022/03/08 09:28 PM

PE2E SEARCH - Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	British Equivalents	Time Stamp
N29	31	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive)))	(US-PGPUB; USPAT)	OR	OFF	OFF	2021/10/23 11:12 AM

Bibliographic Data

Application No: 17/371,8.	39			
Foreign Priority claimed:	OYes	O No		
35 USC 119 (a-d) conditions met:	Yes	No		Met After Allowance
Verified and Acknowledged:	/AJAY A	ARORA/		
	Examiner's	s Signature		Initials
Title:	SEMICON REGIONS		VICES W	ITH GRADED DOPANT

FILING or 371(c) DATE	CLASS	GROUP ART UNIT	ATTORNEY DOCKET NO.
07/09/2021	257	2892	GRTD60-35314
RULE			

APPLICANTS

GREENTHREAD, LLC, Dallas, TX, UNITED STATES

INVENTORS

G.R. MOHAN RAO, ALLEN, TX, UNITED STATES

CONTINUING DATA

This application is a CON of 16947294 07/27/2020 PAT 11121222 16947294 is a CON of 16717950 12/17/2019 PAT 10734481 16717950 is a CON of 15590282 05/09/2017 PAT 10510842 15590282 is a CON of 14931636 11/03/2015 PAT 9647070 14931636 is a CON of 14515584 10/16/2014 PAT 9190502 14515584 is a CON of 13854319 04/01/2013ABN 13854319 is a CON of 11622496 01/12/2007 PAT 8421195 11622496 is a DIV of 10934915 09/03/2004ABN **FOREIGN APPLICATIONS IF REQUIRED, FOREIGN LICENSE GRANTED**** 07/22/2021 **STATE OR COUNTRY** UNITED STATES

ADDRESS

MUNCK WILSON MANDALA L.L.P P.O. Drawer 800889 DALLAS, TX 75380 UNITED STATES

FILING FEE RECEIVED

\$7,160

Doc Code: DIST.E.FILE Document Description: Electronic T	Ferminal Disclaimer - Filed		PTO/SB/26 U.S. Patent and Trademark Office Department of Commerce		
Electronic Petition Request	TERMINAL DISCLAIMER TO OBVIATE A DOUBLE PATENTING REJECTION OVER A "PRIOR" PATENT				
Application Number	17371839				
Filing Date	09-Jul-2021				
First Named Inventor	G.R. MOHAN RAO				
Attorney Docket Number	GRTD60-35314				
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				
Office Action	es not obviate requirement for resp ner is not being used for a Joint Re				
Owner	-	ercent Inter			
GREENTHREAD, LLC	10	100%			
· · ·	any patent granted on the instant		isclaims, except as provided below, the n which would extend beyond the expiration		
11121222					
granted on the instant application sh	all be enforceable only for and dur	ing such p	The owner hereby agrees that any patent so eriod that it and the prior patent are commonly nd is binding upon the grantee, its successors		
application that would extend to the is presently shortened by any termina - expires for failure to pay a maintena - is held unenforceable; - is found invalid by a court of compe - is statutorily disclaimed in whole or - has all claims canceled by a reexami - is reissued; or	expiration date of the full statutory al disclaimer," in the event that saic nce fee; tent jurisdiction; terminally disclaimed under 37 CFI nation certificate;	y term of th d prior pate R 1.321;	he term of any patent granted on the instant he prior patent, "as the term of said prior patent int later: esently shortened by any terminal disclaimer.		
• Terminal disclaimer fee under 3	37 CFR 1.20(d) is included with Elec	tronic Tern	ninal Disclaimer request.		

	l certify, in accordance with 37 CFR 1.4(d)(4), that the terminal disclaimer fee under 37 CFR 1.20(d) required for this terminal disclaimer has already been paid in the above-identified application.								
Applicant claims the following fee st	atus:								
Small Entity	Small Entity								
O Micro Entity									
Regular Undiscounted									
belief are believed to be true; and fu the like so made are punishable by f	hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and he like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and hat such willful false statements may jeopardize the validity of the application or any patent issued thereon.								
THIS PORTION MUST BE COMPLETE	ED BY THE SIGNATORY OR SIGNATORIES								
I certify, in accordance with 37 CFR	1.4(d)(4) that I am:								
 An attorney or agent registered this application 	d to practice before the Patent and Trademark Office who is of record in								
Registration Number30646	5								
 A sole inventor 									
A joint inventor; I certify that I power of attorney in the applic	am authorized to sign this submission on behalf of all of the inventors as evidenced by the cation								
A joint inventor; all of whom a	A joint inventor; all of whom are signing this request								
Signature	/Gregory M. Howison, Reg. #30646/								
Name	Gregory M. Howison								

*Statement under 37 CFR 3.73(b) is required if terminal disclaimer is signed by the assignee (owner). Form PTO/SB/96 may be used for making this certification. See MPEP § 324.

Electronic Patent Application Fee Transmittal							
Application Number:	173	371839					
Filing Date:	09-	Jul-2021					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. MOHAN RAO						
Filer:	Gregory Michael Howison/Joselyn Rodriguez						
Attorney Docket Number:	GR	TD60-35314					
Filed as Large Entity							
Filing Fees for Utility under 35 USC 111(a)							
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)		
Basic Filing:			·				
STATUTORY OR TERMINAL DISCLAIMER		1814	1	170	170		
Pages:							
Claims:							
Miscellaneous-Filing:							
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
	Total in USD (\$)		170	

Doc Code: DISQ.E.FILE Document Description: Electronic Terminal Disclaimer – Approved

Application No.: 17371839

Filing Date: 09-Jul-2021

Applicant/Patent under Reexamination: RAO

Electronic Terminal Disclaimer filed on March 15, 2022

APPROVED

This patent is subject to a terminal disclaimer

DISAPPROVED

Approved/Disapproved by: Electronic Terminal Disclaimer automatically approved by EFS-Web

U.S. Patent and Trademark Office
Electronic A	Electronic Acknowledgement Receipt							
EFS ID:	45218088							
Application Number:	17371839							
International Application Number:								
Confirmation Number:	2197							
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS							
First Named Inventor/Applicant Name:	G.R. MOHAN RAO							
Customer Number:	25883							
Filer:	Gregory Michael Howison/Joselyn Rodriguez							
Filer Authorized By:	Gregory Michael Howison							
Attorney Docket Number:	GRTD60-35314							
Receipt Date:	15-MAR-2022							
Filing Date:	09-JUL-2021							
Time Stamp:	15:55:28							
Application Type:	Utility under 35 USC 111(a)							

Payment information:

Submitted with Payment	yes				
Payment Type	DA				
Payment was successfully received in RAM	\$170				
RAM confirmation Number	E20223EF55242618				
Deposit Account	500208				
Authorized User	Joselyn Rodriguez				
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:					
37 CFR 1.17 (Patent application and reexamination processing fees)					

37 CFR 1.21 (Miscellaneous fees and charges)

File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.
			41407		
1	Terminal Disclaimer-Filed (Electronic)	eTerminal-Disclaimer.pdf	ce154e2964899d218ef9dae5a3347ca4e03 ea568	no	2
Warnings:			Į I		
Information:					
			38134		
2	Fee Worksheet (SB06)	fee-info.pdf	3ae58ae3a 199f0bc9be08814725ee818db8 0dd20	no	2
Warnings:	Į		- <u> </u>		
Information:					
		Total Files Size (in bytes): 7	9541	
	edgement Receipt evidences receipt I by the applicant, and including pag				
Post Card, as <u>New Applicat</u> If a new appli 1.53(b)-(d) an Acknowledge <u>National Stac</u> If a timely sul	described in MPEP 503. tions Under 35 U.S.C. 111 faction is being filed and the applicat ad MPEP 506), a Filing Receipt (37 CFF ement Receipt will establish the filing ge of an International Application und omission to enter the national stage of d other applicable requirements a Fo	ion includes the necessary R 1.54) will be issued in due g date of the application. <u>der 35 U.S.C. 371</u> of an international applicat	components for a filin course and the date s ion is compliant with t	g date (see hown on th the conditic	37 CFR is ons of 35

P	Under the Paperwork Reduction Act of 1995, no persons are required to PATENT APPLICATION FEE DETERMINATION RECORD Appl Substitute for Form PTO-875 Appl							nd to a collection of informat on or Docket Number 17/371,839	ion unless it displays a Filing Date 07/09/2021	To be Mailed
ENTITY: 🗹 LARGE 🗌 SMALL 🗌 MICRO APPLICATION AS FILED - PART I										
	(Column 1) (Column 2) FOR NUMBER FILED NUMBER EXTRA									
	FOR BASIC FEE		NUI			NUMBER EXTRA		RATE (\$)	-	FEE (\$)
	(37 CFR 1.16(a), (b), c	or (c))		N/A		N/A		N/A		
_	SEARCH FEE (37 CFR 1.16(k), (i), or			N/A		N/A		N/A		
	EXAMINATION FEE (37 CFR 1.16(o), (p), c			N/A		N/A		N/A		
	TAL CLAIMS CFR 1.16(i))			mir	ius 20 = *			x \$100 =		
	EPENDENT CLAIM CFR 1.16(h))	S		m	inus 3 = *			x \$480 =		
APPLICATION SIZE FEE (37 CFR 1.16(s)) If the specification and drawings exceed 100 sheets of paper, the application size fee due is \$310 (\$155 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).					\$155 or					
	MULTIPLE DEPENI	DENT CLAI	M PRES	SENT (37	CFR 1.16(j))					
* If th	ne difference in co	olumn 1 is	less th	an zero,	enter "0" in colu	mn 2.		TOTAL		
					APPLICAT	ION AS AMEI	NDED - P	ART II		
		(Colum	n 1)		(Column 2)	(Column 3)			
ENDMENT	03/04/2022	CLAIMS REMAINII AFTER AMENDM			HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EX	TRA	RATE (\$) ADDITIONAL FE		IONAL FEE (\$)
M	Total (37 CFR 1.16(i))	* 30		Minus	** 30	= 0		x \$100 =		0
EN	Independent (37 CFR 1.16(h))	*2		Minus	*** 3	= 0		x \$480 =	480 = 0	
AM	Application S	Size Fee (3	37 CFF	R 1.16(s))					
	FIRST PRES 1.16(j))	SENTATIC	ON OF	MULTIP	LE DEPENDEN	T CLAIM (37 CF	R			
	(177							TOTAL ADD'L FE	E	0
		(Colum	<u> </u>		(Column 2)	(Column 3)			
Τ		CLAIM REMAIN AFTEI AMENDM	ING R		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EX	TRA	RATE (\$)	ADDIT	IONAL FEE (\$)
ЧË	Total (37 CFR 1.16(i))	*		Minus	**	=		x \$0 =		
AMENDMENT	Independent (37 CFR 1.16(h))	*		Minus	***	=		x \$0 =		
ME	Application S	Size Fee (3	37 CFF	R 1.16(s))					
A	FIRST PRE	SENTATIC	ON OF	MULTIP	LE DEPENDEN	T CLAIM (37 CF	R			
								TOTAL ADD'L FE	E	
* If t	he entry in column 1	1 is less that	n the er	ntry in colu	umn 2, write "0" in	column 3.		LIE		
	the "Highest Numbe						".	/THERESA D	DAWKINS/	
	f the "Highest Numb									
The	The "Highest Number Previously Paid For" (Total or Independent) is the highest number found in the appropriate box in column 1.									

This collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS

ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	G. R. Mohan Rao
Serial No.:	17/371,839
Confirmation No.:	2197
Filed:	July 9, 2021
Group:	2892
Examiner:	Ajay Arora
For:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT
	REGIONS

Mail Stop AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

AMENDMENT AND RESPONSE TO OFFICE ACTION

This communication is responsive to the Examiner's Office Action dated February 28, 2022. Reconsideration is respectfully requested.

<u>Amendments to the Claims</u> are reflected in the listing of claims beginning on page 2 of this paper. <u>Remarks/Arguments</u> begin on page 7 of this paper.

In the Claims

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This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) An electronic system, the system comprising:

at least one semiconductor device, the at least one semiconductor device including: a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed;

> a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the first and second active regions towards an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface towards the area of the substrate where there are no active regions, wherein at least some of the transistors form digital logic of the semiconductor device.

2. (Previously Presented) The system of Claim 1, wherein the substrate of the at least one semiconductor device is a p-type substrate.

3. (Previously Presented) The system of Claim 1, wherein the substrate of the at least one semiconductor device has epitaxial silicon on top of a nonepitaxial substrate.

4. (Previously Presented) The system of Claim 1, wherein the first active region and second active region of the at least one semiconductor device contain digital logic formed by one of either p-channel and n-channel devices.

5. (Previously Presented) The system of Claim 1, wherein the first active region and second active region of the at least one semiconductor device contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.

6. (Previously Presented) The system of Claim 1, wherein the first active region and second active region of the at least one semiconductor device are each separated by at least one isolation region.

7. (Previously Presented) The system of Claim 1, wherein the graded dopant is fabricated with an ion implantation process.

8. (Previously Presented) The system of Claim 1, wherein the first and second active regions of the at least one semiconductor device are formed adjacent the first surface of the substrate of the at least one semiconductor device.

9. (Previously Presented) The system of Claim 1, wherein dopants of the graded dopant concentration in the first active region or the second active region of the at least one semiconductor device are either p-type or n-type.

10. (Previously Presented) The system of Claim 1, wherein dopants of the graded dopant concentration in the first active region of the at least one semiconductor device are both p-type and n-type.

11. (Previously Presented) The system of Claim 1, wherein dopants of the graded dopant concentration in the second active region of the at least one semiconductor device are both p-type and n-type.

12. (Previously Presented) The system of Claim 1, wherein dopants of the graded dopant region in the well region of the at least one semiconductor device are both p-type and n-type.

13. (Previously Presented) The system of claim 1, wherein the transistors which can be formed in the first and second active regions of the at least one semiconductor device are CMOS digital logic transistors requiring at least a source, a drain, a gate and a channel.

14. (Previously Presented) The system of Claim 1, wherein the at least one semiconductor device is a dynamic random access memory (DRAM).

15. (Previously Presented) The system of Claim 1, wherein the at least one semiconductor device is a complementary metal oxide semiconductor (CMOS) with a nonepitaxial substrate.

16. (Previously Presented) The system of Claim 1, wherein the at least one semiconductor device is a flash memory.

17. (Previously Presented) The system of Claim 1, wherein the at least one semiconductor device comprises digital logic and capacitors.

18. (Previously Presented) The system of Claim 1, wherein the at least one semiconductor device is a central processing unit.

19. (Previously Presented) The system of Claim 1, wherein the at least one semiconductor device is an image sensor.

20. (Previously Presented) The system of Claim 1, wherein each of the first and second active regions of the at least one semiconductor device are in the lateral or vertical direction.

21. (Previously Presented) An electronic system, comprising:

at least one semiconductor device, the at least one semiconductor device including: a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface of the substrate with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed in the surface thereof;

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Page 4 of 8

a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed in the surface thereof;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the surface to an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface to the area of the substrate where there are no active regions, and wherein the graded dopant concentration is linear, quasilinear, error function, complementary error function, or any combination thereof.

22. (Previously Presented) The system of Claim 21, wherein the substrate of the at least one semiconductor device is an n-type substrate.

23. (Previously Presented) The system of Claim 21, wherein the substrate of the at least one semiconductor device is a p-type substrate.

24. (Previously Presented) The system of Claim 21, wherein the substrate of the at least one semiconductor device has epitaxial silicon on top of a nonepitaxial substrate.

25. (Previously Presented) The system of Claim 21, wherein the first active region and second active region of the at least one semiconductor device contain at least one of either p-channel and n-channel devices.

26. (Previously Presented) The system of Claim 21, wherein the first active region and second active region of the at least one semiconductor device contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.

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27. (Previously Presented) The system of Claim 21, wherein the first active region and second active region of the at least one semiconductor device are each separated by at least one isolation region.

28. (Previously Presented) The system of Claim 21, wherein dopants of the graded dopant concentration in the first active region or the second active region of the at least one semiconductor device are either p-type or n-type.

29. (Previously Presented) The system of Claim 21, wherein dopants of the graded dopant concentration in the first active region of the at least one semiconductor device are both p-type and n-type.

30. (Previously Presented) The system of Claim 21, wherein dopants of the graded dopant concentration in the second active region of the at least one semiconductor device are both p-type and n-type.

REMARKS

Applicant has carefully reviewed the Office Action dated February 28, 2022. Reconsideration and favorable action is respectfully requested.

Claims 1-30 are rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 1-30 of U.S. Patent No. 11121222. A Terminal Disclaimer is submitted concurrently with this response with respect to U.S. Patent No. 11121222.

Applicant has now made an earnest attempt in order to place this case in condition for allowance. For the reasons stated above, Applicant respectfully requests full allowance of the claims as amended.

If any issues arise, or if the Examiner has any suggestions for expediting allowance of this Application, the Applicant respectfully invites the Examiner to contact the undersigned at the telephone number indicated below or at whowison@munckwilson.com.

Recognizing that Internet communications are not secure, Applicant hereby authorizes the USPTO to communicate with the undersigned and practitioners in accordance with 37 CFR 1.33 and 37 CFR 1.34 concerning any subject matter of this application by video conferencing, instant messaging, or electronic mail. Applicant understands that a copy of these communications will be made of record in the application file.

Please charge any additional fees or deficiencies in fees or credit any overpayment to Deposit Account No. 50-0208/GRTD60-35314.

Respectfully submitted, MUNCK WILSON MANDALA, LLP Attorneys for Applicant

/William G. Howison, Reg. #66850/

William G. Howison Registration No. 66,850

WGH/als

P.O. Drawer 800889 Dallas, Texas 75380 Tel: 972-628-3600 Fax: 972-628-3616 March 4, 2022

Electronic Acknowledgement Receipt						
EFS ID:	45143918					
Application Number:	17371839					
International Application Number:						
Confirmation Number:	2197					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	G.R. MOHAN RAO					
Customer Number:	25883					
Filer:	William G. Howison					
Filer Authorized By:						
Attorney Docket Number:	GRTD60-35314					
Receipt Date:	04-MAR-2022					
Filing Date:	09-JUL-2021					
Time Stamp:	12:32:31					
Application Type:	Utility under 35 USC 111(a)					

Payment information:

Submitted with Payment no								
File Listing:								
Document Number	Document Description File Name I The State Sta							
			104672					
1		GRT35314AMD.pdf	b7e71d2fc480d3afb876e1eed26332baeb2 bb3e6	yes	8			

	Multipart Description/PDF files in .zip description								
	Document Description	Start	End						
	Response After Final Action	1	1						
	Claims	2	6						
	Applicant Arguments/Remarks Made in an Amendment	7	8						
Warnings:									
Information:									
	Total Files Size (in bytes):	104	4672						

This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

Doc Code: DIST.E.FILE Document Description: Electronic		PTO/SB/26 U.S. Patent and Trademark Office Department of Commerce						
Electronic Petition Request	TERMINAL DISCLAIMER TO OBVIATE A DOUBLE PATENTING REJECTION OVER A "PRIOR" PATENT							
Application Number	17371839							
Filing Date	09-Jul-2021							
First Named Inventor	G.R. MOHAN RAO							
Attorney Docket Number	GRTD60-35314							
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS							
Filing of terminal disclaimer do Office Action	es not obviate requirement for resp	oonse unde	er 37 CFR 1.111 to outstanding					
This electronic Terminal Disclai	mer is not being used for a Joint Re	search Agr	eement.					
Owner	Ρε	ercent Inter	rest					
VERVAIN, LLC	1(100%						
	f any patent granted on the instant		isclaims, except as provided below, the n which would extend beyond the expiration					
11121222								
granted on the instant application sl	nall be enforceable only for and dur	ring such p	The owner hereby agrees that any patent so eriod that it and the prior patent are commonly nd is binding upon the grantee, its successors					
In making the above disclaimer, the owner does not disclaim the terminal part of the term of any patent granted on the instant application that would extend to the expiration date of the full statutory term of the prior patent, "as the term of said prior patent is presently shortened by any terminal disclaimer," in the event that said prior patent later: - expires for failure to pay a maintenance fee; - is held unenforceable; - is found invalid by a court of competent jurisdiction; - is statutorily disclaimed in whole or terminally disclaimed under 37 CFR 1.321; - has all claims canceled by a reexamination certificate;								
		-	esently shortened by any terminal disclaimer.					
• Terminal disclaimer fee under 37 CFR 1.20(d) is included with Electronic Terminal Disclaimer request.								

	I certify, in accordance with 37 CFR 1.4(d)(4), that the terminal disclaimer fee under 37 CFR 1.20(d) required for this terminal disclaimer has already been paid in the above-identified application.								
Applica	nt claims the following fee sta	atus:							
🔿 Sn	nall Entity								
Ом	icro Entity								
● Re	egular Undiscounted								
belief ai the like	hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and he like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and hat such willful false statements may jeopardize the validity of the application or any patent issued thereon.								
THIS P	PORTION MUST BE COMPLETE	D BY THE SIGNATORY OR SIGNATORIES							
l certif	y, in accordance with 37 CFR	1.4(d)(4) that I am:							
	n attorney or agent registered is application	to practice before the Patent and Trademark Office who is of record in							
	Registration Number 66850								
<u>О</u> А	sole inventor								
	joint inventor; I certify that I a ower of attorney in the applic	im authorized to sign this submission on behalf of all of the inventors as evidenced by the ation							
O A.	 A joint inventor; all of whom are signing this request 								
Signat	ture	/William G. Howison, Reg. #66850/							
Name		William G. Howison							

*Statement under 37 CFR 3.73(b) is required if terminal disclaimer is signed by the assignee (owner). Form PTO/SB/96 may be used for making this certification. See MPEP § 324.

Electronic Patent Application Fee Transmittal							
Application Number:	17:	371839					
Filing Date:	09-	09-Jul-2021					
Fitle of Invention: SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS							
First Named Inventor/Applicant Name:	G.F	R. MOHAN RAO					
Filer:	Wi	lliam G. Howison					
Attorney Docket Number:	GR	TD60-35314					
Filed as Large Entity							
Filing Fees for Utility under 35 USC 111(a)							
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)		
Basic Filing:							
STATUTORY OR TERMINAL DISCLAIMER		1814	1	170	170		
Pages:			·				
Claims:							
Miscellaneous-Filing:							
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
	Tot	al in USD) (\$)	170

Doc Code: DISQ.E.FILE Document Description: Electronic Terminal Disclaimer – Approved

Application No.: 17371839

Filing Date: 09-Jul-2021

Applicant/Patent under Reexamination: RAO

Electronic Terminal Disclaimer filed on March 4, 2022

APPROVED

This patent is subject to a terminal disclaimer

DISAPPROVED

Approved/Disapproved by: Electronic Terminal Disclaimer automatically approved by EFS-Web

U.S. Patent and Trademark Office

Electronic Acknowledgement Receipt		
EFS ID:	45143893	
Application Number:	17371839	
International Application Number:		
Confirmation Number:	2197	
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS	
First Named Inventor/Applicant Name:	G.R. MOHAN RAO	
Customer Number:	25883	
Filer:	William G. Howison	
Filer Authorized By:		
Attorney Docket Number:	GRTD60-35314	
Receipt Date:	04-MAR-2022	
Filing Date:	09-JUL-2021	
Time Stamp:	12:30:37	
Application Type:	Utility under 35 USC 111(a)	

Payment information:

Submitted with Payment	yes	
Payment Type	CARD	
Payment was successfully received in RAM	\$170	
RAM confirmation Number	E202234C30322647	
Deposit Account 500208		
Authorized User William Howison		
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:		
37 CFR 1.16 (National application filing, search, and examination fees)		

37 CFR 1.17 (Patent application and reexamination processing fees)

37 CFR 1.19 (Document supply fees)

37 CFR 1.21 (Miscellaneous fees and charges)

File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.
			41402		
1	Terminal Disclaimer-Filed (Electronic)	eTerminal-Disclaimer.pdf	4d991e41980f21eb9155bf9068f5448b37bf 6f71	no	2
Warnings:			ļ I		
Information:					
			38019		
2	Fee Worksheet (SB06)	fee-info.pdf	8ce81bc4d9c0cfb1086a96d9c0b9a84fc97e 97bf	no	2
Warnings:			11	I	
Information:					
		Total Files Size (in bytes): 7	9421	
characterized Post Card, as <u>New Applicat</u> If a new appli 1.53(b)-(d) ar	edgement Receipt evidences receipt by the applicant, and including pag described in MPEP 503. tions Under 35 U.S.C. 111 ication is being filed and the applicat ind MPEP 506), a Filing Receipt (37 CF	e counts, where applicable	. It serves as evidence components for a filin	of receipt si g date (see	milar to 37 CFR
<u>National Stac</u> If a timely sul U.S.C. 371 an	ement Receipt will establish the filing ge of an International Application un omission to enter the national stage d other applicable requirements a Fo e submission under 35 U.S.C. 371 wil	g date of the application. <u>der 35 U.S.C. 371</u> of an international applicat orm PCT/DO/EO/903 indicat	ing acceptance of the	the conditic application	ons of 35

UNIT	ed States Patent		UNITED STATES DEPARTMENT United States Patent and Trade Address: COMMISSIONER FOR P P.O. Box 1450 Alexandria, Virginia 22313-145 www.uspto.gov	emark Office ATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197
	7590 02/28/2022 SON MANDALA L.L.P		EXAM	IINER
P.O. Drawer 80 DALLAS, TX	0889		ARORA	A, AJAY
2			ART UNIT	PAPER NUMBER
			2892	
			NOTIFICATION DATE	DELIVERY MODE
			02/28/2022	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com admin@dalpat.com eofficeaction@appcoll.com

	Application No.	Applicant(s)		
	17/371,839	RAO, G.R. N	IOHAN		
Office Action Summary	Examiner	Art Unit	AIA (FITF) Status		
	AJAY ARORA	2892	No		
The MAILING DATE of this communication appears on the cover sheet with the correspondence address					
Period for Reply					
A SHORTENED STATUTORY PERIOD FOR REPL	Y IS SET TO EXPIRE <u>3</u> MONTH	S FROM TH	E MAILING		
DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1	26(a) In no event, however, may a raphy ha tin	ably filed offer SIX	(6) MONTHS from the mailing		
date of this communication.		-			
 If NO period for reply is specified above, the maximum statutory period v Failure to reply within the set or extended period for reply will, by statute 	, cause the application to become ABANDONE	ED (35 U.S.C. § 13	33).		
Any reply received by the Office later than three months after the mailing adjustment. See 37 CFR 1.704(b).	g date of this communication, even if timely file	d, may reduce any	earned patent term		
Status					
1) Responsive to communication(s) filed on 12	(1/2021				
□ A declaration(s)/affidavit(s) under 37 CFR					
	\Box This action is non-final.				
3) An election was made by the applicant in res		ent set forth	during the interview		
on; the restriction requirement and ele					
4) Since this application is in condition for allow	ance except for formal matters	, prosecutio	n as to the merits is		
closed in accordance with the practice under	<i>Ex parte Quayle</i> , 1935 C.D. 1	1, 453 O.G.	213.		
Disposition of Claims*					
5) 🗹 Claim(s) 1-30 is/are pending in the app	lication.				
5a) Of the above claim(s) is/are withdu					
6) Claim(s) is/are allowed.					
7) \checkmark Claim(s) <u>1-30</u> is/are rejected.					
	ad/ar alactica requirement				
9) Claim(s) are subject to restriction a * If any claims have been determined <u>allowable</u> , you may be el	•	secution High	way program at a		
participating intellectual property office for the corresponding a	-	-	iway piogram at a		
http://www.uspto.gov/patents/init_events/pph/index.jsp or send					
Application Papers		-			
10) The specification is objected to by the Exami	ner				
11) The drawing(s) filed on is/are: a) a		/ the Evamin	lor		
Applicant may not request that any objection to the d	• • •				
Replacement drawing sheet(s) including the correction					
	3(,),				
Priority under 35 U.S.C. § 119 12) Acknowledgment is made of a claim for forei	an priority under 35 U.S.C. & 1	19(a)-(d) or ((f)		
Certified copies:			.').		
a)□ All b)□ Some** c)□ None of t	the:				
1. Certified copies of the priority docur	nents have been received.				
2. Certified copies of the priority docur		oplication No)		
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).					
** See the attached detailed Office action for a list of the certifi	ed copies not received.				
Attachment(s)					
1) Notice of References Cited (PTO-892)	3) Interview Summar				
2) Information Disclosure Statement(s) (PTO/SB/08a and/or PTO/S	B/08b) Paper No(s)/Mail E 4)	Jate			
Paper No(s)/Mail Date U.S. Patent and Trademark Office	·/·				

DETAILED ACTION

Notice of Pre-AIA or AIA Status

1. The present application is being examined under the pre-AIA first to invent provisions.

Double Patenting

2. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. A nonstatutory double patenting rejection is appropriate where the conflicting claims are not identical, but at least one examined application claim is not patentably distinct from the reference claim(s) because the examined application claim is either anticipated by, or would have been obvious over, the reference claim(s). See, e.g., *In re Berg*, 140 F.3d 1428, 46 USPQ2d 1226 (Fed. Cir. 1998); *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) or 1.321(d) may be used to overcome an actual or provisional rejection based on nonstatutory double patenting provided the reference application or patent either is shown to be commonly owned with the examined application, or claims an invention made as a result of activities undertaken within the scope of a joint research agreement. See MPEP § 717.02 for applications subject to examination under the first inventor to file provisions of the AIA as explained in MPEP § 2159. See MPEP § 2146 *et seq.* for applications not subject to examination under the first inventor to file provisions of the AIA. A terminal disclaimer must be signed in compliance with 37 CFR 1.321(b).

The USPTO Internet website contains terminal disclaimer forms which may be used. Please visit www.uspto.gov/patent/patents-forms. The filing date of the application in which the form is filed determines what form (e.g., PTO/SB/25, PTO/SB/26, PTO/AIA/25, or PTO/AIA/26) should be used. A web-based eTerminal Disclaimer may

be filled out completely online using web-screens. An eTerminal Disclaimer that meets all requirements is auto-processed and approved immediately upon submission. For more information about eTerminal Disclaimers, refer to

www.uspto.gov/patents/process/file/efs/guidance/eTD-info-l.jsp.

3. Claims 1-30 are rejected on the ground of nonstatutory double patenting as being unpatentable over claims 1-30 of U.S. Patent No. US 11121222. Although the claims at issue are not identical, they are not patentably distinct from each other because the claims of the current application are only different in that they claim "An electronic system, the system comprising at least one semiconductor device, the at least one semiconductor device including.." (see, for example, base claims 1 and 21) compared to claims 1-30 of U.S. Patent No. 11121222 (see for example, base claims 1 and 21), which claims a specific type of electronic system that comprises at least one semiconductor device; i.e. a VLSI semiconductor device. Thus, claims 1-30 of the

current application are broader in scope compared to the corresponding claims 1-30 of U.S. Patent No. 11121222, as explained above, but are otherwise similar.

Art Based Rejection

4. No art based rejection has been provided, as the prior art does not teach or suggest the features of claims 1-30. The closest prior art is Hong (US 2007/0045682), hereinafter Hong, especially see Figures 4A-4D and 5A-5C and para 26-32 (as also explained in Notice of Allowance of 8/11/2021 for parent application 16/947,294).

Conclusion

 Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, THIS ACTION IS MADE FINAL. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY ARORA whose telephone number is (571)272-8347. The examiner can normally be reached 9 AM - 5 PM.

Examiner interviews are available via telephone, in-person, and video conferencing using a USPTO supplied web-based collaboration tool. To schedule an interview, applicant is encouraged to use the USPTO Automated Interview Request (AIR) at http://www.uspto.gov/interviewpractice.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on 5712721708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of published or unpublished applications may be obtained from Patent Center. Unpublished application information in Patent Center is available to registered users. To file and manage patent submissions in Patent Center, visit: https://patentcenter.uspto.gov. Visit https://www.uspto.gov/patents/apply/patentcenter for more information about Patent Center and https://www.uspto.gov/patents/docx for information about filing in DOCX format. For additional questions, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY ARORA/ Primary Examiner, Art Unit 2892



	Application/Control No.	Applicant(s)/Patent Under Reexamination
	17/371,839	RAO, G.R. MOHAN
Examiner		Art Unit
	AJAY ARORA	2892

CPC - Searched*		
Symbol	Date	Examiner
H01L 29/1095	10/23/2021	AKA

CPC Combination Sets - Searched*			
Symbol Date Examiner			

US Classification - Searched*			
Class	Subclass	Date	Examiner
257	25	10/23/2021	AKA

* See search history printout included with this form or the SEARCH NOTES box below to determine the scope of the search.

Search Notes		
Search Notes	Date	Examiner
Inventor search	10/23/2021	AKA
Assignee search	10/23/2021	AKA
References for all parent applications (10/934,915; 11/622,496; 15/ 590,282; 16/717950 and 16/947294) considered	10/23/2021	AKA
.clm. interference search	10/23/2021	AKA
EAST search history report	10/23/2021	AKA
Revised EAST search history report	02/23/2022	AKA

/AJAY ARORA/ Primary Examiner, Art Unit 2892



	Application/Control No.	Applicant(s)/Patent Under Reexamination
17/371,839 RAO, G.R. MOHAN		RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY ARORA	2892

Interference Search			
US Class/CPC Symbol	US Subclass/CPC Group	Date	Examiner
H01L	29/1095	10/23/2021	АКА
257	25	10/23/2021	AKA

/AJAY ARORA/ Primary Examiner, Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination	
Index of Claims	17/371,839	RAO, G.R. MOHAN	
	Examiner	Art Unit	
	AJAY ARORA	2892	

•	Rejected	,	- Cancelled	N	Non-Elected	Α	Appeal
=	Allowed		- Restricted	Ι	Interference	0	Objected

					CLAIMS					
Clair	ms renumbe	ered in the sa	ame order as	s presented	by applicar	t	🗌 СРА	🗌 Т.С	D. 🗌	R.1.47
CL	AIM					DATE				
Final	Original	10/23/2021	02/23/2022							
	1	√	1							
	2	✓	\checkmark							
	3	1	\checkmark							
	4	✓	\checkmark							
	5	√	\checkmark							
	6	~	1							
	7	~	~							
	8	1	1							
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	19	1	<i>√</i>							
	20	✓ ✓	<i>√</i>							
	21	✓ ✓	<i>√</i>							
	22	1	1							
	23	1	1							<u> </u>
	24	1	1							
	25	✓ ✓	✓ ✓							
	26 27	-								
	27	1								
	28	✓ ✓	✓ ✓							
	30	✓ ✓	\checkmark							
	1 30	√	✓							

Part of Paper No.: 20220223

Ref# British Hits Default Plurals Search Query DBs Operator Equivalents L34 3 ON ON 16/947,294 (US-PGPUB; USPAT; OR USOCR; FIT (AU, AP, AT, BE, BG, BR, BY, CA, CH, CN, CS, CU, CZ, DD, DE, DK, EA, EE, EP, ES, FI, FR, GB, HR, HU, ID, IE, IL, IS, IT, JP, KR, LT, LU, LV, MA, OA, RU, SU, WO, MC, MD, MY, NL, NO, NZ, PH, PL, PT, RO, RS, SE, SG, SI, SK, TH, TN, TR, TW, UA, VN); FPRS; EPO; JPO; DERWENT; IBM_TDB) L35 544 (source drain (US-PGPUB; USPAT; OR OFF OFF source\$1drain) AND USOCR; FPRS; EPO; drift AND ((gradient JPO; DERWENT;

IBM_TDB)

PE2E SEARCH - Search History (Prior Art)

PE2E SEARCH - Search History (Interference)

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concentration near2 dop\$3) AND well

There are no Interference searches to show.

Time Stamp

2022/02/23

2022/02/23

11:22 PM

11:02 PM

UNITED STATES PATENT AND TRADEMARK OFFICE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov							
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.			
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197			
	7590 01/31/2022 SON MANDALA L.L.P	EXAMINER					
P.O. Drawer 80 DALLAS, TX	00889		ARORA	A, AJAY			
2			ART UNIT	PAPER NUMBER			
			2892				
			NOTIFICATION DATE	DELIVERY MODE			
			01/31/2022	ELECTRONIC			

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com admin@dalpat.com eofficeaction@appcoll.com UNITED STATES PATENT AND TRADEMARK OFFICE



Commissioner for Patents United States Patent and Trademark Office P.O. Box 1450 Alexandria, VA 22313-1450 www.uspto.gov

In re Application of	
RAO, G.R. MOHAN	
Application No. 17/371,839	
Filed: 9 Jul 2021	
For: SEMICONDUCTOR DEVICES WITH	
GRADED DOPANT REGIONS	

DECISION ON PETITION

This is a decision on the petition under 37 CFR 1.182 filed October 19, 2021, to expunge an assignment previously recorded against the above-identified application. In particular, the petitioner requests that Assignment 2, i.e., from Greenthread, LLC to Vervain, LLC be expunged.

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The petition to expunge the assignment documents is **DISMISSED**. This is not a final agency action.

As discussed in the *Manual of Patent Examining Procedure* (MPEP) § 323.01(d), petitions to correct, modify or "expunge" assignment records are **rarely** granted. Such petitions are granted only if the petitioner can prove that:

- (A) the normal corrective procedures outlined in MPEP § 323.01(a) through § 323.01(c) will not provide the petitioner with adequate relief; and
- (B) the integrity of the assignment records will not be affected by granting the petition.

The petition has not proven either item (A) or (B).

In regard to item (A), petitioner asserts that the corrective procedures outlined in MPEP § 323.01(a) through § 323.01(c) will not provide adequate relief. In particular, petitioner argues that MPEP § 323.01(a) and (b) do not apply because the recordation error is not a typographical error and matches the cover sheet. Further, petitioner argues that MPEP § 323.01(c) does not apply because the assignment was not improperly filed and recorded by another person against the above-identified application. These arguments are not persuasive as the corrective procedures outlined in MPEP § 323.01(a) through § 323.01(c) are not limited to only minor or typographical errors in filing. A corrective document may be recorded as set forth below.

Furthermore, in regard to item (B), petitioner contends that the integrity of the assignment records will not be affected by the desired expungement. However, the removal of a document in its entirety, as requested, will affect the assignment records. The integrity of the records is recognized as separate from the chain of title. Expungement would prevent the records from being searchable in the Assignment Historical Database or otherwise available to the public, which may be necessary for a competent authority to determine the proper chain of title. Moreover, the expungement requested involves a validity determination by the USPTO regarding the information to be expunged, which may impact ownership claims on the related patent. The USPTO, however, has no authority to decide ownership issues. See Cedars-Sinai Medical Center v. Watkins, 11F.3d 1573, 1581 n.10, 29 USPQ 2d 1188, 1194 n.10 (Fed. Cir. 1993), cert. denied, 114 S. Ct. (1994). Rather, state law governs contractual obligations, including patent assignment agreements. See Intellectual Ventures I LLC v. Erie Indem. Co., 121 USPQ2d 1928, 1930 (Fed. Cir. 2017); In re Haines, 1900 C.D. 102, 103 (Comm'r Pat. 1900). While the ownership of patent rights is typically a question exclusively for state courts, the question of whether contractual language effects a present assignment agreement of patent rights, or an agreement to assign rights in the future, is resolved by Federal Circuit law. See Abraxis Bioscience Inc. v. Navinta LLC, 96 USPQ2d 1977, 1981 (Fed. Cir. 2010); Speedplay, Inc. v. Bebpo, Inc., 211 F.3d 1245, 1253 [53USPQ2d 1984] (Fed. Cir. 2000).

35 U.S.C. § 261 provides the USPTO with only the limited authority to maintain the assignment records, and does not grant the USPTO with the authority to remove documents.

Petitioner should note that, as discussed in MPEP § 323.01(d),

"Even if a petition to "expunge" a document is granted with respect to a particular application or patent, the image of the recorded document will remain in the records of the Assignment Services Division at the same reel and frame number, and the image will appear when someone views that reel and frame number."

In the context of the assignment records, "expunge" does not mean that a document will be removed in its entirety. Rather, "expunge" means that a document containing sensitive information, such as a Social Security Number, may be replaced in the electronically searchable records with a redacted copy of the same document. The original document will remain in the assignment records at the reel/frame number given without redaction. Through "expungement," the electronic links between the document and the application will be deleted so the original document is no longer available through an electronic search.

As background, the USPTO simply acts in a ministerial capacity in recording documents that have been submitted for recordation. *See* 35 USC 261 and 37 CFR 3.11. However, the recording of a document pursuant to 37 CFR 3.11 is **not** a determination by the USPTO of the validity of the document *per se* or the effect that document has on the title to a patent or application. *See* 37 CFR 3.54. Moreover, it is USPTO policy to maintain a complete history of claimed interests in a

given property, and, as such, a recorded assignment document will be retained, even if it is subsequently found to be invalid. *In re Raney*, 24 USPQ2d 1713 (Comm'r Pat. 1992).

Here, petitioner seeks an extraordinary remedy, properly addressed under 37 CFR 1.182. The USPTO will not normally resort to an extraordinary remedy under 37 CFR 1.182 if the rules of practice and the procedures before the USPTO already provide an avenue for the requested relief. *See Cantello v. Rasmussen*, 220 USPQ 664, (Comm'r Pat. 1982).

As set forth in MPEP § 323, an error in a recorded assignment is not corrected by expunging the previous document, but by simply submitting a "corrective document" that explains the nature of the recorded document so as to clarify the assignment records. "Corrective documents" are not limited to assignments, but include any documents affecting title to a patent or application. *See* MPEP § 313. This would include an explanation of the recorded document so as to clarify the assignment records document?" submission and indicate the reel and frame number where the incorrectly recorded assignment document appears. The corrective document will be recorded and given a new reel and frame number and recording date. The recording fee set forth in 37 CFR 1.21(h) is required for each patent application and patent against which the corrective document is being recorded. *See* MPEP § 302.06.

Therefore, the rules of practice and the procedures before the USPTO provide an avenue for the requested relief without relying upon extraordinary measures. As a request for the Office to invalidate an assignment is both extraordinary and contrary to USPTO policy, this petition must be dismissed.

Telephone inquiries concerning this communication should be directed to Katherine Zalasky McDonald at (571) 270-7064.

/Christopher Bottorff/

Christopher Bottorff Petitions Examiner Office of Petitions

Under the Paperwork Reduction Act of 1995, no persons are required to re PATENT APPLICATION FEE DETERMINATION RECORD Applic Substitute for Form PTO-875 Applic								to a collection of informat or Docket Number 7/371,839	ion unless it displays a Filing Date 07/09/2021	a valid OMB control number.	
	ENTITY: 🗹 LARGE 🗌 SMALL 🗌 MICRO										
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	FOR		NU	MBER FII		NUMBER EXTRA RATE (\$)				FEE (\$)	
	BASIC FEE (37 CFR 1.16(a), (b), c	or (c))		N/A		N/A		N/A	_		
	SEARCH FEE (37 CFR 1.16(k), (i), or			N/A		N/A		N/A			
	EXAMINATION FEE (37 CFR 1.16(o), (p), c			N/A		N/A		N/A			
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FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM (37 CFR 1.16(j))											
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* If the entry in column 1 is less than the entry in column 2, write "0" in column 3.								LIE			
** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20".								/TINA M. BELL/			
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The	"Highest Number P	reviously P	aid For"	(Total or	Independent) is the	e highest number i	ound in the ap	propriate box in colur	mn 1.		

This collection of information is required by 37 CFR 1.16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS

ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	G.R. MOHAN RAO
Serial No.:	17/371,839
Confirmation No.:	2197
Filed:	July 9, 2021
Group:	2892
Examiner:	Ajay ARORA
For:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT
	REGIONS

Mail Stop AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

AMENDMENT AND RESPONSE TO OFFICE ACTION

This communication is responsive to the Examiner's Office Action dated October 28, 2021. Reconsideration is respectfully requested.

<u>Amendments to the Claims</u> are reflected in the listing of claims beginning on page 2 of this paper. <u>Remarks/Arguments</u> begin on page 7 of this paper.
In the Claims

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This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A<u>n electronic system VLSI semiconductor device</u>, <u>the system</u> comprising:

at least one semiconductor device, the at least one semiconductor device including: a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed;

a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the first and second active regions towards an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface towards the area of the substrate where there are no active regions, wherein at least some of the transistors form digital logic of the [[VLSI]]semiconductor device.

2. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the substrate <u>of the at least one semiconductor device</u> is a p-type substrate.

3. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the substrate <u>of the at least one semiconductor device</u> has epitaxial silicon on top of a nonepitaxial substrate.

4. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the first active region and second active region <u>of the at least one semiconductor device</u> contain digital logic formed by one of either p-channel and n-channel devices.

5. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the first active region and second active region <u>of the at least one semiconductor device</u> contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.

6. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the first active region and second active region <u>of the at least one semiconductor device</u> are each separated by at least one isolation region.

7. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the graded dopant is fabricated with an ion implantation process.

8. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the first and second active regions <u>of the at least one semiconductor device</u> are formed adjacent the first surface of the substrate <u>of the at least one semiconductor device</u>.

9. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein dopants of the graded dopant concentration in the first active region or the second active region <u>of the at</u> <u>least one semiconductor device</u> are either p-type or n-type.

10. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein dopants of the graded dopant concentration in the first active region<u>of the at least one semiconductor</u> <u>device</u> are both p-type and n-type.

11. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein dopants of the graded dopant concentration in the second active region <u>of the at least one semiconductor</u> <u>device</u> are both p-type and n-type.

12. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein dopants of the graded dopant region in the well region <u>of the at least one semiconductor device</u> are both p-type and n-type.

13. (Currently amended) The <u>system VLSI semiconductor device</u> of claim 1, wherein the transistors which can be formed in the first and second active regions <u>of the at least one</u> <u>semiconductor device</u> are CMOS digital logic transistors requiring at least a source, a drain, a gate and a channel.

14. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the <u>at</u> <u>least one semiconductor device is a dynamic random access memory (DRAM).</u>

15. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the <u>at</u> <u>least one semiconductor device is a complementary metal oxide semiconductor (CMOS) with a</u> nonepitaxial substrate.

16. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the <u>at</u> <u>least one semiconductor device is a flash memory</u>.

17. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the <u>at</u> <u>least one semiconductor device comprises digital logic and capacitors.</u>

18. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the <u>at</u> <u>least one semiconductor device is a central processing unit.</u>

19. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein the <u>at</u> <u>least one semiconductor device is an image sensor.</u> 20. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 1, wherein each of the first and second active regions of the at least one semiconductor device are in the lateral or vertical direction.

21. (Currently amended) A<u>n electronic system VLSI semiconductor device</u>, comprising: at least one semiconductor device, the at least one semiconductor device including:

a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface of the substrate with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed in the surface thereof;

a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed in the surface thereof;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the surface to an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface to the area of the substrate where there are no active regions, and wherein the graded dopant concentration is linear, quasilinear, error function, complementary error function, or any combination thereof.

22. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 21, wherein the substrate <u>of the at least one semiconductor device</u> is an n-type substrate.

23. (Currently amended) The <u>system_VLSI semiconductor device</u> of Claim 21, wherein the substrate <u>of the at least one semiconductor device</u> is a p-type substrate.

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24. (Currently amended) The <u>system_VLSI semiconductor device</u> of Claim 21, wherein the substrate<u>of the at least one semiconductor device</u> has epitaxial silicon on top of a nonepitaxial substrate.

25. (Currently amended) The <u>system_VLSI semiconductor device</u> of Claim 21, wherein the first active region and second active region <u>of the at least one semiconductor device</u> contain at least one of either p-channel and n-channel devices.

26. (Currently amended) The <u>system_VLSI semiconductor device</u> of Claim 21, wherein the first active region and second active region<u>of the at least one semiconductor device</u> contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.

27. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 21, wherein the first active region and second active region<u>of the at least one semiconductor device</u> are each separated by at least one isolation region.

28. (Currently amended) The <u>system_VLSI semiconductor device</u> of Claim 21, wherein dopants of the graded dopant concentration in the first active region or the second active region <u>of</u> the at least one semiconductor device are either p-type or n-type.

29. (Currently amended) The <u>system VLSI semiconductor device</u> of Claim 21, wherein dopants of the graded dopant concentration in the first active region <u>of the at least one</u> <u>semiconductor device</u> are both p-type and n-type.

30. (Currently amended) The <u>system_VLSI semiconductor device</u> of Claim 21, wherein dopants of the graded dopant concentration in the second active region<u>of the at least one</u> <u>semiconductor device</u> are both p-type and n-type.

REMARKS

Applicant has carefully reviewed the Office Action dated October 28, 2021. Applicant has amended Claims 1-30 to more clearly point out the present inventive concept. The amendments are supported by the specification as filed, such as in paragraph [0002]. No new matter has been added. Reconsideration and favorable action is respectfully requested.

Claims 1-30 were provisionally rejected under 35 U.S.C. § 101 as claiming the same invention as that of Claims 1-30 of co-pending Application No. 16/947,294 ("294" Application"). This rejection is respectfully traversed.

A reliable test for double patenting under 35 U.S.C. § 101 is whether a claim in the application could be literally infringed without literally infringing a corresponding claim in the patent. *See* MPEP § 804. Although a terminal disclaimer is not effective in overcoming a statutory double patenting rejection, the claims may be cancelled or amended so that they are not coextensive in scope. *Id.*

Applicant submits that Claims 1-30, as amended herein, are not coextensive in scope with the '294 Application. Accordingly, Applicant respectfully requests that the provisional double patenting rejection be withdrawn.

Applicant has now made an earnest attempt in order to place this case in condition for allowance. For the reasons stated above, Applicant respectfully requests full allowance of the claims as amended.

If any issues arise, or if the Examiner has any suggestions for expediting allowance of this Application, the Applicant respectfully invites the Examiner to contact the undersigned at the telephone number indicated below or at whowison@munckwilson.com.

Recognizing that Internet communications are not secure, Applicant hereby authorizes the USPTO to communicate with the undersigned and practitioners in accordance with 37 CFR 1.33 and 37 CFR 1.34 concerning any subject matter of this application by video conferencing, instant

messaging, or electronic mail. Applicant understands that a copy of these communications will be made of record in the application file.

Please charge any additional fees or deficiencies in fees or credit any overpayment to Deposit Account No. 50-0208/GRTD60-35314.

Respectfully submitted, MUNCK WILSON MANDALA, LLP Attorneys for Applicant

/William G. Howison, Reg. #66850/

William G. Howison Registration No. 66,850

WGH/als

P.O. Drawer 800889 Dallas, Texas 75380 Tel: 972-628-3600 Fax: 972-628-3616 December 1, 2021

Electronic Acknowledgement Receipt				
EFS ID:	44406378			
Application Number:	17371839			
International Application Number:				
Confirmation Number:	2197			
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS			
First Named Inventor/Applicant Name:	G.R. MOHAN RAO			
Customer Number:	25883			
Filer:	William G. Howison			
Filer Authorized By:				
Attorney Docket Number:	GRTD60-35314			
Receipt Date:	01-DEC-2021			
Filing Date:	09-JUL-2021			
Time Stamp:	19:00:40			
Application Type:	Utility under 35 USC 111(a)			

Payment information:

Submitted with Payment		no	no			
File Listing:						
Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)	
			123821			
1		GRT35314AMD.pdf	6ce164b4363ce2aead4fe55db6433770dad 9b708	yes	8	

	Document Description	Start	End
	Amendment/Req. Reconsideration-After Non-Final Reject	1	1
	Claims	2	6
	Applicant Arguments/Remarks Made in an Amendment	7	8
Warnings:			
Information:			
	Total Files Size (in bytes):	123	3821

New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.

UNITED ST	ates Patent and Trademan	UNITED STA' United States Address: COMMI PO. Box I	, Virginia 22313-1450
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314
25883 MUNCK WILSON MANDA P.O. Drawer 800889 DALLAS, TX 75380	ALA L.L.P		CONFIRMATION NO. 2197 TION NOTICE

Title:SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Publication No.US-2021-0359086-A1 Publication Date:11/18/2021

NOTICE OF PUBLICATION OF APPLICATION

The above-identified application will be electronically published as a patent application publication pursuant to 37 CFR 1.211, et seq. The patent application publication number and publication date are set forth above.

The publication may be accessed through the USPTO's publically available Searchable Databases via the Internet at www.uspto.gov. The direct link to access the publication is currently http://www.uspto.gov/patft/.

The publication process established by the Office does not provide for mailing a copy of the publication to applicant. A copy of the publication may be obtained from the Office upon payment of the appropriate fee set forth in 37 CFR 1.19(a)(1). Orders for copies of patent application publications are handled by the USPTO's Public Records Division. The Public Records Division can be reached by telephone at (571) 272-3150 or (800) 972-6382, by facsimile at (571) 273-3250, by mail addressed to the United States Patent and Trademark Office, Public Records Division, Alexandria, VA 22313-1450 or via the Internet.

In addition, information on the status of the application, including the mailing date of Office actions and the dates of receipt of correspondence filed in the Office, may also be accessed via the Internet through the Patent Electronic Business Center at www.uspto.gov using the public side of the Patent Application Information and Retrieval (PAIR) system. The direct link to access this status information is currently https://portal.uspto.gov/pair/PublicPair. Prior to publication, such status information is confidential and may only be obtained by applicant using the private side of PAIR.

Further assistance in electronically accessing the publication, or about PAIR, is available by calling the Patent Electronic Business Center at 1-866-217-9197.

Office of Data Managment, Application Assistance Unit (571) 272-4000, or (571) 272-4200, or 1-888-786-0101

page 1 of 1

UNIT	ED STATES PATENT	t	JNITED STATES DEPARTMENT Jnited States Patent and Trade Address: COMMISSIONER FOR P P.O. Box 1450 Alexandria, Virginia 22313-145 www.uspto.gov	emark Office ATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197
	7590 10/28/2021 SON MANDALA L.L.P		EXAM	IINER
P.O. Drawer 80 DALLAS, TX	00889		ARORA	A, AJAY
2			ART UNIT	PAPER NUMBER
			2892	
			NOTIFICATION DATE	DELIVERY MODE
			10/28/2021	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com admin@dalpat.com eofficeaction@appcoll.com

	Application No.	Applicant(s					
Office Action Commence	17/371,839	RAO, G.R. M	IOHAN				
Office Action Summary	Examiner	Art Unit	AIA (FITF) Status				
	AJAY ARORA	2892	No				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address							
Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPL DATE OF THIS COMMUNICATION.	Y IS SET TO EXPIRE <u>3</u> MONTH	S FROM TH	E MAILING				
- Extensions of time may be available under the provisions of 37 CFR 1.1	36(a). In no event, however, may a reply be tin	nely filed after SIX	(6) MONTHS from the mailing				
date of this communication If NO period for reply is specified above, the maximum statutory period							
 Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing 							
adjustment. See 37 CFR 1.704(b).							
Status							
1) Responsive to communication(s) filed on $\frac{7/9}{100}$							
A declaration(s)/affidavit(s) under 37 CFR		·					
, , , , , , , , , , , , , , , , , , , ,	This action is non-final.	ant ant farth	during the interview				
3) An election was made by the applicant in resonance on ; the restriction requirement and electron is the restriction requirement and electron is the restriction requirement and electron is the restriction is the restriction requirement and electron is the restriction restricti							
4) Since this application is in condition for allow	•						
closed in accordance with the practice unde							
Disposition of Claims*							
5) 🗹 Claim(s) 1-30 is/are pending in the app	blication.						
5a) Of the above claim(s) is/are withd							
6) Claim(s) is/are allowed.							
7) \checkmark Claim(s) 1-30 is/are rejected.							
8) Claim(s) is/are objected to.							
9) Claim(s) are subject to restriction a	nd/or election requirement						
* If any claims have been determined <u>allowable</u> , you may be el	•	secution Hig	1way program at a				
participating intellectual property office for the corresponding a	-	-					
http://www.uspto.gov/patents/init_events/pph/index.jsp or send	l an inquiry to PPHfeedback@uspto	.gov.					
Application Papers							
10) The specification is objected to by the Exami	ner.						
11) I The drawing(s) filed on <u>8/11/2021</u> is/are: a)	accepted or b) dijected	to by the Ex	aminer.				
Applicant may not request that any objection to the c							
Replacement drawing sheet(s) including the correction	on is required if the drawing(s) is obje	cted to. See 3	7 CFR 1.121(d).				
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for forei	gn priority under 35 U.S.C. § 1	19(a)-(d) or	(f).				
	that						
a) All b) Some** c) None of							
1. Certified copies of the priority docu							
2. Certified copies of the priority docu	•	•					
3. Copies of the certified copies of the application from the International B	• •	received in 1	his National Stage				
** See the attached detailed Office action for a list of the certif	ied copies not received.						
Attachment(s)							
1) 🔽 Notice of References Cited (PTO-892)	3) 🔲 Interview Summar Paper No(s)/Mail I						
2) Information Disclosure Statement(s) (PTO/SB/08a and/or PTO/S	SB/08b) 4) Other:						
Paper No(s)/Mail Date <u>8/13/2021</u> . U.S. Patent and Trademark Office							

DETAILED ACTION

Notice of Pre-AIA or AIA Status

1. The present application is being examined under the pre-AIA first to invent provisions.

Double Patenting

 A rejection based on double patenting of the "same invention" type finds its support in the language of 35 U.S.C. 101 which states that "whoever invents or discovers any new and useful process... may obtain a patent therefor..." (Emphasis added). Thus, the term "same invention," in this context, means an invention drawn to identical subject matter. See *Miller v. Eagle Mfg. Co.*, 151 U.S. 186 (1894); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); *In re Ockert*, 245 F.2d 467, 114 USPQ 330 (CCPA 1957).

A statutory type (35 U.S.C. 101) double patenting rejection can be overcome by canceling or amending the claims that are directed to the same invention so they are no longer coextensive in scope. The filing of a terminal disclaimer cannot overcome a double patenting rejection based upon 35 U.S.C. 101.

3. Claims 1-30, respectively, are provisionally rejected under 35 U.S.C. 101 as claiming the same invention as that of claims 1-30, respectively, of copending Application No. 16/947,294 (reference application). This is a <u>provisional</u> statutory double patenting rejection since the claims directed to the same invention have not in fact been

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patented (although a Notice of Allowance for application 16/947,294 dated 8/11/2021 has been issued, a patent has not yet been issued).

Art Based Rejection

4. No art based rejection has been provided, as the prior art does not teach or suggest the features of claims 1-30. The closest prior art is Hong (US 2007/0045682), hereinafter Hong, especially see Figures 4A-4D and 5A-5C and para 26-32 (as also explained in Notice of Allowance of 8/11/2021 for parent application 16/947,294).

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to AJAY ARORA whose telephone number is (571)272-8347. The examiner can normally be reached 9 AM - 5 PM.

Examiner interviews are available via telephone, in-person, and video conferencing using a USPTO supplied web-based collaboration tool. To schedule an interview, applicant is encouraged to use the USPTO Automated Interview Request (AIR) at http://www.uspto.gov/interviewpractice.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Thao X. Le can be reached on 5712721708. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of published or unpublished applications may be obtained from Patent Center. Unpublished application information in Patent Center is available to registered users. To file and manage patent submissions in Patent Center, visit: https://patentcenter.uspto.gov. Visit https://www.uspto.gov/patents/apply/patent-

center for more information about Patent Center and

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additional questions, contact the Electronic Business Center (EBC) at 866-217-9197

(toll-free). If you would like assistance from a USPTO Customer Service

Representative, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/AJAY ARORA/ Primary Examiner, Art Unit 2892

 Application/Control No.
 Applicant(s)/Patent Under

 17/371,839
 Reexamination

 RAO, G.R. MOHAN
 Examiner

 AJAY ARORA
 Art Unit

 2892
 Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	CPC Classification
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*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)						
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

U.S. Patent and Trademark Office PTO-892 (Rev. 01-2001)

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Application/Control No.	Applicant(s)/Patent Under Reexamination
17/371,839	RAO, G.R. MOHAN
Examiner	Art Unit
AJAY ARORA	2892

CPC - Searched*				
Symbol	Date	Examiner		
H01L 29/1095	10/23/2021	AKA		

CPC Combination Sets - Searched*					
Symbol Date Examiner					

US Classification - Searched*							
Class Subclass Date Examiner							
257	25	10/23/2021	AKA				

* See search history printout included with this form or the SEARCH NOTES box below to determine the scope of the search.

Search Notes							
Search Notes	Date	Examiner					
Inventor search	10/23/2021	AKA					
Assignee search	10/23/2021	АКА					
References for all parent applications (10/934,915; 11/622,496; 15/ 590,282; 16/717950 and 16/947294) considered	10/23/2021	АКА					
.clm. interference search	10/23/2021	АКА					
EAST search history report	10/23/2021	АКА					

Interference Search							
US Class/CPC Symbol	US Subclass/CPC Group	Date	Examiner				
H01L	29/1095	10/23/2021	AKA				
257	25	10/23/2021	AKA				

/AJAY ARORA/ Primary Examiner, Art Unit 2892

U.S. Patent and Trademark Office



Application/Control No.	Applicant(s)/Patent Under Reexamination
17/371,839	RAO, G.R. MOHAN
Examiner	Art Unit
AJAY ARORA	2892

/AJAY ARORA/ Primary Examiner, Art Unit 2892

	Application/Control No.	Applicant(s)/Patent Under Reexamination
Index of Claims	17/371,839	RAO, G.R. MOHAN
	Examiner	Art Unit
	AJAY ARORA	2892

•	Rejected	-	Cancelled	Ν	Non-Elected	Α	Appeal
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EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	574	(source drain source/drain) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 15:37
L3	574	L2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 15:37
L4	1	("9647070").PN.	US-PGPUB; USPAT	OR	OFF	2021/10/23 16:21
L5	1	("6384431").PN.	US-PGPUB; USPAT	OR	OFF	2021/10/23 16:21
S1	0	17/371,839	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:17
S2	31	((("GREENTHREAD") near3 ("LLC"))).AS,AANM.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 10:18
S3	29	((("RAO") near3 ("G.R") near3 ("MOHAN"))).INV.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 10:19
S4	30,065	H01L29/1095.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO;	OR	OFF	2021/10/23 10:19

			JPO; DERWENT; IBM_TDB			
S5	669	(257/25).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:19
S6	56	("20010028097" "20020195656" "20030183856" "20070045682" "20080142899" "20140034997" "20170243876" "4160985" "4684971" "4688063" "4907058" "4994887" "5835402" "6025237" "6384431" "6465862").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 10:20
S7	29	("5448087" "5888857" "20030030488" "6720622" "20030026126" "5973575" "5262345" "20040027753").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:20
S8	12	(US-20040027753-\$ or US- 20030030488-\$ or US-20140034997-\$ or US-20060049464-\$ or US- 20030026126-\$ or US-20070181927-\$ or US-20070045682-\$).did. or (US- 5973575-\$ or US-5262345-\$ or US- 5448087-\$ or US-6720622-\$ or US- 5888857-\$).did.	US-PGPUB; USPAT	OR	ON	2021/10/23 10:21
S9	47	("20020056883" "20020084430" "20020102783" "20030042511" "4160985" "5637898" "5517052" "4481522" "6831292" "20020093281" "5029277" "20060113592" "20020134419").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:22
S10	118	("20020074585" "5496746" "6683343" "6696314" "6452086" "6472715" "6747883" "5797999" "6670544" "20040063288" "4347654" "4866000" "6744117" "6754093" "5213988" "5569612" "RE37441" "4001864" "6756616" "5130262" "5329144" "6706550" "6753202" "5480816" "6713813" "6737722" "5575862" "6211028").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:23

S11	255	("20020102783" "20030026126" "20030030488" "6211028" "6310366" "6753202" "7115925" "8164124" "6878603" "20020056883" "20020093281" "20150200314" "4347654" "5496746" "6452086" "6737722" "6747883" "6780713" "20030042511" "5029277" "5888857" "6670544" "6706550" "6713813" "6921943" "7504692" "20040027753" "4160985" "5448087" "6472715" "6683343" "6831292" "7307327" "5569612" "5575862" "5637898" "6720622" "6744117" "20070045682" "20020134419" "20060113592" "20130001661" "4481522" "5262345" "6756616" "6933215" "7233044" "20010040622" "20020074585" "5130262" "20020074585" "5130262" "20020074585" "5130262" "20020084430" "4001864" "4866000" "5480816" "5517052" "5797999" "5973575" "6754093" "7064385" "20120048462").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23
S12	271	("20020102783" "20020134419" "20070045682" "6310366" "RE37441" "20040027753" "20120048462" "4160985" "4347654" "5213988" "5575862" "8164124" "20130001661" "5329144" "5496746" "5569612" "5637898" "5973575" "6211028" "6683343" "6696314" "6713813" "6754093" "7064385" "20030030488" "20070045682" "4481522" "6753202" "20020056883" "20020084430" "20020093281" "20020084430" "20020093281" "20030026126" "20030042511" "4001864" "5130262" "5262345" "5448087" "6472715" "6670544" "6720622" "6780713" "6921946" "10510842" "20010040622" "20020074585" "6465862" "6747883" "7233044" "7307327" "20030030488" "20040063288" "20060113592" "20150200314" "4866000" "5029277" "5480816" "5517052" "5797999" "6452086" "6706550"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 10:59

		"6737722" "6831292" "6878603" "7115925" "9190502" "9647070" "5888857" "6744117" "6756616" "6933215" "7504692" "8421195").PN.				
S13	316	("20020102783" "20020134419" "20070045682" "6310366" "RE37441" "4907058" "20040027753" "20080142899" "20120048462" "4160985" "4347654" "5213988" "5575862" "8164124" "20010028097" "4994887" "6025237" "20130001661" "5329144" "5496746" "5569612" "5637898" "5973575" "6211028" "6683343" "6696314" "6713813" "6754093" "7064385" "20140034997" "10734481" "4481522" "6753202" "20020195656" "20030183856" "20020056883" "20020084430" "20020093281" "20030026126" "20030042511" "4001864" "5130262" "5262345" "5448087" "6472715" "6670544" "6720622" "6780713" "6921946" "20170243876" "5835402" "200300183856" "4684971" "20030030488" "20020074585" "20030030488" "20040063288" "20030030488" "20040063288" "20030030488" "20040063288" "20030030488" "20040063288" "20060113592" "20150200314" "4866000" "5029277" "5480816" "5517052" "5797999" "6452086" "6706550" "6737722" "6831292" "6384431" "5888857" "6744117" "6756616" "6933215" "7504692" "8421195").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23
S14	319	S7 S9 S10 S11 S12 S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:01
S15	10	S3 and drift	US-PGPUB; USPAT;	OR	OFF	2021/10/23 11:02

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S16	14	S2 and drift	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:02
S17	574	(source drain source/drain) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:03
S18	25,930	H01L27/11521.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:03
S19	14,669	H01L27/11524.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:04
S20	29,711	H01L27/14643.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:04
S21	11,836	H01L29/36.cpc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:04
S22	13,097	H01L29/7395.cpc.	US-PGPUB; USPAT; USOCR;	OR	ON	2021/10/23 11:04

			FPRS; EPO; JPO; DERWENT; IBM_TDB			
S23	18	S4 and S18 and S21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:08
S24	18	S4 and S18 and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:10
S25	18	S4 and S19 and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:10
S26	66	S4 and S19 and S21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2021/10/23 11:10
S27	2	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive))).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:11
S28	32	((source drain "source/drain" active) and drift and ((gradient graded) near2 concentration near2 dop\$3) and well and ((no near2 active) (inactive)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2021/10/23 11:13

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Doc description: Information Disclosure Statement (IDS) Filed

17/371,839 - GAU: 2892

PTO/SB/08a (02-18)

Approved for use through 11/30/2020. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)

Application Number		17371839		
Filing Date		2021-07-09		
First Named Inventor	G.R. M	Aohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Number	ar l	GRTD60-35314		

				U.S	PATENTS	Remove		
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear		
/A.A/	1	4160985	A	1979-07-10	Kamins et al.			
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Application Number		17371839		
Filing Date		2021-07-09		
First Named Inventor G.R. I		Mohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Number		GRTD60-35314		

/A.A/	96	465862	В1	2002-10-15	Harris			
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Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date	Name of Patentee or Applicant of cited Document	Releva		Lines where es or Relevan
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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.A/

Application Number		17371839		
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First Named Inventor G.R.		Mohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Numb	er	GRTD60-35314		

Examiner Initial*	Cite No	Foreign Document Number ³	Country Code²İ	Kind Code⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear	T5	
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/A.A/	4	2004049453	wo	A1	2004-06-10	Zheng et al.			
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Examiner Initials*	Cite No	(book, magazine, jou	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.						
	1	IPR2020-00288-Exhibi	IPR2020-00288-Exhibit 1029-Claim Construction District Court 4 20-2020						
	2	IPR2020-00288-Exhibit 2007-Minutes for Markman Hearing Held Via Video Conference Before U.S. District Judge Rodney Gilstrap, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 61							
	3	IPR2020-00288-Petitio	IPR2020-00288-Petitioner Reply						
	4	IPR2020-00289-00289 Petitioner Reply							

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.A/

Application Number		17371839		
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First Named Inventor G.R.		Mohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Number	er	GRTD60-35314		

5	IPR2020-00292 - Petition for IPR	
6	IPR2020-00292-Exhibit 2002-Excerpt from Exhibit 4 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on U.S. Patent No. 6,384,431 to Takahashi	
7	IPR2020-00288 - Ex. 1020 - Michael Nastasi and James W. Mayer, Ion Implantation and Synthesis of Materials (2006). 4 pages	
8	IPR2020-00288-Exhibit 2001 - IPR2020-00288 - Excerpt from Exhibit 1 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Morris	
9	IPR2020-00288-Exhibit 2002-xcerpt from Exhibit 2 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Miyamoto	
10	IPR2020-00288-Exhibit 2009-Complaint for Patent Infringement, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 1	
11	IPR2020-00288-Exhibit 2011- Exhibit A to Revised Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 60-1	
12	IPR2020-00288-Exhibit 2012-Samsungs Responsive Claim Construction Brief - District Court	
13	IPR2020-00288-Exhibit 2013- Glew Dec	
14	IPR2020-00288-Exhibit 2014- Excerpt from Exhibit 10 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions	
15	IPR2020-00288-Patent Owner Preliminary Response	

Application Number		17371839		
Filing Date		2021-07-09		
First Named Inventor G.R.		Mohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Numb	er	GRTD60-35314		

	16	IPR2020-00288-Patent Owner Sur Reply	
-	17	IPR2020-00288-Petition	
-	18	IPR2020-00289-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne	
-	19	IPR2020-00289-Exhibit 1003-Smith Dec	
	20	IPR2020-00289-Exhibit 1010- S. M. Sze et al., Semiconductor Devices: Physics and Technology,John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")	
	21	IPR2020-00289-Exhibit 1012-Ben G. Streetman, Solid State Electronic Devices, 2nd Ed., Prentice-Hall, 1980 ("Streetman")	
2	22	IPR2020-00289-Exhibit 2001-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne	
2	23	IPR2020-00289-Exhibit 2002- Exhibit 3 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Wieczorek	
2	24	IPR2020-00289-Exhibit 2011-Behzad Razavi, Design of Analog CMOS Integrated Circuits, 2001 ("Razavi")	
	25	IPR2020-00289-Exhibit 2012-Excerpts from Wolf, S., Silicon Processing for the VLSI Era, Vol.4 - Deep-Submicron Process Technology (2002) ("Wolf Vol. 4")	
	26	IPR2020-00289-Exhibit 2013-Glew Dec	

Application Number		17371839		
Filing Date		2021-07-09		
First Named Inventor G.R. I		Mohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Numb	er	GRTD60-35314		

27	7 IPR2020-00289-Patent Owner Pre Resp	
28	B IPR2020-00289-Patent Owner Sur reply	
29	9 IPR2020-00289-Petition	
30) IPR2020-00290-Exhibit 1003-Declaration of Dr. Bruce Smith	
31	IPR2020-00290-Exhibit 1013-Tango, Mega bit Memory Technology	
32	2 IPR2020-00290-Patent Owner Preliminary Resp	
33	B IPR2020-00290-Patent Owner Sur Reply	
34	PR2020-00290-Petition	
35	5 IPR2020-00290-Petitioners Reply to Patent Owner Preliminary Response	
36	6 IPR2020-00291-Exhibit 1003-Declaration of Dr. Bruce Smith	
37	, IPR2020-00291-Exhibit 1011- The Insulated Gate Bipolar Transistor: IGBT Theory and Design, Vinod Kumar Khanna, IEEE Press and Wiley-Interscience, 2003	

Application Number		17371839
Filing Date		2021-07-09
First Named Inventor G.R. I		Mohan Rao
Art Unit		2812
Examiner Name		
Attorney Docket Number		GRTD60-35314

:	38	IPR2020-00291-Exhibit 1020-S. M. Sze, Physics of Semiconductor Devices, Wiley-Interscience, 2nd Ed., 1981 ("Sze 81")	
:	39	IPR2020-00291-Exhibit 1021-S. M. Sze, Semiconductor Devices: Physics and Technology, John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")	
	40	IPR2020-00291-Exhibit 2001-Exhibit 2 to Appendix B of Samsung Electronics Co., LTD's Invalidity Contentions (Invalidity Contention based on U.S. Patent Application Publication No. 2002/0195656 ("Hattori"))	
	41	IPR2020-00291-Exhibit 2013- Declaration of Dr. Alexander D. Glew	
	42	IPR2020-00291-Patent Owner Preliminary Resp	
	43	IPR2020-00291-Patent Owner Sur Reply	
	44	IPR2020-00291-Petition	
	45	IPR2020-00291-Petitioners Reply	
	46	IPR2020-00292-Exhibit 1003-Declaration of Dr. Bruce Smith	
	47	IPR2020-00292-Exhibit 2001-Excerpt from Exhibit 1 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on "Insulated Gate Bipolar Transistor IGBT Theory and Design" by Vinod Kumar Khanna	
	48	IPR2020-00292-Exhibit 2012-Excerpt from Exhibit A to Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 53-1 (Mar. 18, 2020)	

Application Number		17371839
Filing Date		2021-07-09
First Named Inventor G.R. I		Mohan Rao
Art Unit		2812
Examiner Name		
Attorney Docket Number		GRTD60-35314

	49 IPR2020-00292-Patent Owner Preliminary Response						
If you wis	If you wish to add additional non-patent literature document citation information please click the Add button Add						
EXAMINER SIGNATURE							
Examiner	Signa	iture	/AJAY ARORA/		Date Considered	10/23/2021	
	*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						
¹ See Kind Codes of USPTO Patent Documents at <u>www.USPTO.GOV</u> or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here it English language translation is attached.							ument.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.A/

Copies of non-patent literature documents listed not provided in current application but provided in parent application 16/947,294

Application Number Filing Date 2021-07-09 INFORMATION DISCLOSURE First Named Inventor G.R. Mohan Rao STATEMENT BY APPLICANT 2812 Art Unit (Not for submission under 37 CFR 1.99) Examiner Name Attorney Docket Number GRTD60-35314

17371839

CERTIFICATION STATEMENT

Please see 37 CFR 1.97 and 1.98 to make the appropriate selection(s):

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(1).

OR

That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(2).

See attached certification statement.

The fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

× A certification statement is not submitted herewith.

SIGNATURE

A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature	/Gregory M. Howison, Reg. #30646/	Date (YYYY-MM-DD)	2021-08-11
Name/Print	Gregory M. Howison	Registration Number	30646

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1 hour to complete, including gathering, preparing and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether the Freedom of Information Act requires disclosure of these record s.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspections or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	G.R. Mohan RAO
Serial No.:	17/371,839
Confirmation No.:	2197
Filed:	July 9, 2021
Group:	2892
Examiner:	Ajay ARORA
For:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Mail Stop Petitions Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

PETITION TO EXPUNCE ASSIGNMENT RECORDING

Petitioner respectfully petitions to suspend the rules under 37 C.F.R. § 1.182 and requests that Assignment: 2, i.e., from Greenthread, LLC to Vervain, LLC be deleted to reflect the correct ownership of the patent. The reasons why justice requires a waiver of the requirements are as follows:

- The normal corrective procedures as outlined in MPEP § 323.01(a) through § 323.01(c) will not provide petitioners with adequate relief.
- An assignment totally unrelated to the current application was incorrectly recorded in the application. (A copy of the recorded Assignment document is attached)
- The assignment recordation error is not of a typographical nature; thus, MPEP § 323.01(a) does not apply.
- The recorded assignment document does not contain a typographical error and, additionally, matches the cover sheet. As such, MPEP § 323.01(b) does not apply.
- The assignment was not improperly filed and recorded by another person against the current Application. Therefore, MPEP § 323.01(c) does not apply.

Thus,

- There never existed an assignment from Greenthread, LLC to Vervain, LLC with respect to U.S. Application No. 17/371,839 or any applications or patents related to it. (A copy of the USPTO Parent Continuity Data is attached.)
- The recorded assignment is void and should be expunged from the record.
- No right, title or interest was transferred to any existing entity as the result of this recorded document.
- All right, title and interest remain as originally recorded, from inventor G.R. Mohan Rao to Greenthread, LLC.
- There was no intent to assign the patent from Greenthread, LLC to Vervain, LLC, and such recordation was made in error.

For the reasons set forth above, Petitioner respectfully requests that this Petition be granted. Petitioner submits that the integrity of the assignment records will not be affected by the granting of the petition.

Accordingly, Petitioner requests expunction of the recorded assignment from Greenthread, LLC to Vervain, LLC such that all right, title and interest remain in Greenthread, LLC.

Enclosed is the fee of \$420.00 as set forth under C.F.R. 1.17(f). Please charge any deficiency or credit any overpayment to deposit account number 50-0208/GRTD60-35314 of MUNCK, WILSON, MANDALA, LLP.

Respectfully submitted, MUNCK, WILSON, MANDALA, LLP Attorneys for Petitioners

/Gregory M. Howison, Reg. #30646/

Gregory M. Howison Registration No. 30,646

GMH/als P.O. Drawer 800889 Dallas, Texas 75380 Tel: 972-628-3600 Fax: 972-628-3616 October 19, 2021

PETITION TO EXPUNCE ASSINGMENT RECORDING S/N 17/371,839 Atty. Dkt. No. GRTD60-35314 2

ASSIGNOR	ASSIGNEE
Greenthread, LLC	Vervain, LLC
Philip W. John, Jr. Manager	Philip W. John, Jr., Member
6307 Bandera Ave, Apt B	7424 Mason Dells Drive
Dallas, Texas 75225-3617	Dallas, Texas 75230-3244
Email: john@greenthreadllc.com	Email: john@vervainflc.com

ASSIGNMENT AGREEMENT

This Assignment Agreement ("Assignment") is entered into by and between Vervain, LLC, a Texas limited liability company, hereinafter referred to as "Assignee," and Greenthread, LLC, a Texas limited liability company, hereinafter referred to as "Assignor," and shall become effective upon being duly signed by the authorized representative of Assignor ("Effective Date").

RECITALS:

Assignor and Assignee are entering into a Patent Assignment Agreement (the "Agreement").

Pursuant to the Agreement, Assignor hereby desires to assign to Assignee all of its rights, title and interest in and to the following United States patents and pending application:

- U.S. Provisional Application Number 61/509,256, entitled, "Lifetime Mixed Level Nand Flash System," filed on July 19,2011;
- U.S. Patent Number 8,891,298, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on April 25, 2012, and issued on November 18, 2014;
- U.S. Patent Number 9,196,385, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on Octber 28, 2014, and issued on November 24, 2015;
- 4. U.S. Patent Number 9,997,240, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on November 24, 2015, and issued on June 12, 2018, and
- U.S. Patent Application Number 16/006,299, entitled, "Lifetime Mixed Level Non-Volatile Memory System," filed on June 12, 2018, and is pending (collectively referred to hereinafter referred to as the "Patent").

For good and valuable consideration, Assignor and Assignee hereby agree as follows:

ASSIGNMENT:

- Assignor hereby assigns to Assignee its entire worldwide right, title and interest in and to Assignor's Patent, including the entire worldwide right, title and interest in and to any reexamination or reissue of the Patent. This includes, without limitation, Assignor's right to prosecute, and receive, all damages, royalties, awards and compensation for past, present and/or future infringement.
- 2. Assignor agrees to do the following without further consideration, in order to carry out the intent of this Assignment:
 - i. Execute all oaths, assignments, applications, and other papers necessary or desirable to fully secure to Assignee the rights, titles and interests herein conveyed; and
 - ii. Generally do all lawful acts for vesting in Assignee the rights, titles, and interests herein conveyed.
- 3. Assignor has not made and will not hereafter make any assignment, grant, mortgage, license, or other agreement affecting the rights, titles, and interests herein conveyed to Assignee.
- Assignor hereby represents and warrants that Assignor has the authority to assign the applicable Patent pursuant to this Assignment.

The undersigned having read this Assignment and fully understanding the provisions of this Assignment, hereby executes this Assignment as of the Effective Date.

Greenthread, LLC (Assignor) Philip W. John, Jr. Manager

Philip 62 y

Signature: Printed Name: Philip W. John, Jr. Date: August ____, 2019

17/371,839 SEMICONDUCTOR DEVICES WITH GRADED DOPANT GF

GRTD60-35314 10-06-2021::12:46:45

Description	Parent Number	Parent Filing or 371(c) Date	AIA (First Inventor to File)	Parent Status	Patent Number
This application is a Continuation of	16/947,294	07-27-2020	No	Patented	11,121,222
is a continuation of	16/717,950	12-17-2019	No	Patented	10,734,481
is a continuation of	15/590,282	05-09-2017	No	Patented	10,510,842
is a continuation of	14/931,636	11-03-2015	No	Patented	9,647,070
s a continuation of	14/515,584	10-16-2014	No	Patented	9,190,502
is a continuation of	13/854,319	04-01-2013	No	Abandoned	
is a continuation of	11/622,496	01-12-2007	No	Patented	8,421,195
is a Division of	10/934,915	09-03-2004	No	Abandoned	-

Close Window

Electronic Patent Application Fee Transmittal						
Application Number:	17	17371839				
Filing Date:	09-	09-Jul-2021				
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	G.R. MOHAN RAO					
Filer:	Gre	egory Michael Howi	son/Anna Nguy	<i>r</i> en		
Attorney Docket Number:	GR	TD60-35314				
Filed as Large Entity	-					
Filing Fees for Utility under 35 USC 111(a)						
Description		Fee Code	Quantity	Amount	Sub-Total in USD(\$)	
Basic Filing:						
Pages:						
Claims:						
Miscellaneous-Filing:						
Petition:						
PETITION FEE- 37 CFR 1.17(F) (GROUP I)		1462	1	420	420	
Patent-Appeals-and-Interference:						
Post-Allowance-and-Post-Issuance:						

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
Extension-of-Time:				
Miscellaneous:				
	Tot	al in USD	(\$)	420

Electronic A	Electronic Acknowledgement Receipt						
EFS ID:	44060872						
Application Number:	17371839						
International Application Number:							
Confirmation Number:	2197						
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
First Named Inventor/Applicant Name:	G.R. MOHAN RAO						
Customer Number:	25883						
Filer:	Gregory Michael Howison						
Filer Authorized By:							
Attorney Docket Number:	GRTD60-35314						
Receipt Date:	19-OCT-2021						
Filing Date:	09-JUL-2021						
Time Stamp:	11:10:49						
Application Type:	Utility under 35 USC 111(a)						

Payment information:

Submitted with Payment	yes				
Payment Type	DA				
Payment was successfully received in RAM	\$420				
RAM confirmation Number	E20210IB11500206				
Deposit Account	500208				
Authorized User	Gregory Howison				
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:					
37 CFR 1.21 (Miscellaneous fees and charges)					

37 CFR 1.20 (Post Issuance fees)

File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.
			1713018		
1	Petition for review by the Office of Petitions	GRT35314PetitiontoExpunge. pdf	c055f20e57ec2274e0cd97b77d2df6f98953 b462	no	5
Warnings:			I I		
Information:					
			38237		
2	Fee Worksheet (SB06)	fee-info.pdf	ffd80fae29ff2a114a9e9cd93834d8403b477 dbc	no	2
Warnings:			Į I		
Information:					
		Total Files Size (in bytes)	: 17	51255	
characterized Post Card, as <u>New Applicat</u> If a new appli 1.53(b)-(d) an Acknowledge <u>National Stag</u> If a timely sub U.S.C. 371 and national stage <u>New Internat</u>	edgement Receipt evidences receip by the applicant, and including page described in MPEP 503. <u>ions Under 35 U.S.C. 111</u> cation is being filed and the applica d MPEP 506), a Filing Receipt (37 CF ement Receipt will establish the filin <u>te of an International Application un</u> prission to enter the national stage d other applicable requirements a F e submission under 35 U.S.C. 371 wi ional Application Filed with the USP national application is being filed an	ge counts, where applicable. tion includes the necessary of R 1.54) will be issued in due g date of the application. <u>Inder 35 U.S.C. 371</u> of an international applicati orm PCT/DO/EO/903 indicati ill be issued in addition to the <u>PTO as a Receiving Office</u>	It serves as evidence components for a filin course and the date s ion is compliant with ing acceptance of the e Filing Receipt, in du	of receipt s g date (see hown on th the conditic application e course.	imilar to 37 CFR is ons of 35 a as a
an internation and of the Int	nal filing date (see PCT Article 11 an ernational Filing Date (Form PCT/R(rity, and the date shown on this Ack	d MPEP 1810), a Notification D/105) will be issued in due c	of the International <i>I</i> ourse, subject to pres	Application criptions co	Number oncerning

UNIT	ed States Paten	t	UNITED STATES DEPARTMENT Jnited States Patent and Trade (ddress: COMMISSIONER FOR P P.O. Box 1450 Alexandria, Virginia 22313-145 www.uspto.gov	emark Office ATENTS
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	2197
	7590 10/05/202 SON MANDALA L.L.I	-	EXAN	IINER
P.O. Drawer 80 DALLAS, TX	0889		CENTRAL	, DOCKET
2			ART UNIT	PAPER NUMBER
			OPAP	
			NOTIFICATION DATE	DELIVERY MODE
			10/05/2021	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

IPdocketing@munckwilson.com admin@dalpat.com eofficeaction@appcoll.com

	Decisio	on Granting Request for	Application No. 17/371,839	Applicant(s) RAO, G.R. MC	Applicant(s) RAO, G.R. MOHAN					
	Prioritized Examination (Track I)		Examiner APRIL M WISE	Art Unit OPET	AIA (FITF) Status No					
1.	 THE REQUEST FILED <u>09 July 2021</u> IS <u>GRANTED</u>. The above-identified application has met the requirements for prioritized examination A. Image: For an original nonprovisional application (Track I). B. Image: For an application undergoing continued examination (RCE). 									
2.	2. The above-identified application will undergo prioritized examination. The application will be accorded special status throughout its entire course of prosecution until one of the following occurs:									
	Α.	filing a petition for extension	of time to extend the tim	ne period for filin	g a reply;					
	В.	filing an amendment to amen independent claims, more th								
	C.	filing a request for continued	examination ;							
	D.	filing a notice of appeal;								
	E.	filing a request for suspension	of action;							
	F.	mailing of a notice of allowance	Э;							
	G.	mailing of a final Office action;								
	Н.	completion of examination as	defined in 37 CFR 41.10	2; or						
	I.	abandonment of the application	า.							
	Telephone inquiries with regard to this decision should be directed to undersigned at (571)272-1642. In his/her absence, calls may be directed to Petition Help Desk at (571) 272-3282.									
	/APRIL N Paralega	/I WISE/ al Specialist, Office of Petitions								

U.S. Patent and Trademark Office PTO-2298 (Rev. 02-2012) Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)

Application Number		17371839		
Filing Date		2021-07-09		
First Named Inventor	G.R. I	Nohan Rao		
Art Unit		2812		
Examiner Name				
Attorney Docket Number		GRTD60-35314		

				U.S.I	PATENTS	Remove
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
	1	4160985	A	1979-07-10	Kamins et al.	
	2	4684971	A	1987-08-04	Payne	
	3	4688063	A	1987-08-18	Lu et al.	
	4	4907058	A	1990-03-06	Sakai	
	5	4994887	A	1991-02-19	Hutter et al.	
	6	5835402	A	1998-11-10	Rao et al.	
	7	6025237	A	2000-02-15	Choi	
	8	6384431	B1	2002-05-07	Takahashi et al.	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT))

(Not	for	submission	under	37	CFR	1.99)
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Application Number		17371839	
Filing Date		2021-07-09	
First Named Inventor	G.R. I	Mohan Rao	
Art Unit		2812	
Examiner Name			
Attorney Docket Number		GRTD60-35314	

	9 6	465862	B1	2002-10-15	Harris		
If you wis	h to add a	dditional U.S. Pater	t citatio	n information p	lease click the Add button.		Add
		1	U.S.P	ATENT APPLI			Remove
Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date	Name of Patentee or Applicant of cited Document	Releva	Columns,Lines where Int Passages or Relevant s Appear
	1	20010028097	A1	2001-10-11	Matsuoka et al.		
	2	20020195656	A1	2002-12-26	Hattori		
	3	20030183856	A1	2003-10-02	Wieczorek et al.		
	4	20070045682	A1	2007-03-01	Hong et al.		
	5	20080142899	A1	2008-06-19	Morris et al.		
	6	20140034997	A1	2014-02-06	Rahimo et al.		
	7	20170243876	A1	2017-08-24	Rao		
If you wis	h to add a	dditional U.S. Publis	-	-	n information please click the Ade	d button	Add Remove

INFORMATION DISCLOSURE Application Number 17371839 Filing Date 2021-07-09 First Named Inventor G.R. Mohan Rao Art Unit 2812 Examiner Name Attorney Docket Number Attorney Docket Number GRTD60-35314

Examiner Initial*	Cite No	Foreign Document Number ³	Country Code²i	Kind Code⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear	T5		
	1	2003051551	JP	A	2003-02-21	Miyamoto et al.		×		
	2	2003218356	JP	A	2003-07-31	Matsumoto et al.				
	3	s6482563	JP	A	1989-03-28	Kondo				
	4	2004049453	wo	A1	2004-06-10	Zheng et al.				
If you wis	h to ac	d additional Foreign I	Patent Docum	ent citation	information p	lease click the Add butto	n Add			
			NON-PA	TENT LITE	RATURE DO	CUMENTS	Remove			
Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.								
	1	IPR2020-00288-Exhibit 1029-Claim Construction District Court 4 20-2020								
	2	IPR2020-00288-Exhibit 2007-Minutes for Markman Hearing Held Via Video Conference Before U.S. District Judge Rodney Gilstrap, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 61								
	3	IPR2020-00288-Petitioner Reply								
	4	IPR2020-00289-00289 Petitioner Reply								

INFORMATION DISCLOSURE Application Number 17371839 Filing Date 2021-07-09 First Named Inventor G.R. Mohan Rao Art Unit 2812 Examiner Name Attorney Docket Number Attorney Docket Number GRTD60-35314

5	IPR2020-00292 - Petition for IPR	
6	IPR2020-00292-Exhibit 2002-Excerpt from Exhibit 4 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on U.S. Patent No. 6,384,431 to Takahashi	
7	IPR2020-00288 - Ex. 1020 - Michael Nastasi and James W. Mayer, Ion Implantation and Synthesis of Materials (2006). 4 pages	
8	IPR2020-00288-Exhibit 2001 - IPR2020-00288 - Excerpt from Exhibit 1 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Morris	
9	IPR2020-00288-Exhibit 2002-xcerpt from Exhibit 2 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Miyamoto	
10	IPR2020-00288-Exhibit 2009-Complaint for Patent Infringement, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 1	
11	IPR2020-00288-Exhibit 2011- Exhibit A to Revised Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 60-1	
12	IPR2020-00288-Exhibit 2012-Samsungs Responsive Claim Construction Brief - District Court	
13	IPR2020-00288-Exhibit 2013- Glew Dec	
14	IPR2020-00288-Exhibit 2014- Excerpt from Exhibit 10 to Appendix A of Samsung Electronics Co., Ltd.'s Invalidity Contentions	
15	IPR2020-00288-Patent Owner Preliminary Response	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT))

(Not for submission	under 37	CFR 1.99
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Application Number		17371839
Filing Date		2021-07-09
First Named Inventor	G.R. I	Mohan Rao
Art Unit		2812
Examiner Name		
Attorney Docket Numbe	r	GRTD60-35314

16	IPR2020-00288-Patent Owner Sur Reply	
17	IPR2020-00288-Petition	
18	IPR2020-00289-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne	
19	IPR2020-00289-Exhibit 1003-Smith Dec	
20	IPR2020-00289-Exhibit 1010- S. M. Sze et al., Semiconductor Devices: Physics and Technology,John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")	
21	IPR2020-00289-Exhibit 1012-Ben G. Streetman, Solid State Electronic Devices, 2nd Ed., Prentice-Hall, 1980 ("Streetman")	
22	IPR2020-00289-Exhibit 2001-Exhibit 1 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Payne	
23	IPR2020-00289-Exhibit 2002- Exhibit 3 to Appendix C of Samsung Electronics Co., Ltd.'s Invalidity Contentions regarding Wieczorek	
24	IPR2020-00289-Exhibit 2011-Behzad Razavi, Design of Analog CMOS Integrated Circuits, 2001 ("Razavi")	
25	IPR2020-00289-Exhibit 2012-Excerpts from Wolf, S., Silicon Processing for the VLSI Era, Vol.4 - Deep-Submicron Process Technology (2002) ("Wolf Vol. 4")	
26	IPR2020-00289-Exhibit 2013-Glew Dec	

INFORMATION DISCLOSURE Application Number 17371839 Filing Date 2021-07-09 First Named Inventor G.R. Mohan Rao Art Unit 2812 Examiner Name Attorney Docket Number Attorney Docket Number GRTD60-35314

27	IPR2020-00289-Patent Owner Pre Resp	
28	IPR2020-00289-Patent Owner Sur reply	
29	IPR2020-00289-Petition	
30	IPR2020-00290-Exhibit 1003-Declaration of Dr. Bruce Smith	
31	IPR2020-00290-Exhibit 1013-Tango, Mega bit Memory Technology	
32	IPR2020-00290-Patent Owner Preliminary Resp	
33	IPR2020-00290-Patent Owner Sur Reply	
34	IPR2020-00290-Petition	
35	IPR2020-00290-Petitioners Reply to Patent Owner Preliminary Response	
36	IPR2020-00291-Exhibit 1003-Declaration of Dr. Bruce Smith	
37	IPR2020-00291-Exhibit 1011- The Insulated Gate Bipolar Transistor: IGBT Theory and Design, Vinod Kumar Khanna, IEEE Press and Wiley-Interscience, 2003	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT))

(Not for submission	under 37	CFR	1.99)
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Application Number		17371839
Filing Date		2021-07-09
First Named Inventor	G.R. I	Mohan Rao
Art Unit		2812
Examiner Name		
Attorney Docket Number		GRTD60-35314

38	IPR2020-00291-Exhibit 1020-S. M. Sze, Physics of Semiconductor Devices, Wiley-Interscience, 2nd Ed., 1981 ("Sze 81")	
39	IPR2020-00291-Exhibit 1021-S. M. Sze, Semiconductor Devices: Physics and Technology, John Wiley & Sons, 2nd Ed., 2002 ("Sze '02")	
40	IPR2020-00291-Exhibit 2001-Exhibit 2 to Appendix B of Samsung Electronics Co., LTD's Invalidity Contentions (Invalidity Contention based on U.S. Patent Application Publication No. 2002/0195656 ("Hattori"))	
41	IPR2020-00291-Exhibit 2013- Declaration of Dr. Alexander D. Glew	
42	IPR2020-00291-Patent Owner Preliminary Resp	
43	IPR2020-00291-Patent Owner Sur Reply	
44	IPR2020-00291-Petition	
45	IPR2020-00291-Petitioners Reply	
46	IPR2020-00292-Exhibit 1003-Declaration of Dr. Bruce Smith	
47	IPR2020-00292-Exhibit 2001-Excerpt from Exhibit 1 to Appendix B of Samsung Electronics Co., Ltd.'s Invalidity Contentions (Invalidity Contention based on "Insulated Gate Bipolar Transistor IGBT Theory and Design" by Vinod Kumar Khanna	
48	IPR2020-00292-Exhibit 2012-Excerpt from Exhibit A to Joint Claim Construction Chart Pursuant to Patent Rule 4-5, Greenthread, LLC v. Samsung Electronics Co., Ltd., et al., Case No. 2:19-CV-147-JRG, Dkt. 53-1 (Mar. 18, 2020)	

INFORMATION DISCLOSURE Application Number 17371839 Filing Date 2021-07-09 First Named Inventor G.R. Mohan Rao Art Unit 2812 Examiner Name Attorney Docket Number GRTD60-35314

	49	IPR20	R2020-00292-Patent Owner Preliminary Response							
If you wish	n to ac	d add	ditional non-patent literature document citation information please click the Add button Add	_						
			EXAMINER SIGNATURE							
Examiner	Signa	ture	Date Considered							
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.										
¹ See Kind Codes of USPTO Patent Documents at <u>www.USPTO.GOV</u> or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here if English language translation is attached.										

	Application Number		17371839	
	Filing Date		2021-07-09	
INFORMATION DISCLOSURE	First Named Inventor	G.R. I	Mohan Rao	
STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Art Unit		2812	
	Examiner Name			
	Attorney Docket Number	ər	GRTD60-35314	

CERTIFICATION STATEMENT

Please see 37 CFR 1.97 and 1.98 to make the appropriate selection(s):

That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(1).

OR

That no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement. See 37 CFR 1.97(e)(2).

See attached certification statement.

The fee set forth in 37 CFR 1.17 (p) has been submitted herewith.

 \times A certification statement is not submitted herewith.

SIGNATURE

A signature of the applicant or representative is required in accordance with CFR 1.33, 10.18. Please see CFR 1.4(d) for the form of the signature.

Signature	/Gregory M. Howison, Reg. #30646/	Date (YYYY-MM-DD)	2021-08-11
Name/Print	Gregory M. Howison	Registration Number	30646

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1 hour to complete, including gathering, preparing and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether the Freedom of Information Act requires disclosure of these record s.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspections or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Electronic Ac	knowledgement Receipt
EFS ID:	43485685
Application Number:	17371839
International Application Number:	
Confirmation Number:	2197
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS
First Named Inventor/Applicant Name:	G.R. MOHAN RAO
Customer Number:	25883
Filer:	Gregory Michael Howison
Filer Authorized By:	
Attorney Docket Number:	GRTD60-35314
Receipt Date:	13-AUG-2021
Filing Date:	09-JUL-2021
Time Stamp:	13:18:02
Application Type:	Utility under 35 USC 111(a)

Payment information:

Submitted wi	th Payment	no						
File Listing:								
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)		
				72988				
1	Information Disclosure Statement (IDS) Form (SB08)	G	RT35314IDSTransmittal.pdf	e400130c27c0fc12e2dff0b81893cb8d6195 2629	no	1		
Warnings:								

Information:								
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2	Information Disclosure Statement (IDS) Form (SB08)	1055703 28cb5924ed51719ac3d30056384a0a0d794 6e1da	no	10				
Warnings:								
Information	:							
		Total Files Size (in bytes)	11	28691				
characterize Post Card, as <u>New Applica</u> If a new appl 1.53(b)-(d) a Acknowledg <u>National Sta</u> If a timely su U.S.C. 371 ar national stag <u>New Interna</u>	vledgement Receipt evidences receip d by the applicant, and including pag s described in MPEP 503. <u>Ations Under 35 U.S.C. 111</u> lication is being filed and the applica nd MPEP 506), a Filing Receipt (37 CF gement Receipt will establish the filing <u>ge of an International Application un</u> abmission to enter the national stage nd other applicable requirements a Fo ge submission under 35 U.S.C. 371 wi <u>tional Application Filed with the USP</u> rnational application is being filed ar	ge counts, where applicable. tion includes the necessary of R 1.54) will be issued in due g date of the application. <u>Inder 35 U.S.C. 371</u> of an international applicati orm PCT/DO/EO/903 indicati Il be issued in addition to the <u>TO as a Receiving Office</u>	It serves as evidence components for a filin course and the date s ion is compliant with ing acceptance of the e Filing Receipt, in du ion includes the nece	of receipt s og date (see hown on th the condition application e course. ssary comp	imilar to a 37 CFR is ons of 35 as a onents for			

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	G.R. Mohan Rao
Serial No.:	17/371,839
Confirmation No.:	2197
Filed:	July 9, 2021
Group:	2812
Examiner:	to be assigned
For:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT
	REGIONS
Iail Ston DD	

Mail Stop DD Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

INFORMATION DISCLOSURE STATEMENT

In accordance with the requirements of 37 C.F.R. §§ 1.56, 1.97, and 1.98, attached please find a Form PTO SB/08 listing information for consideration by the Office in connection with its examination of the above-captioned patent application.

It is brought to Examiner's attention that the references listed on the attached Form PTO SB/08 were previously submitted to the Office in connection with a prior application, namely Application Serial No. 16/947,294, which is relied upon in the current application for an earlier filing date under 35 U.S.C. §120. Pursuant to 37 C.F.R. 1.98(d), copies of such previously submitted items are not provided herein.

Respectfully submitted, MUNCK WILSON MANDALA, LLP Attorneys for Applicant(s)

/Gregory M. Howison, Reg. #30646/

Gregory M. Howison Registration No. 30,646

GMH/als P.O. Drawer 800889 Dallas, Texas 75380 Tel: 972-628-3600 Fax: 972-628-3616 August 11, 2021

Information Disclosure Statement SN: 17/371,839 Atty. Dkt. No. GRTD60-35314

PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875									Application or Docket Number 17/371,839		
APPLICATION AS FILED - PART I (Column 1) (Column 2) SMALL ENTITY									OTHER THAN OR SMALL ENTITY		
	FOR	NUMBE	R FILE		REXTRA	RATE(\$)	FEE(\$)		RATE(\$)	FEE(\$)	
	SIC FEE CFR 1.16(a), (b), or (c))	N	/A	1	N/A	N/A		1	N/A	320	
	ARCH FEE FR 1.16(k), (i), or (m))	N	/A	٦	N/A	N/A]	N/A	700	
	MINATION FEE (FR 1.16(0), (p), or (q)	, N	/A	1	N/A	N/A		1	N/A	800	
	FAL CLAIMS FR 1.16(i))	30	minus	20= *	10			OR	× 100 =	1000	
	EPENDENT CLAI 2FR 1.16(h))	^{MS} 2	minus	3 = *				1	× 480 =	0.00	
FEE	PLICATION SIZ E CFR 1.16(s))	E sheets of p \$310 (\$15 50 sheets	aper, th 5 for sm or fractio	and drawings e le application si all entity) for ea on thereof. See ' CFR 1.16(s).	ze fee due is ch additional					0.00	
MUI	LTIPLE DEPEND	ENT CLAIM PRE	SENT (3	7 CFR 1.16(j))				1		0.00	
* If t	he difference in c	olumn 1 is less th	an zero,	enter "0" in colui	mn 2.	TOTAL		1	TOTAL	2820	
		CATION AS A			1			-			
		(Column 1)		(Column 2)	(Column 3)	SMALL	ENTITY	OR	OTHER THAN SMALL ENTITY		
NT A		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)		RATE(\$)	ADDITIONAL FEE(\$)	
ΜË	Total (37 CFR 1.16(i))	*	Minus	**	=	X =		OR	x =		
AMENDMENT	Independent (37 CFR 1.16(h))	*	Minus	***	=	x =		OR	x =		
AM	Application Size F	ee (37 CFR 1.16(s))									
	FIRST PRESENT	ATION OF MULTIPI	E DEPEN	IDENT CLAIM (37 (CFR 1.16(j))			OR			
	•					TOTAL ADD'L FEE		OR	TOTAL ADD'L FEE		
		(Column 1)		(Column 2)	(Column 3)			_			
AT B		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)		RATE(\$)	ADDITIONAL FEE(\$)	
ΜË	Total (37 CFR 1.16(i))	*	Minus	**	=	X =		OR	x =		
AMENDMENT	Independent (37 CFR 1.16(h))	*	Minus	***	=	x =		OR	x =		
AM	Application Size F	ee (37 CFR 1.16(s))	-		•						
	FIRST PRESENT	ATION OF MULTIPI	E DEPEN	IDENT CLAIM (37 (CFR 1.16(j))			OR			
						TOTAL ADD'L FEE		OR	TOTAL ADD'L FEE		
* ***	* If the "Highest N * If the "Highest N	olumn 1 is less th Number Previous umber Previously Iber Previously Paid	y Paid F Paid For"	or" IN THIS SPA IN THIS SPACE i	CE is less than s less than 3, en	20, enter "20".	in column 1.	_			

UNITED STATES PATENT AND TRADEMARK OFFICE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS PO. Box 1450 Adexandria, Virginia 22313-1450 www.uspic.gov									
APPLICATION NUMBER	FILING or 371(c) DATE	GRP ART UNIT	FIL FEE REC'D	ATTY.DOCKET.NO	TOT CLAIMS IND CLAIMS				
17/371,839	07/09/2021	2812	2820	GRTD60-35314	30 2				
25883 MUNCK WILS P.O. Drawer 8 DALLAS, TX 7	00889	L.L.P		UPDATED F	ONFIRMATION NO. 2197 ILING RECEIPT				

Date Mailed: 08/13/2021

Receipt is acknowledged of this non-provisional utility patent application. The application will be taken up for examination in due course. Applicant will be notified as to the results of the examination. Any correspondence concerning the application must include the following identification information: the U.S. APPLICATION NUMBER, FILING DATE, NAME OF FIRST INVENTOR, and TITLE OF INVENTION. Fees transmitted by check or draft are subject to collection.

Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please submit a written request for a corrected Filing Receipt, including a properly marked-up ADS showing the changes with strike-through for deletions and underlining for additions. If you received a "Notice to File Missing Parts" or other Notice requiring a response for this application, please submit any request for correction to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections provided that the request is grantable.

Inventor(s)

G.R. MOHAN RAO, ALLEN, TX;

Applicant(s)

GREENTHREAD, LLC, Dallas, TX;

Power of Attorney: The patent practitioners associated with Customer Number 25883

Domestic Priority data as claimed by applicant

This application is a CON of 16/947,294 07/27/2020 which is a CON of 16/717,950 12/17/2019 PAT 10734481 which is a CON of 15/590,282 05/09/2017 PAT 10510842 which is a CON of 14/931,636 11/03/2015 PAT 9647070 which is a CON of 14/515,584 10/16/2014 PAT 9190502 which is a CON of 13/854,319 04/01/2013 ABN which is a CON of 11/622,496 01/12/2007 PAT 8421195 which is a DIV of 10/934,915 09/03/2004 ABN

Foreign Applications for which priority is claimed (You may be eligible to benefit from the **Patent Prosecution Highway** program at the USPTO. Please see <u>http://www.uspto.gov</u> for more information.) - None. Foreign application information must be provided in an Application Data Sheet in order to constitute a claim to foreign priority. See 37 CFR 1.55 and 1.76.

Permission to Access Application via Priority Document Exchange: Yes

page 1 of 4

Permission to Access Search Results: Yes

Applicant may provide or rescind an authorization for access using Form PTO/SB/39 or Form PTO/SB/69 as appropriate.

If Required, Foreign Filing License Granted: 07/22/2021

The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is **US 17/371,839 Projected Publication Date:** 11/18/2021

Non-Publication Request: No Early Publication Request: No

Title

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Preliminary Class

438

Statement under 37 CFR 1.55 or 1.78 for AIA (First Inventor to File) Transition Applications: No

PROTECTING YOUR INVENTION OUTSIDE THE UNITED STATES

Since the rights granted by a U.S. patent extend only throughout the territory of the United States and have no effect in a foreign country, an inventor who wishes patent protection in another country must apply for a patent in a specific country or in regional patent offices. Applicants may wish to consider the filing of an international application under the Patent Cooperation Treaty (PCT). An international (PCT) application generally has the same effect as a regular national patent application in each PCT-member country. The PCT process **simplifies** the filing of patent applications on the same invention in member countries, but **does not result** in a grant of "an international patent" and does not eliminate the need of applicants to file additional documents and fees in countries where patent protection is desired.

Almost every country has its own patent law, and a person desiring a patent in a particular country must make an application for patent in that country in accordance with its particular laws. Since the laws of many countries differ in various respects from the patent law of the United States, applicants are advised to seek guidance from specific foreign countries to ensure that patent rights are not lost prematurely.

Applicants also are advised that in the case of inventions made in the United States, the Director of the USPTO must issue a license before applicants can apply for a patent in a foreign country. The filing of a U.S. patent application serves as a request for a foreign filing license. The application's filing receipt contains further information and guidance as to the status of applicant's license for foreign filing.

Applicants may wish to consult the USPTO booklet, "General Information Concerning Patents" (specifically, the section entitled "Treaties and Foreign Patents") for more information on timeframes and deadlines for filing foreign patent applications. The guide is available either by contacting the USPTO Contact Center at 800-786-9199, or it can be viewed on the USPTO website at http://www.uspto.gov/web/offices/pac/doc/general/index.html.

For information on preventing theft of your intellectual property (patents, trademarks and copyrights), you may wish to consult the U.S. Government website, http://www.stopfakes.gov. Part of a Department of Commerce initiative, this website includes self-help "toolkits" giving innovators guidance on how to protect intellectual property in specific page 2 of 4

countries such as China, Korea and Mexico. For questions regarding patent enforcement issues, applicants may call the U.S. Government hotline at 1-866-999-HALT (1-866-999-4258).

LICENSE FOR FOREIGN FILING UNDER

Title 35, United States Code, Section 184

Title 37, Code of Federal Regulations, 5.11 & 5.15

GRANTED

The applicant has been granted a license under 35 U.S.C. 184, if the phrase "IF REQUIRED, FOREIGN FILING LICENSE GRANTED" followed by a date appears on this form. Such licenses are issued in all applications where the conditions for issuance of a license have been met, regardless of whether or not a license may be required as set forth in 37 CFR 5.15. The scope and limitations of this license are set forth in 37 CFR 5.15(a) unless an earlier license has been issued under 37 CFR 5.15(b). The license is subject to revocation upon written notification. The date indicated is the effective date of the license, unless an earlier license of similar scope has been granted under 37 CFR 5.13 or 5.14.

This license is to be retained by the licensee and may be used at any time on or after the effective date thereof unless it is revoked. This license is automatically transferred to any related applications(s) filed under 37 CFR 1.53(d). This license is not retroactive.

The grant of a license does not in any way lessen the responsibility of a licensee for the security of the subject matter as imposed by any Government contract or the provisions of existing laws relating to espionage and the national security or the export of technical data. Licensees should apprise themselves of current regulations especially with respect to certain countries, of other agencies, particularly the Office of Defense Trade Controls, Department of State (with respect to Arms, Munitions and Implements of War (22 CFR 121-128)); the Bureau of Industry and Security, Department of Commerce (15 CFR parts 730-774); the Office of Foreign AssetsControl, Department of Treasury (31 CFR Parts 500+) and the Department of Energy.

NOT GRANTED

No license under 35 U.S.C. 184 has been granted at this time, if the phrase "IF REQUIRED, FOREIGN FILING LICENSE GRANTED" DOES NOT appear on this form. Applicant may still petition for a license under 37 CFR 5.12, if a license is desired before the expiration of 6 months from the filing date of the application. If 6 months has lapsed from the filing date of this application and the licensee has not received any indication of a secrecy order under 35 U.S.C. 181, the licensee may foreign file the application pursuant to 37 CFR 5.15(b).

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page 3 of 4

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page 4 of 4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:	G.R. Mohan RAO
Serial No.:	17/371,839
Confirmation No.:	2197
Filed:	July 9, 2021
Group:	2812
Examiner:	To be assigned
For:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Mail Stop: Missing Parts Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS

In response to the Notice to File Corrected Application Papers dated July 23, 2021, the Applicant submits replacement Drawings marked "Replacement Sheets."

Please charge any additional fees or deficiencies in fees or credit any overpayment to Deposit Account No. 50-0208/GRTD60-35314.

Respectfully submitted, MUNCK WILSON MANDALA, LLP Attorneys for Applicant(s)

/Gregory M. Howison, Reg. #30,646/

Gregory M. Howison Registration No. 30,646

GMH/als P.O. Drawer 800889 Dallas, Texas 75380 Tel: 972-628-3600 Fax: 972-628-3616 August 9, 2021

UNITED ST	ates Patent and Trademai	UNITED STA United State: Address: COMMI PO. Box	a, Virginia 22313-1450			
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE			
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314			
			CONFIRMATION NO. 2197			
25883		FORMALI	TIES LETTER			
MUNCK WILSON MANDA	ALA L.L.P					
P.O. Drawer 800889 DALLAS, TX 75380						
,			Date Mailed: 07/23/2021			

NOTICE TO FILE CORRECTED APPLICATION PAPERS

Filing Date Granted

An application number and filing date have been accorded to this application. The application is informal since it does not comply with the regulations for the reason(s) indicated below. Applicant is given **TWO MONTHS** from the date of this Notice within which to correct the informalities indicated below. Extensions of time may be obtained by filing a petition accompanied by the extension fee under the provisions of 37 CFR 1.136(a).

The required item(s) identified below must be timely submitted to avoid abandonment:

- Replacement drawings in compliance with 37 CFR 1.84 and 37 CFR 1.121(d) are required. The drawings submitted are not acceptable because:
 - The drawings contain excessive text. Suitable descriptive legends may be used, or may be required by the Examiner where necessary for understanding of the drawing but should contain as few words as possible (see 37 CFR 1.84(o)). See Figure(s) 3D.

Applicant is cautioned that correction of the above items may cause the specification and drawings page count to exceed 100 pages. If the specification and drawings exceed 100 pages, applicant will need to submit the required application size fee.

Replies must be received in the USPTO within the set time period or must include a proper Certificate of Mailing or Transmission under 37 CFR 1.8 with a mailing or transmission date within the set time period. For more information and a suggested format, see Form PTO/SB/92 and MPEP 512.

Replies should be mailed to:

Mail Stop Missing Parts Commissioner for Patents P.O. Box 1450 Alexandria VA 22313-1450

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/hnguyen/





GRTD60-35314

4





FIGURE 2 Prior art



FIGURE 3A Prior art



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FIGURE 3B Prior art


GRTD60-35314

FIGURE 3C Prior art



Prior art FIGURE 3D

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FIGURE 4

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FIGURE 5A

GRTD60-35314



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FIGURE 5B



FIGURE 5C

Electronic Ac	Electronic Acknowledgement Receipt					
EFS ID:	43455028					
Application Number:	17371839					
International Application Number:						
Confirmation Number:	2197					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
First Named Inventor/Applicant Name:	g.R. Mohan Rao					
Customer Number:	25883					
Filer:	Gregory Michael Howison					
Filer Authorized By:						
Attorney Docket Number:	GRTD60-35314					
Receipt Date:	11-AUG-2021					
Filing Date:	09-JUL-2021					
Time Stamp:	12:00:40					
Application Type:	Utility under 35 USC 111(a)					

Payment information:

Submitted with	Payment		no				
File Listing	:						
Document Number	Document Description		File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)	
1				140749			
	Applicant Response to Pre-Exam Formalities Notice	GR	T35314ResponseNTCCORRP PRS.pdf	c5bf953560418734698dda9fb92096cd615 ce9b1	no	3	
Warnings:		•			I		

Information								
	Drawings-only black and white line		3531672					
2	drawings	GRT35314DWGS.pdf	969dd9563ede422ad99ba4e86bd6299ca6 0c5702	no	10			
Warnings:		•	•					
Information								
		Total Files Size (in bytes)	36	72421				
characterize Post Card, as <u>New Applica</u> If a new appl 1.53(b)-(d) a Acknowledg <u>National Sta</u> If a timely su U.S.C. 371 ar national stag <u>New Interna</u> If a new inter an internatio	This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503. New Applications Under 35 U.S.C. 111 If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application. National Stage of an International Application under 35 U.S.C. 371 If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course. New International Application Filed with the USPTO as a Receiving Office If a new international application is being filed and the international application includes the necessary components for an international Application set on the international Application set on the international Application is being filed and the international application includes the necessary components for an international Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning							

	United State	<u>s Patent</u>	and Tradem	UNITED STATES	
APPLICATION NUMBER	FILING or 371(c) DATE	GRP ART UNIT	FIL FEE REC'D	ATTY.DOCKET.NO	TOT CLAIMS IND CLAIMS
17/371,839	07/09/2021	2812	2820	GRTD60-35314	30 2
				CC	ONFIRMATION NO. 2197
25883				FILING REC	EIPT
MUNCK WILS P.O. Drawer 8 DALLAS, TX 7	00889	L.L.P			000000 1271 85 59 5

Date Mailed: 07/23/2021

Receipt is acknowledged of this non-provisional utility patent application. The application will be taken up for examination in due course. Applicant will be notified as to the results of the examination. Any correspondence concerning the application must include the following identification information: the U.S. APPLICATION NUMBER, FILING DATE, NAME OF FIRST INVENTOR, and TITLE OF INVENTION. Fees transmitted by check or draft are subject to collection.

Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please submit a written request for a corrected Filing Receipt, including a properly marked-up ADS showing the changes with strike-through for deletions and underlining for additions. If you received a "Notice to File Missing Parts" or other Notice requiring a response for this application, please submit any request for correction to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections provided that the request is grantable.

Inventor(s)

G.R. MOHAN RAO, ALLEN, TX;

Applicant(s)

GREENTHREAD, LLC, Dallas, TX;

Power of Attorney: The patent practitioners associated with Customer Number 25883

Domestic Priority data as claimed by applicant

This application is a CON of 16/947,294 07/27/2020 which is a CON of 16/717,950 12/17/2019 PAT 10734481 which is a CON of 15/590,282 05/09/2017 PAT 10510842 which is a CON of 14/931,636 11/03/2015 PAT 9647070 which is a CON of 14/515,584 10/16/2014 PAT 9190502 which is a CON of 13/854,319 04/01/2013 ABN which is a CON of 11/622,496 01/12/2007 PAT 8421195 which is a DIV of 10/934,915 09/03/2004 ABN

Foreign Applications for which priority is claimed (You may be eligible to benefit from the **Patent Prosecution Highway** program at the USPTO. Please see <u>http://www.uspto.gov</u> for more information.) - None. Foreign application information must be provided in an Application Data Sheet in order to constitute a claim to foreign priority. See 37 CFR 1.55 and 1.76.

Permission to Access Application via Priority Document Exchange: Yes

page 1 of 4

Permission to Access Search Results: Yes

Applicant may provide or rescind an authorization for access using Form PTO/SB/39 or Form PTO/SB/69 as appropriate.

If Required, Foreign Filing License Granted: 07/22/2021

The country code and number of your priority application, to be used for filing abroad under the Paris Convention, is **US 17/371,839 Projected Publication Date:** To Be Determined - pending completion of Corrected Papers **Non-Publication Request:** No **Early Publication Request:** No **Title**

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Preliminary Class

438

Statement under 37 CFR 1.55 or 1.78 for AIA (First Inventor to File) Transition Applications: No

PROTECTING YOUR INVENTION OUTSIDE THE UNITED STATES

Since the rights granted by a U.S. patent extend only throughout the territory of the United States and have no effect in a foreign country, an inventor who wishes patent protection in another country must apply for a patent in a specific country or in regional patent offices. Applicants may wish to consider the filing of an international application under the Patent Cooperation Treaty (PCT). An international (PCT) application generally has the same effect as a regular national patent application in each PCT-member country. The PCT process **simplifies** the filing of patent applications on the same invention in member countries, but **does not result** in a grant of "an international patent" and does not eliminate the need of applicants to file additional documents and fees in countries where patent protection is desired.

Almost every country has its own patent law, and a person desiring a patent in a particular country must make an application for patent in that country in accordance with its particular laws. Since the laws of many countries differ in various respects from the patent law of the United States, applicants are advised to seek guidance from specific foreign countries to ensure that patent rights are not lost prematurely.

Applicants also are advised that in the case of inventions made in the United States, the Director of the USPTO must issue a license before applicants can apply for a patent in a foreign country. The filing of a U.S. patent application serves as a request for a foreign filing license. The application's filing receipt contains further information and guidance as to the status of applicant's license for foreign filing.

Applicants may wish to consult the USPTO booklet, "General Information Concerning Patents" (specifically, the section entitled "Treaties and Foreign Patents") for more information on timeframes and deadlines for filing foreign patent applications. The guide is available either by contacting the USPTO Contact Center at 800-786-9199, or it can be viewed on the USPTO website at http://www.uspto.gov/web/offices/pac/doc/general/index.html.

For information on preventing theft of your intellectual property (patents, trademarks and copyrights), you may wish to consult the U.S. Government website, http://www.stopfakes.gov. Part of a Department of Commerce initiative, this website includes self-help "toolkits" giving innovators guidance on how to protect intellectual property in specific page 2 of 4

countries such as China, Korea and Mexico. For questions regarding patent enforcement issues, applicants may call the U.S. Government hotline at 1-866-999-HALT (1-866-999-4258).

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Title 35, United States Code, Section 184

Title 37, Code of Federal Regulations, 5.11 & 5.15

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PATENT APPLICATION FEE DETERMINATION RECORD Substitute for Form PTO-875								Application or Docket Number 17/371,839		
	APPLICATION AS FILED - PART I (Column 1) (Column 2) SMALL ENTITY							OR	OTHER TH	
	FOR	NUMBE	R FILE		REXTRA	RATE(\$)	FEE(\$)		RATE(\$)	FEE(\$)
	SIC FEE FR 1.16(a), (b), or (c))	N	/A	1	N/A	N/A]	N/A	320
	ARCH FEE FR 1.16(k), (i), or (m))	N	/A	1	N/A	N/A		1	N/A	700
	MINATION FEE FR 1.16(0), (p), or (q)	N	/A	1	N/A	N/A		1	N/A	800
TOT	AL CLAIMS FR 1.16(i))	30	minus	20= *	10			OR	× 100 =	1000
IND	EPENDENT CLAI	^{MS} 2	minus	3 = *				1	× 480 =	0.00
API FEE	PLICATION SIZ	E sheets of p \$310 (\$15 50 sheets	aper, th 5 for sm or fractio	and drawings e le application si all entity) for ea on thereof. See ' CFR 1.16(s).	ze fee due is ch additional					0.00
MUI	TIPLE DEPEND	ENT CLAIM PRE	SENT (3	7 CFR 1.16(j))				1		0.00
*lft	he difference in c	olumn 1 is less th	an zero,	enter "0" in colu	mn 2.	TOTAL		1	TOTAL	2820
		CATION AS A			1			-		
		(Column 1)		(Column 2)	(Column 3)	SMALL ENTITY		OR	OTHER THAN SMALL ENTITY	
NT A		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)		RATE(\$)	ADDITIONAL FEE(\$)
ΜË	Total (37 CFR 1.16(i))	*	Minus	**	=	x =		OR	x =	
AMENDMENT	Independent (37 CFR 1.16(h))	*	Minus	***	=	x =		OR	x =	
AM	Application Size F	ee (37 CFR 1.16(s))								
	FIRST PRESENT	ATION OF MULTIPL	E DEPEN	IDENT CLAIM (37 (CFR 1.16(j))			OR		
	1					TOTAL ADD'L FEE		OR	TOTAL ADD'L FEE	
	-	(Column 1)		(Column 2)	(Column 3)		_	-		
LT B		CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE(\$)	ADDITIONAL FEE(\$)		RATE(\$)	ADDITIONAL FEE(\$)
ΜË	Total (37 CFR 1.16(i))	*	Minus	**	=	X =		OR	x =	
AMENDMENT	Independent (37 CFR 1.16(h))	*	Minus	***	=	× =		OR	x =	
Application Size Fee (37 CFR 1.16(s))										
	FIRST PRESENT	ATION OF MULTIPL	E DEPEN	IDENT CLAIM (37 (CFR 1.16(j))			OR		
						TOTAL ADD'L FEE		OR	TOTAL ADD'L FEE	
**	 If the entry in cc If the "Highest N If the "Highest Num 	Number Previous umber Previously I	y Paid F Paid For"	or" IN THIS SPA IN THIS SPACE i	CE is less than s less than 3, en	20, enter "20".	x in column 1.			

UNITED ST	ates Patent and Trademan	UNITED STA United State: Address: COMMI PO. Box	a, Virginia 22313-1450	
APPLICATION NUMBER	FILING OR 371(C) DATE	FIRST NAMED APPLICANT	ATTY. DOCKET NO./TITLE	
17/371,839	07/09/2021	G.R. MOHAN RAO	GRTD60-35314	
			CONFIRMATION NO. 2197	
25883		FORMALITIES LETTER		
MUNCK WILSON MAND/ P.O. Drawer 800889 DALLAS, TX 75380	ALA L.L.P		OC000000127165596*	
			Date Mailed: 07/23/2021	

NOTICE TO FILE CORRECTED APPLICATION PAPERS

Filing Date Granted

An application number and filing date have been accorded to this application. The application is informal since it does not comply with the regulations for the reason(s) indicated below. Applicant is given **TWO MONTHS** from the date of this Notice within which to correct the informalities indicated below. Extensions of time may be obtained by filing a petition accompanied by the extension fee under the provisions of 37 CFR 1.136(a).

The required item(s) identified below must be timely submitted to avoid abandonment:

- Replacement drawings in compliance with 37 CFR 1.84 and 37 CFR 1.121(d) are required. The drawings submitted are not acceptable because:
 - The drawings contain excessive text. Suitable descriptive legends may be used, or may be required by the Examiner where necessary for understanding of the drawing but should contain as few words as possible (see 37 CFR 1.84(o)). See Figure(s) 3D.

Applicant is cautioned that correction of the above items may cause the specification and drawings page count to exceed 100 pages. If the specification and drawings exceed 100 pages, applicant will need to submit the required application size fee.

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TRANSMITTAL FOR POWER OF ATTORNEY TO ONE OR MORE REGISTERED PRACTITIONERS

NOTE: This form is to be submitted with the Power of Attorney by Applicant form (PTO/AIA/82B) to identify the application to which the Power of Attorney is directed, in accordance with 37 CFR 1.5, unless the application number and filing date are identified in the Power of Attorney by Applicant form. If neither form PTO/AIA/82A nor form PTO/AIA82B identifies the application to which the Power of Attorney is lirected, the Power of Attorney will not be recognized in the application.						
Application Number						
Filing Date						
First Named Inventor	G.R. MOHAN RAO					
Title	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
Art Unit						
Examiner Name						
Attorney Docket Number	GRTD60-35314					
SIGNATURE of A	pplicant or Patent Practitioner					
Signature /Greg	ory M. Howison, Reg. #30646/	Date (Optional)				
Name GREGO	GREGORY M. HOWISON		30,646			
Title (if Applicant is a juristic entity)						
Applicant Name (if Applicant is a juristic entity)						
NOTE: This form must be signed more than one applicant, use mul	in accordance with 37 CFR 1.33. See 37 CFR 1.4(d) for the second se	or signature requir	ements and certifications. If			
*Total of <u>ONE</u>	forms are submitted.					

This collection of information is required by 37 CFR 1.131, 1.32, and 1.33. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 3 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

POWER OF ATTORNEY BY APPLICANT

I hereby revoke all previous powers of attorney given in the application identified in <u>either</u> the attached transmittal letter or the boxes below.								
	ication Number	Filing Date						
	e boxes above may be left blank if information i	•						
		owing Customer Number as my/our attorney(s) or agent(s), and Coffice connected therewith for the application referenced in						
	the attached transmittal letter (form PTO/AIA/82A) or identified above:							
OR								
all business in the l		FO/AIA/82C) as my/our attorney(s) or agent(s), and to transact nected therewith for the patent application referenced in the (Note: Complete form PTO/AIA/82C.)						
		he application identified in the attached transmittal						
letter or the boxes abo	ve to: iated with the above-mentioned Customer Num	ber						
OR	,							
استنبا	iated with Customer Number:							
OR Firm or	[
Individual Name								
Address								
City	State	Zip						
Country Telephone	Em	ail						
	plicant is a juristic entity, list the Applicant name							
r ant the oppreant to the op	picant is a junsic entity, list the Applicant name	s in the box).						
GREENTHRE	EAD, LLC							
Inventor or Joint In	ventor (title not required below)							
Legal Representati	ve of a Deceased or Legally Incapacitated Inve	entor (title not required below)						
Assignee or Perso	n to Whom the Inventor is Under an Obligation	to Assign (provide signer's title if applicant is a juristic entity)						
	wise Shows Sufficient Proprietary Interest (e.g. ncurrently being filed with this document) (prov	, a petition under 37 CFR 1.46(b)(2) was granted in the ide signer's title if applicant is a juristic entity)						
	SIGNATURE of Applica							
The undersigned (whose the signature	hiller's supplied below) is authorized to act on beha	alf of the applicant (e.g., where the applicant is a juristic entity).						
Name 6	Hilip W Scher JR							
Title	MANAGER	GREENTHREAD, LLC						
NOTE: Signature - This f		e with 37 CFR 1.33. See 37 CFR 1.4 for signature requirements						
Total of ONE	forms are submitted.							
USPTO to process) an application. Including gathering, preparing, and of time you require to complete this	Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1. submitting the completed application form to the USPTO. Til form and/or suggestions for reducing this burden, should be x 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES (ulred to obtain or retain a benefit by the public which is to file (and by the 11 and 1.14. This collection is estimated to take 3 minutes to complete, ne will vary depending upon the individual case. Any comments on the amount sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. DR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner						

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

PTO/AIA/01 (06-12) Approved for use through 01/31/2014. OMB 0861-6032 U.S. Palent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Discours are required to respond to a collection of information unless 8 disclays a valid OMB control number.

DEC	LARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN APPLICATION DATA SHEET (37 CFR 1.76)				
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				
As the belo	w named inventor, I hereby declare that:				
This declar is directed					
	United States application or PCT International application number				
	filed on				
The above-	dentified application was made or authorized to be made by me.				
I believe the	t I am the original inventor or an original joint inventor of a claimed invention in the application.				
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inventor: Signature:	G.R. Mohan Rao Dete (Optional): Sept 30, 2015 URMohan Rao				
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ABSTRACT

Most semiconductor devices manufactured today, have uniform dopant concentration, either in the lateral or vertical device active (and isolation) regions. By grading the dopant concentration, the performance in various semiconductor devices can be significantly improved. Performance improvements can be obtained in application specific areas like increase in frequency of operation for digital logic, various power MOSFET and IGBT ICs, improvement in refresh time for DRAMs, decrease in programming time for nonvolatile memory, better visual quality including pixel resolution and color sensitivity for imaging ICs, better sensitivity for varactors in tunable filters, higher drive capabilities for JFETs, and a host of other applications.

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WHAT IS CLAIMED IS:

1.	A VLSI semiconductor device, comprising:
	a substrate of a first doping type at a first doping level having a surface;
	a first active region disposed adjacent the surface with a second doping type
	opposite in conductivity to the first doping type and within which transistors can be formed;
	a second active region separate from the first active region disposed adjacent to the
	first active region and within which transistors can be formed;
	transistors formed in at least one of the first active region or second active region;
	at least a portion of at least one of the first and second active regions having at least
	one graded dopant concentration to aid carrier movement from the first and second active
	regions towards an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface towards the area of the substrate where there are no active regions, wherein at least some of the transistors form digital logic of the VLSI semiconductor device.

2. The VLSI semiconductor device of Claim 1, wherein the substrate is a p-type substrate.

3. The VLSI semiconductor device of Claim 1, wherein the substrate has epitaxial silicon on top of a nonepitaxial substrate.

The VLSI semiconductor device of Claim 1, wherein the first active region and second 4. active region contain digital logic formed by one of either p-channel and n-channel devices.

5. The VLSI semiconductor device of Claim 1, wherein the first active region and second active region contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.

6. The VLSI semiconductor device of Claim 1, wherein the first active region and second active region are each separated by at least one isolation region.

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7. The VLSI semiconductor device of Claim 1, wherein the graded dopant is fabricated with an ion implantation process.

8. The VLSI semiconductor device of Claim 1, wherein the first and second active regions are formed adjacent the first surface of the substrate.

9. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the first active region or the second active region are either p-type or n-type.

10. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the first active region are both p-type and n-type.

11. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant concentration in the second active region are both p-type and n-type.

12. The VLSI semiconductor device of Claim 1, wherein dopants of the graded dopant region in the well region are both p-type and n-type.

13. The VLSI semiconductor device of claim 1, wherein the transistors which can be formed in the first and second active regions are CMOS digital logic transistors requiring at least a source, a drain, a gate and a channel.

14. The VLSI semiconductor device of Claim 1, wherein the device is a dynamic random access memory (DRAM).

15. The VLSI semiconductor device of Claim 1, wherein the device is a complementary metal oxide semiconductor (CMOS) with a nonepitaxial substrate.

16. The VLSI semiconductor device of Claim 1, wherein the device is a flash memory.

17. The VLSI semiconductor device of Claim 1, wherein the device comprises digital logic and capacitors.

18. The VLSI semiconductor device of Claim 1, wherein the device is central processing unit.

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19. The VLSI semiconductor device of Claim 1, wherein the device is an image sensor.

20. The VLSI semiconductor device of Claim 1, wherein each of the first and second active regions are in the lateral or vertical direction.

21. A VLSI semiconductor device, comprising:

a substrate of a first doping type at a first doping level having a surface;

a first active region disposed adjacent the surface of the substrate with a second doping type opposite in conductivity to the first doping type and within which transistors can be formed in the surface thereof;

a second active region separate from the first active region disposed adjacent to the first active region and within which transistors can be formed in the surface thereof;

transistors formed in at least one of the first active region or second active region;

at least a portion of at least one of the first and second active regions having at least one graded dopant concentration to aid carrier movement from the surface to an area of the substrate where there are no active regions; and

at least one well region adjacent to the first or second active region containing at least one graded dopant region, the graded dopant region to aid carrier movement from the surface to the area of the substrate where there are no active regions, and wherein the graded dopant concentration is linear, quasilinear, error function, complementary error function, or any combination thereof.

22. The VLSI semiconductor device of Claim 21, wherein the substrate is an n-type substrate.

23. The VLSI semiconductor device of Claim 21, wherein the substrate is a p-type substrate.

24. The VLSI semiconductor device of Claim 21, wherein the substrate has epitaxial silicon on top of a nonepitaxial substrate.

25. The VLSI semiconductor device of Claim 21, wherein the first active region and second active region contain at least one of either p-channel and n-channel devices.

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26. The VLSI semiconductor device of Claim 21, wherein the first active region and second active region contain either p-channel or n-channel devices in n-wells or p-wells, respectively, and each well has at least one graded dopant.

27. The VLSI semiconductor device of Claim 21, wherein the first active region and second active region are each separated by at least one isolation region.

28. The VLSI semiconductor device of Claim 21, wherein dopants of the graded dopant concentration in the first active region or the second active region are either p-type or n-type.

29. The VLSI semiconductor device of Claim 21, wherein dopants of the graded dopant concentration in the first active region are both p-type and n-type.

30. The VLSI semiconductor device of Claim 21, wherein dopants of the graded dopant concentration in the second active region are both p-type and n-type.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE APPLICATION FOR UNITED STATES PATENT

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

Inventor(s):

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application is a Continuation of U.S. Patent Application No. 16/947,294, filed July 27, 2020, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, which is a Continuation of U.S. Patent Application No. 16/717,950, filed December 17, 2019, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 10,734,481 on August 04, 2020. U.S. Patent Application No. 16/717,950 is a Continuation of U.S. Patent Application No. 15/590,282, filed May 9, 2017, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 10,510, 842 on December 17, 2019, which is a Continuation of U.S. Patent Application No. 14/931,636, filed November 3, 2015, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 9,647,070 on May 9, 2017, which is Continuation of U.S. Patent Application No. 14/515,584, filed October 16, 2014, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 9,190,502 on November 17, 2015, which is a Continuation of U.S. Patent Application No. 13/854,319 filed April 1, 2013, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, which is a Continuation of 11/622,496, filed January 12, 2007, entitled SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS, issued as U.S. Patent No. 8,421,195 on April 16, 2013, which is a Divisional of U.S. Patent Application No. 10/934,915, filed September 3, 2004. The disclosures of which are incorporated herein by reference in their entirety.

TECHNICAL FIELD

[0002] This present invention relates to all semiconductor devices and systems. Particularly it applies to diffused diodes, avalanche diodes, Schottky devices, power MOS transistors, JFET's, RF bipolar transistors, IGBTs (Insulated Gate Bipolar Transistors), varactors, digital VLSI, mixed signal circuits and sensor devices including camera ICs employing CCD (Charge Coupled Device) as well as CMOS technologies.

PATENT

BACKGROUND

[0003] Bipolar Junction Transistors (BJT) are classified as minority carrier devices because minority carriers are the principle device conduction mechanism. However, majority carriers also play a small but finite role in modulating the conductivity in BJTs. Consequently, both carriers (electrons and holes) play a role in the switching performance of BJTs. The maximum frequency of operation in BJTs is limited by the base transit time as well as the quick recombination of the majority carriers when the device is switched off (prior to beginning the next cycle). The dominant carrier mechanism in BJTs is carrier diffusion. The carrier drift current component is fairly small, especially in uniformly doped base BJTs. Efforts have been made in graded base transistors to create an aiding drift field to enhance the diffusing minority carrier's speed from emitter to collector. However, most semiconductor devices, including various power MOSFETs (traditional, DMOS, lateral, vertical and a host of other configurations), IGBT's (Insulated Gated Base Transistors), still use a uniformly doped 'drift epitaxial' region in the base. FIG. 1 shows the relative doping concentration versus distance in a BJT. FIG. 2 shows the uniformly doped epi region in an IGBT. In contrast to BJTs, MOS devices are majority carrier devices for conduction. The conduction is channel dominated. The channel can be a surface in one plane in planar devices. The surface can also be on the sidewalls in a vertical device. Other device architectures to combine planar and vertical conductions are also possible. The maximum frequency of operation is dictated primarily by source-drain separation distance. Most MOS devices use a uniformly doped substrate (or a well region). When a MOSFET is optimally integrated with a BJT in a monolithic fashion, an IGBT results. The IGBT inherits the advantages of both MOSFET and BJT. It also brings new challenges because the required characteristics (electron transit and hole recombination as fast as possible in n-channel IGBT) necessitate different dopant gradients either in the same layer at different positions, or at the interfaces of similar or dissimilar layers.

[0004] Retrograde wells have been attempted, with little success, to help improve soft error immunity in SRAMs and visual quality in imaging circuits. FIG. 3A shows a typical CMOS VLSI device employing a twin well substrate, on which active devices are subsequently fabricated. FIGS. 3B, 3C, and 3D illustrate device cross sections, as practiced today. Retrograde and halo wells have also been attempted to improve refresh time in DRAMs (dynamic random-access memories), as well as, reducing dark current (background noise) and enhance RGB (Red, Green,

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Blue) color resolution in digital camera ICs. Most of these techniques either divert the minority carriers away from the active regions of critical charge storage nodes at the surface, or, increase minority carrier density locally as the particular application requires.

BRIEF DESCRIPTION OF THE DRAWINGS

[0005] For a more complete understanding of the present invention, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

[0006] FIG. 1 illustrates the relative doping profiles of emitter, base and collector for the two most popular bipolar junction transistors: namely, uniform base ("A") and graded base ("B");

[0007] FIG. 2 illustrates the cross section of a commercial IGBT with a uniform epitaxial drift region (base);

[0008] FIGS. 3A, 3B, 3C, and 3D illustrate cross sections of commonly used prior art CMOS silicon substrates; FIG. 3A showing a typical prior art IC with two wells (one n⁻well in which p-channel transistors are subsequently fabricated and one p⁻well in which n-channel transistors are subsequently fabricated); FIG 3B showing a prior art EEPROM (Electronically Erasable Programmable Read-Only Memory) memory cell having a tunnel insulator; FIG. 3C showing a prior art DRAM memory cell; and FIG. 3D showing a prior art NAND flash memory cell;

[0009] FIG. 4 illustrates the cross section of an IGBT, using one embodiment of the invention described here, where the dopant is optimally graded in the epitaxial drift region; and

[0010] FIGS. 5A, 5B, and 5C illustrate the cross sections of a CMOS silicon substrate with two wells and an underlying layer using embodiments of the invention to improve performance in each application—VLSI logic, DRAM/image IC, nonvolatile memory IC.

DETAILED DESCRIPTION

[0011] The relative doping concentrations of emitter and collector regions varies from 10^{18} to 10^{20} /cm³, whereas the base region is 10^{14} to 10^{16} /cm³ depending on the desired characteristics of the BJT. In graded base p-n-p transistors, the donor dopant concentration may be 10 to $100 \times$ at the emitter-base junction, relative to the base-collector junction (1×). The gradient can be linear, quasi linear, exponential or complimentary error function. The relative slope of the donor concentration throughout the base creates a suitable aiding drift electric field, to help the holes (p-n-p transistor) transverse from emitter to collector. Since the aiding drift electric field helps hole conduction, the current gain at a given frequency is enhanced, relative to a uniformly-doped (base) BJT. The improvement in cut-off frequency (or, frequency at unity gain, f_T) can be as large as $2\times-5\times$. Similar performance improvements are also applicable to n-p-n transistors.

[0012] As illustrated in FIG. 4, in one embodiment according to the invention, a donor gradient is established from the emitter-drift epitaxial base region junction of the punch-through IGBT, to the drift epitaxial base region—n⁺ buffer layer boundary (electrons in this case are accelerated in their transit from emitter to collector). The "average" base resistance is optimized so that conductivity modulation and lifetime (for minority carriers) in the base region are not compromised. By sweeping the carriers towards the n⁺ buffer region a number of advantages are obtained. First, the frequency of operation (combination of ton and toff as is known in the IGBT commercial nomenclature) can be enhanced. Second, and maybe more importantly, during toff, holes can be recombined much quicker at the n⁺ buffer layer, compared to the uniformly doped n^{-} epitaxial drift region by establishing a different dopant gradient near the n^{+} buffer layer. It should be noted that the drift region can also be a non-epitaxial silicon substrate. Although epitaxy enhances lifetime, it is not mandatory. Different layers of dopant regions can be transferred through wafer to wafer bonding (or other similar transfer mechanisms) for eventual device fabrication. The "reverse recovery time" for an IGBT is significantly improved due to the optimized graded dopant in the so called "drift region" as well as at the interfaces of the drift region. Graded dopants can also be implemented in the n⁺ buffer layer as well as other regions adjacent to the respective layers. Two important performance enhancements are the result of dopant gradients. For example, in an n-channel IGBT, electrons can be swept from source to drain rapidly, while at the same time holes can be recombined closer to the n⁺ buffer layer. This can improve ton and toff in the same device.

[0013] As illustrated in FIGS. 5A, 5B, and 5C, donor gradient is also of benefit to very large scale integrated circuits (VLSI)—VLSI logic, DRAM, nonvolatile memory like NAND flash. Spurious minority carriers can be generated by clock switching in digital VLSI logic and memory ICs. These unwanted carriers can discharge dynamically-held "actively held high" nodes. In most cases, statically-held nodes (with V_{cc}) cannot be affected. Degradation of refresh time in DRAMs is one of the results, because the capacitor holds charge dynamically. Similarly, degradation of CMOS digital images in digital imaging ICs is another result of the havoc caused by minority carriers. Pixel and color resolution can be significantly enhanced in imaging ICs with the embodiments described herein. Creating "subterranean" recombination centers underneath the wells (gold doping, platinum doping) as is done in some high-voltage diodes is not practical for VLSI circuits. Hence, a novel technique is described herein which creates a drift field to sweep these unwanted minority carriers from the active circuitry at the surface into the substrate in a monolithic die as quickly as possible. In a preferred embodiment, the subterranean n-layer has a graded donor concentration to sweep the minority carriers deep into the substrate. One or more of such layers can also be implemented through wafer to wafer bonding or similar "transfer" mechanisms. This n-layer can be a deeply-implanted layer. It can also be an epitaxial layer. As desired, the n-well and p-wells can also be graded or retrograded in dopants to sweep those carriers away from the surface as well. The graded dopant can also be implemented in surface channel MOS devices to accelerate majority carriers towards the drain. To decrease programming time in nonvolatile memory devices, carriers should be accelerated towards the surface when programming of memory cells is executed. The graded dopant can also be used to fabricate superior Junction Field-Effect transistors where the "channel pinch-off" is controlled by a graded channel instead of a uniformly doped channel (as practiced in the prior art).

[0014] One of ordinary skill and familiarity in the art will recognize that the concepts taught herein can be customized and tailored to a particular application in many advantageous ways. For instance, minority carriers can be channeled to the surface to aid programming in nonvolatile memory devices (NOR, NAND, multivalued-cell). Moreover, single-well, and triple-well CMOS fabrication techniques can also be optimized to incorporate these embodiments individually and collectively. Any modifications of such embodiments (described here) fall within the spirit and scope of the invention. Hence, they fall within the scope of the claims described below.

[0015] Although the invention has been described with reference to specific embodiments, these descriptions are not meant to be construed in a limiting sense. Various modifications of the disclosed embodiments, as well as alternative embodiments of the invention will become apparent to persons skilled in the art upon reference to the description of the invention. It should be appreciated by those skilled in the art that the conception and the specific embodiment disclosed may be readily utilized as a basis for modifying or designing other structures for carrying out the same purposes of the present invention. It should also be realized by those skilled in the art that such equivalent constructions do not depart from the spirit and scope of the invention as set forth in the appended claims.

[0016] It is therefore, contemplated that the claims will cover any such modifications or embodiments that fall within the true scope of the invention.

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Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314			
		Application Number				
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS					
The application data sheet is part of the provisional or nonprovisional application for which it is being submitted. The following form contains the bibliographic data arranged in a format specified by the United States Patent and Trademark Office as outlined in 37 CFR 1.76. This document may be completed electronically and submitted to the Office in electronic format using the Electronic Filing System (EFS) or the document may be printed and included in a paper filed application.						

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Title of the Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS						
Attorney Docket Number	GRTD60-35314	GRTD60-35314 Small Entity Status Claimed					
Application Type	Nonprovisional	Nonprovisional 🗸					
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For the purposes of a filing date under 37 CFR 1.53(b), the description and any drawings of the present application are replaced by this reference to the previously filed application, subject to conditions and requirements of 37 CFR 1.57(a).

Application number of the previously filed application	Filing date (YYYY-MM-DD)	Intellectual Property Authority or Country		

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Prior Application Status	Pending -		Remove	
Application Number	Continuity Type	Prior Application Number	Filing or 371(c) Date (YYYY-MM-DD)	
	Continuation of	16947294	2020-07-27	

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This section allows for the applicant to claim priority to a foreign application. Providing this information in the application data sheet constitutes the claim for priority as required by 35 U.S.C. 119(b) and 37 CFR 1.55. When priority is claimed to a foreign application that is eligible for retrieval under the priority document exchange program (PDX)ⁱ the information will be used by the Office to automatically attempt retrieval pursuant to 37 CFR 1.55(i)(1) and (2). Under the PDX program, applicant bears the ultimate responsibility for ensuring that a copy of the foreign application is received by the Office from the participating foreign intellectual property office, or a certified copy of the foreign priority application is filed, within the time period specified in 37 CFR 1.55(g)(1).

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Application Data Sheet 37 CFR 1.76			Attorney Docket Number		GRTD60-35314	
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Title of Invention	SEMIC	ONDUCTOR DEVICE	S WITH G	RADED DOPANT RE	GIONS	
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Statement under 37 CFR 1.55 or 1.78 for AIA (First Inventor to File) Transition Applications

This application (1) claims priority to or the benefit of an application filed before March 16, 2013 and (2) also contains, or contained at any time, a claim to a claimed invention that has an effective filing date on or after March
 16, 2013.

NOTE: By providing this statement under 37 CFR 1.55 or 1.78, this application, with a filing date on or after March 16, 2013, will be examined under the first inventor to file provisions of the AIA.

Application Data Sheet 37 CFR 1.76		Attorney Docket Number GRTD60-35314			
		Application Number			
Title of Invention	SEMICONDUCTOR DEVICES	DEVICES WITH GRADED DOPANT REGIONS			

Authorization or Opt-Out of Authorization to Permit Access:

When this Application Data Sheet is properly signed and filed with the application, applicant has provided written authority to permit a participating foreign intellectual property (IP) office access to the instant application-as-filed (see paragraph A in subsection 1 below) and the European Patent Office (EPO) access to any search results from the instant application (see paragraph B in subsection 1 below).

Should applicant choose not to provide an authorization identified in subsection 1 below, applicant <u>must opt-out</u> of the authorization by checking the corresponding box A or B or both in subsection 2 below.

<u>NOTE</u>: This section of the Application Data Sheet is <u>**ONLY**</u> reviewed and processed with the <u>**INITIAL**</u> filing of an application. After the initial filing of an application, an Application Data Sheet cannot be used to provide or rescind authorization for access by a foreign IP office(s). Instead, Form PTO/SB/39 or PTO/SB/69 must be used as appropriate.

1. Authorization to Permit Access by a Foreign Intellectual Property Office(s)

A. <u>Priority Document Exchange (PDX)</u> - Unless box A in subsection 2 (opt-out of authorization) is checked, the undersigned hereby <u>grants the USPTO authority</u> to provide the European Patent Office (EPO), the Japan Patent Office (JPO), the Korean Intellectual Property Office (KIPO), the State Intellectual Property Office of the People's Republic of China (SIPO), the World Intellectual Property Organization (WIPO), and any other foreign intellectual property office participating with the USPTO in a bilateral or multilateral priority document exchange agreement in which a foreign application claiming priority to the instant patent application is filed, access to: (1) the instant patent application-as-filed and its related bibliographic data, (2) any foreign or domestic application to which priority or benefit is claimed by the instant application and its related bibliographic data, and (3) the date of filing of this Authorization. See 37 CFR 1.14(h) (1).

B. <u>Search Results from U.S. Application to EPO</u> - Unless box B in subsection 2 (opt-out of authorization) is checked, the undersigned hereby <u>grants the USPTO authority</u> to provide the EPO access to the bibliographic data and search results from the instant patent application when a European patent application claiming priority to the instant patent application is filed. See 37 CFR 1.14(h)(2).

The applicant is reminded that the EPO's Rule 141(1) EPC (European Patent Convention) requires applicants to submit a copy of search results from the instant application without delay in a European patent application that claims priority to the instant application.

2. Opt-Out of Authorizations to Permit Access by a Foreign Intellectual Property Office(s)

A. Applicant **DOES NOT** authorize the USPTO to permit a participating foreign IP office access to the instant application-as-filed. If this box is checked, the USPTO will not be providing a participating foreign IP office with any documents and information identified in subsection 1A above.

B. Applicant **DOES NOT** authorize the USPTO to transmit to the EPO any search results from the instant patent application. If this box is checked, the USPTO will not be providing the EPO with search results from the instant application.

NOTE: Once the application has published or is otherwise publicly available, the USPTO may provide access to the application in accordance with 37 CFR 1.14.
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES	S WITH GRADED DOPANT RE	GIONS

Applicant Information:

Providing assignment information ir to have an assignment recorded by		for compliance with any re	equirement of part 3 of Title 37 of CFR			
Applicant 1 Remove						
The information to be provided in this 1.43; or the name and address of the who otherwise shows sufficient propr applicant under 37 CFR 1.46 (assign	section is the name and address assignee, person to whom the ir ietary interest in the matter who i ee, person to whom the inventor	s of the legal representation oventor is under an obligat s the applicant under 37 (is obligated to assign, or p	this section should not be completed. ve who is the applicant under 37 CFR tion to assign the invention, or person CFR 1.46. If the applicant is an person who otherwise shows sufficient s who are also the applicant should be Clear			
Assignee	Legal Representative ur	nder 35 U.S.C. 117	Joint Inventor			
Person to whom the inventor is ob	ligated to assign.	Person who show	vs sufficient proprietary interest			
If applicant is the legal representation	tive, indicate the authority to	file the patent application	on, the inventor is:			
			•			
Name of the Deceased or Legally	/ Incapacitated Inventor:					
If the Applicant is an Organization	on check here.					
Organization Name GREEN	THREAD, LLC					
Mailing Address Information I	or Applicant:					
Address 1 454	4 Harrys Lane					
Address 2			1			
City	as	State/Province	тх			
Country US	Country ⁱ US Postal Code 75229					
Phone Number	Phone Number Fax Number					
Email Address						
Additional Applicant Data may be generated within this form by selecting the Add button.						

Assignee Information including Non-Applicant Assignee Information:

Providing assignment information in this section does not substitute for compliance with any requirement of part 3 of Title 37 of CFR to have an assignment recorded by the Office.

PTO/AIA/14 (02-18)

Approved for use through 11/30/2020. OMB 0651-0032 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Application Data Sheet 37 CFR 1.76		Attorney Doo	ket Number	GRTD60	GRTD60-35314		
		Application N	lumber				
Title of Invention SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS							
Assignee 1							
application publicati	ion. An assig	e information, including nee-applicant identifie an assignee-applicant	d in the "Applica	ant Information	n" section wil	l appear on the	
						F	Remove
If the Assignee of	or Non-Appl	licant Assignee is an	Organization	check here.			
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NOTE: This Application Data Sheet must be signed in accordance with 37 CFR 1.33(b). However, if this Application Data Sheet is submitted with the INITIAL filing of the application and either box A or B is not checked in subsection 2 of the "Authorization or Opt-Out of Authorization to Permit Access" section, then this form must also be signed in accordance with 37 CFR 1.14(c). This Application Data Sheet must be signed by a patent practitioner if one or more of the applicants is a juristic entity (e.g., corporation or association). If the applicant is two or more joint inventors, this form must be signed by a patent practitioner, all joint inventors who are the applicant, or one or more joint inventor-applicants who have been given power of attorney (e.g., see USPTO Form PTO/AIA/81) on behalf of all joint inventor-applicants. See 37 CFR 1.4(d) for the manner of making signatures and certifications.							
Signature /Gregory M. Howison, Reg. #30646/			Date (YYYY-MM-DI	D) 2021-07-09		
First Name G	regory	Last Name	Howison		Registra	ation Number	r 30646
Additional Signature may be generated within this form by selecting the Add button.							

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Application Data Sheet 37 CFR 1.76		Attorney Docket Number	GRTD60-35314
		Application Number	
Title of Invention	SEMICONDUCTOR DEVICES WITH GRADED DOPANT RE		GIONS

This collection of information is required by 37 CFR 1.76. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 23 minutes to complete, including gathering, preparing, and submitting the completed application data sheet form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. **SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450**.

Privacy Act Statement

The Privacy Act of 1974 (P.L. 93-579) requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

The information provided by you in this form will be subject to the following routine uses:

- 1 The information on this form will be treated confidentially to the extent allowed under the Freedom of Information Act (5 U.S.C. 552) and the Privacy Act (5 U.S.C. 552a). Records from this system of records may be disclosed to the Department of Justice to determine whether the Freedom of Information Act requires disclosure of these records.
- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3 A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent CooperationTreaty.
- 6. A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (i.e., GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspections or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.

Electronic Patent Application Fee Transmittal					
Application Number:					
Filing Date:					
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				iions
First Named Inventor/Applicant Name:	G. R. Mohan	Rao			
Filer:	Gregory Micl	nael How	ison/Joselyn Ro	odriguez	
Attorney Docket Number:	GRTD60-353	14			
Filed as Large Entity					
Filing Fees for Track I Prioritized Examination - Nonp	rovisional Ap	plicatio	on under 35 U	ISC 111(a)	
Description	Fee	Code	Quantity	Amount	Sub-Total in USD(\$)
Basic Filing:					
UTILITY APPLICATION FILING	1()11	1	320	320
UTILITY SEARCH FEE	1	11	1	700	700
UTILITY EXAMINATION FEE	1:	811	1	800	800
REQUEST FOR PRIORITIZED EXAMINATION 1817			1	4200	4200
Pages:					
Claims:					
CLAIMS IN EXCESS OF 20 1202 10 100 1000					1000
Miscellaneous-Filing:					

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)			
PUBL. FEE- EARLY, VOLUNTARY, OR NORMAL	1504	1	0	0			
PROCESSING FEE, EXCEPT PROV. APPLS.	1830	1	140	140			
Petition:							
Patent-Appeals-and-Interference:							
Post-Allowance-and-Post-Issuance:							
Extension-of-Time:							
Miscellaneous:							
	Tot	al in USD	(\$)	7160			

Electronic Acknowledgement Receipt					
EFS ID:	43208746				
Application Number:	17371839				
International Application Number:					
Confirmation Number:	2197				
Title of Invention:	SEMICONDUCTOR DEVICES WITH GRADED DOPANT REGIONS				
First Named Inventor/Applicant Name:	G. R. Mohan Rao				
Customer Number:	25883				
Filer:	Gregory Michael Howison/Joselyn Rodriguez				
Filer Authorized By:	Gregory Michael Howison				
Attorney Docket Number:	GRTD60-35314				
Receipt Date:	09-JUL-2021				
Filing Date:					
Time Stamp:	15:54:57				
Application Type:	Utility under 35 USC 111(a)				

Payment information:

Submitted with Payment	yes			
Payment Type	CARD			
Payment was successfully received in RAM	\$7160			
RAM confirmation Number	E202179F55414118			
Deposit Account	500208			
Authorized User Joselyn Rodriguez				
The Director of the USPTO is hereby authorized to charge indicated fees and credit any overpayment as follows:				
37 CFR 1.16 (National application filing, search, and examination fees)				

37 CFR 1.17 (Patent application and reexamination processing fees)

File Listing:

J:						
Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)		
		140549				
TrackOne Request	GRT35314TRACKONE.pdf	779d93c31db6608eb657b16f6f66853e26f3 0ffe	no	2		
I						
Drawings only black and white line		3441256		10		
drawings	GRT35314DWGS.pdf	31b25c7e387f925f58cd58d1c08f8bd71bda f80e	no			
		•				
	GRT35314POAEXE.pdf	1583112				
Power of Attorney		08b2695aac1899d04843b5ffb8b114e330f0 cdf3	no	2		
		μ				
		102924				
Oath or Declaration filed	GRT35314DECEXE.pdf	425aabcd457f692cf118f871fd294b201f2de eSf	no	1		
		Ι				
		145967				
	GRT35314CON.pdf	34de3341512aa1ec1f11993602ac6ed6210 a5b2e	yes	13		
Multipart Description/PDF files in .zip description						
Document Description		Start	E	nd		
Abstract		13	1	3		
Claims		9	1	2		
Specification		1		8		
	Document Description TrackOne Request Drawings-only black and white line drawings Power of Attorney Oath or Declaration filed Multip Document Des Abstrac Claims	Document Description File Name TrackOne Request GRT35314TRACKONE,pdf Drawings-only black and white line drawings GRT35314DWGS,pdf Power of Attorney GRT35314DOAEXE,pdf Power of Attorney GRT35314POAEXE,pdf Oath or Declaration filed GRT35314DOAEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf GRT35314DECEXE,pdf	Document Description File Name File Size(Bytes)/ Message Digest TrackOne Request GRT35314TRACKONE.pdf 140549 TrackOne Request GRT35314TRACKONE.pdf 70933146886665731688685088 Drawings-only black and white line drawings GRT35314DWGS.pdf 3441256 Drawings-only black and white line drawings GRT35314DWGS.pdf 1583112 Power of Attorney GRT35314POAEXE.pdf 102024 Oath or Declaration filed GRT35314DECEXE.pdf 102024 GRT35314DECEXE.pdf 102024 102024 Oath or Declaration filed GRT35314DECEXE.pdf 102024 Multipart Description/PDF files in zip description 346197 36697 Multipart Description/PDF files in zip description 36697 366975 Claims 9 9	Document Description File Name File Size(Bytes)/ Message Digest Multi Part /.zip Interster Interster		

Warnings:					
Information:					
6	Application Data Sheet	GRT35314ADS.pdf	1874721 78965d0da00b7db97d3f7430b8be76363c 3fa998	no	9
Warnings:		ł			•
Information:					
7	Fee Worksheet (SB06)	fee-info.pdf	41799 2b3d674d035c0fbe0e3fa6592b303de43ff4 633a	no	2
Warnings:		•			
Information:			-		
		Total Files Size (in bytes)	73	30328	
characterized Post Card, as <u>New Applica</u> If a new appl 1.53(b)-(d) an Acknowledg <u>National Stad</u> If a timely su U.S.C. 371 an national stag <u>New Internat</u> If a new inter an internatio and of the In	ledgement Receipt evidences receip d by the applicant, and including par- s described in MPEP 503. <u>tions Under 35 U.S.C. 111</u> lication is being filed and the applican nd MPEP 506), a Filing Receipt (37 CF ement Receipt will establish the filin ge of an International Application un bmission to enter the national stage ad other applicable requirements a F ge submission under 35 U.S.C. 371 w tional Application Filed with the USF rnational application is being filed an ternational Filing Date (Form PCT/Re urity, and the date shown on this Act on.	ge counts, where applicable. Intion includes the necessary of FR 1.54) will be issued in due of date of the application. Inder 35 U.S.C. 371 Form PCT/DO/EO/903 indicati Form PCT/DO/EO/903 indicati III be issued in addition to the PTO as a Receiving Office and the international applicat of MPEP 1810), a Notification O/105) will be issued in due c	It serves as evidence components for a filir course and the date s on is compliant with ng acceptance of the e Filing Receipt, in du ion includes the nece of the International ourse, subject to pres	of receipt s ng date (see shown on th the condition application e course. essary comp Application scriptions c	imilar to a 37 CFR his ons of 35 h as a oonents for Number oncerning

CERTIFICATION AND REQUEST FOR PRIORITIZED EXAMINATION UNDER 37 CFR 1.102(e) (Page 1 of 1)					
First Named Inventor:	G.R. MOHAN Rao	Nonprovisional Application N known):	lumber (if		
Title of Invention:	SEMICONDUCTOR DEVIC	CES WITH GRADE	ED DOP/	ANT REGIONS	
	REBY CERTIFIES THE FOLLOWIN ENTIFIED APPLICATION.	G AND REQUESTS PR	IORITIZED	EXAMINATION FOR	
CFR 1.7 filed wit	ocessing fee set forth in 37 CFR 1 17(c), and if not already paid, the h the request. The basic filing fee claims and application size fees a	publication fee set fort e, search fee, examina	h in 37 CF tion fee, a	R 1.18(d) have been nd any required	
	plication contains or is amended t than thirty total claims, and no m			ependent claims and	
3. The ap	plicable box is checked below:				
I. <u>1</u>	Original Application (Track One	e) - Prioritized Exami	nation und	der <u>§ 1.102(e)(1)</u>	
	application is an original nonprov tification and request is being file OR	d with the utility applic			
• • •	application is an original nonprov tification and request is being file			.,	
ii. An exe	cuted oath or declaration under 3	7 CFR 1.63 is filed wit	h the appli	cation.	
II. <u> </u>	Request for Continued Examination	ation - Prioritized Exa	amination	under <u>§</u> 1.102(e)(2)	
 i. A request for continued examination has been filed with, or prior to, this form. ii. If the application is a utility application, this certification and request is being filed via EFS-Web. iii. The application is an original nonprovisional utility application filed under 35 U.S.C. 111(a), or is a national stage entry under 35 U.S.C. 371. iv. This certification and request is being filed prior to the mailing of a first Office action responsive to the request for continued examination. v. No prior request for continued examination has been granted prioritized examination status under 37 CFR 1.102(e)(2). 					
_{Signature} /Greę	gory M. Howison, Reg. #3	30646/	_{Date} July	/ 9, 2021	
Name (Print/Typed) Gregory M. Howison Practitioner Registration Number 30,646				30.646	
Note: Signatures of all the inventors or assignees of record of the entire interest or their representative(s) are required in accordance with 37 CFR 1.33 and 11.18. Please see 37 CFR 1.4(d) for the form of the signature. If necessary, submit multiple forms for more than one signature, see below*.					

*Total of _____ forms are submitted.

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The **Privacy Act of 1974 (P.L. 93-579)** requires that you be given certain information in connection with your submission of the attached form related to a patent application or patent. Accordingly, pursuant to the requirements of the Act, please be advised that: (1) the general authority for the collection of this information is 35 U.S.C. 2(b)(2); (2) furnishing of the information solicited is voluntary; and (3) the principal purpose for which the information is used by the U.S. Patent and Trademark Office is to process and/or examine your submission related to a patent application or patent. If you do not furnish the requested information, the U.S. Patent and Trademark Office may not be able to process and/or examine your submission, which may result in termination of proceedings or abandonment of the application or expiration of the patent.

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- 2. A record from this system of records may be disclosed, as a routine use, in the course of presenting evidence to a court, magistrate, or administrative tribunal, including disclosures to opposing counsel in the course of settlement negotiations.
- 3. A record in this system of records may be disclosed, as a routine use, to a Member of Congress submitting a request involving an individual, to whom the record pertains, when the individual has requested assistance from the Member with respect to the subject matter of the record.
- 4. A record in this system of records may be disclosed, as a routine use, to a contractor of the Agency having need for the information in order to perform a contract. Recipients of information shall be required to comply with the requirements of the Privacy Act of 1974, as amended, pursuant to 5 U.S.C. 552a(m).
- 5. A record related to an International Application filed under the Patent Cooperation Treaty in this system of records may be disclosed, as a routine use, to the International Bureau of the World Intellectual Property Organization, pursuant to the Patent Cooperation Treaty.
- A record in this system of records may be disclosed, as a routine use, to another federal agency for purposes of National Security review (35 U.S.C. 181) and for review pursuant to the Atomic Energy Act (42 U.S.C. 218(c)).
- 7. A record from this system of records may be disclosed, as a routine use, to the Administrator, General Services, or his/her designee, during an inspection of records conducted by GSA as part of that agency's responsibility to recommend improvements in records management practices and programs, under authority of 44 U.S.C. 2904 and 2906. Such disclosure shall be made in accordance with the GSA regulations governing inspection of records for this purpose, and any other relevant (*i.e.*, GSA or Commerce) directive. Such disclosure shall not be used to make determinations about individuals.
- 8. A record from this system of records may be disclosed, as a routine use, to the public after either publication of the application pursuant to 35 U.S.C. 122(b) or issuance of a patent pursuant to 35 U.S.C. 151. Further, a record may be disclosed, subject to the limitations of 37 CFR 1.14, as a routine use, to the public if the record was filed in an application which became abandoned or in which the proceedings were terminated and which application is referenced by either a published application, an application open to public inspection or an issued patent.
- 9. A record from this system of records may be disclosed, as a routine use, to a Federal, State, or local law enforcement agency, if the USPTO becomes aware of a violation or potential violation of law or regulation.



Dopant Concentration (per Cm2)+

Figure 1 Prior Art

Dopant Concentration (per Cm3)

192

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GRTD60-35314

FIGURE 2 Prior art



FIGURE 3A Prior art (Twin well CMOS) for a CMOS integrated circuit

194



FIGURE 3B Prior art for a two-device EEPROM memory cell



FIGURE 3C Prior art for a 1T-1C DRAM memory cell



FIGURE 3D Prior art for a NAND flash memory cell

Note: Control/ Sect transistors have a single insulator - traditional MOS transistor. Storage nodes have a stacked gate structure, typically with

a floating gate and control gate comprising the stack.



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FIGURE 4 A dopant - concentration grinded drift region in a IGBT



FIGURE 5A A CMOS Substrate for digital, mixed, signal, and senors IC's



FIGURE 5B CMOS Substrate for a DRAM or image sensor, with one embodiment of the invention

